

Features

- High FSK Sensitivity: -106 dBm at 20 kBaud/-109.5 dBm at 2.4 kBaud (433.92 MHz)
- High ASK Sensitivity: -112.5 dBm at 10 kBaud/-116.5 dBm at 2.4 kBaud (433.92 MHz)
- Low Supply Current: 10.5 mA in RX and TX Mode (3V/TX with 5 dBm)
- Data Rate 1 to 20 kBaud Manchester FSK, 1 to 10 kBaud Manchester ASK
- ASK/FSK Receiver Uses a Low-IF Architecture with High Selectivity, Blocking and Low Intermodulation (Typical Blocking 55 dB at ± 750 kHz/61 dB at ± 1.5 MHz and 70 dB at ± 10 MHz, System I1dBCP = -30 dBm/System IIP3 = -20 dBm)
- 226 kHz IF Frequency with 30 dB Image Rejection and 170 kHz Usable IF Bandwidth
- Transmitter Uses Closed Loop Fractional-N Synthesizer for FSK Modulation with a High PLL Bandwidth and an Excellent Isolation between PLL and PA
- Tolerances of XTAL Compensated by Fractional-N Synthesizer with 800 Hz RF Resolution
- Integrated RX/TX-Switch, Single-ended RF Input and Output
- RSSI (Received Signal Strength Indicator)
- Communication to Microcontroller with SPI Interface Working at Maximum 500 kBit/s
- Configurable Self Polling and RX/TX Protocol Handling with FIFO-RAM Buffering of Received and Transmitted Data
- 5 Push Button Inputs and One Wake-up Input are Active in Power-down Mode
- Integrated XTAL Capacitors
- PA Efficiency: up to 38% (433 MHz/10 dBm/3V)
- Low Inband Sensitivity Change of Typically ± 1.8 dB within ± 58 kHz Center Frequency Change in the Complete Temperature and Supply Voltage Range
- Supply Voltage Switch, Supply Voltage Regulator, Reset Generation, Clock/Interrupt Generation and Low Battery Indicator for Microcontroller
- Fully Integrated PLL with Low Phase Noise VCO and PLL Loop Filter
- Sophisticated Threshold Control and Quasi Peak Detector Circuit in the Data Slicer
- Power Management via Different Operation Modes
- 433.92 MHz, 868.3 MHz and 315 MHz without External VCO and PLL Components
- Inductive Supply with Voltage Regulator if Battery is Empty (AUX Mode)
- Efficient XTO Start-up Circuit (> -1.5 k Ω Worst Case Start Impedance)
- Changing of Modulation Type ASK/FSK and Data Rate without Component Changes
- Minimal External Circuitry Requirements for Complete System Solution
- Adjustable Output Power: 0 to 10 dBm Adjusted and Stabilized with External Resistor
- ESD Protection at all Pins (2 kV HBM, 200 V MM)
- Supply Voltage Range: 2.4V to 3.6V or 4.4V to 6.6V
- Temperature Range: -40°C to +105°C
- Small 7 \times 7 mm QFN48 Package



UHF ASK/FSK Transceiver

ATA5811
ATA5812

Rev. 4689D-RKE-10/05



Applications

- Automotive Keyless Entry and Passive Entry Go Systems
- Access Control Systems
- Remote Control Systems
- Alarm and Telemetry Systems
- Energy Metering
- Home Automation

Benefits

- No SAW Device Needed in Key Fob Designs to Meet Automotive Specifications
- Low System Cost Due to Very High System Integration Level
- Only One Crystal Needed in System
- Less Demanding Specification for the Microcontroller Due to Handling of Power-down Mode, Delivering of Clock, Reset, Low Battery Indication and Complete Handling of Receive/Transmit Protocol and Polling
- Single-ended Design with High Isolation of PLL/VCO from PA and the Power Supply Allows a Loop Antenna in the Key Fob to Surround the Whole Application

1. General Description

The ATA5811/ATA5812 is a highly integrated UHF ASK/FSK single-channel half-duplex transceiver with low power consumption supplied in a small QFN48 package. The receive part is built as a fully integrated low-IF receiver, whereas direct PLL modulation with the fractional-N synthesizer is used for FSK transmission and switching of the power amplifier for ASK transmission.

The device supports data rates of 1 kBaud to 20 kBaud (FSK) and 1 kBaud to 10 kBaud (ASK) in Manchester, Bi-phase and other codes in transparent mode. The ATA5811 can be used in the 433 MHz to 435 MHz and the 868 MHz to 870 MHz band, the ATA5812 in the 314 MHz to 316 MHz band. The very high system integration level results in few numbers of external components needed.

Due to its blocking and selectivity performance, together with the additional 15 dB to 20 dB loss and the narrow bandwidth of a typical key fob loop antenna, a bulky blocking SAW is not needed in the key fob or sensor application. Additionally, the building blocks needed for a typical RKE and access control system on both sides, the base and the mobile stations, are fully integrated.

Its digital control logic with self polling and protocol generation enables a fast challenge response systems without using a high-performance microcontroller. Therefore, the ATA5811/ATA5812 contains a FIFO buffer RAM and can compose and receive the physical messages themselves. This provides more time for the microcontroller to carry out other functions such as calculating crypto algorithms, composing the logical messages and controlling other devices. Due to that, a standard 4-/8-bit microcontroller without special periphery and clocked with the CLK output of about 4.5 MHz is sufficient to control the communication link. This is especially valid for passive entry and access control systems, where within less than 100 ms several challenge response communications with arbitration of the communication partner have to be handled.

It is hence possible to design bi-directional RKE and access control systems with a fast challenge response crypto function with the same PCB board size and with the same current consumption as uni-directional RKE systems.

Figure 1-1. System Block Diagram

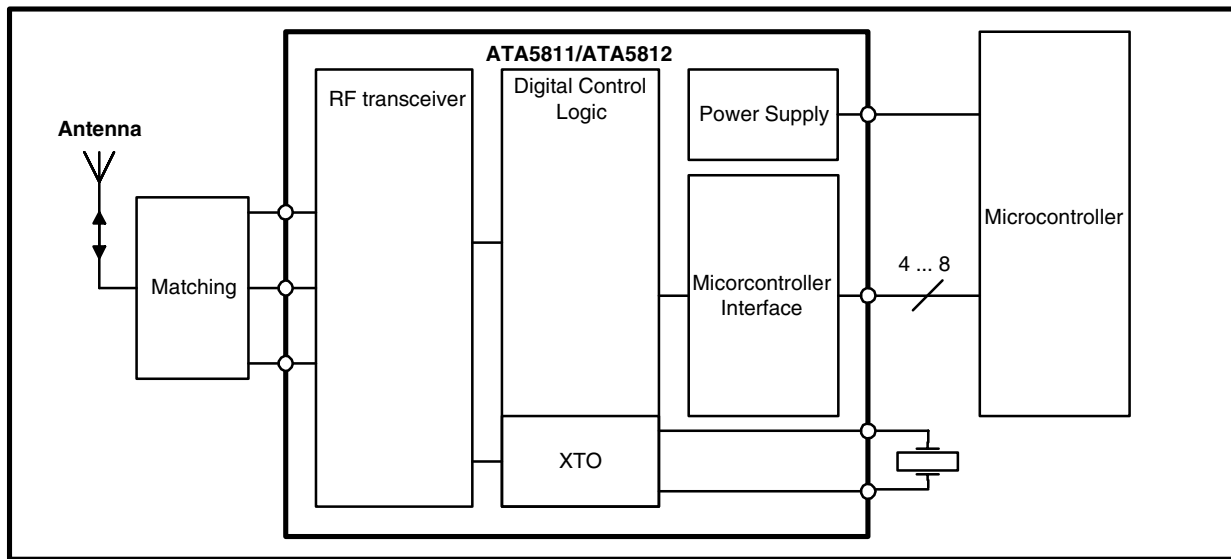


Figure 1-2. Pinning QFN48

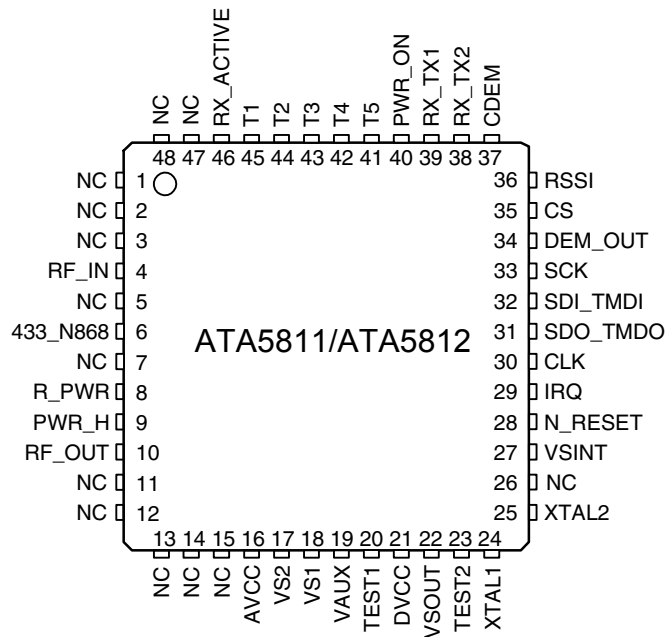


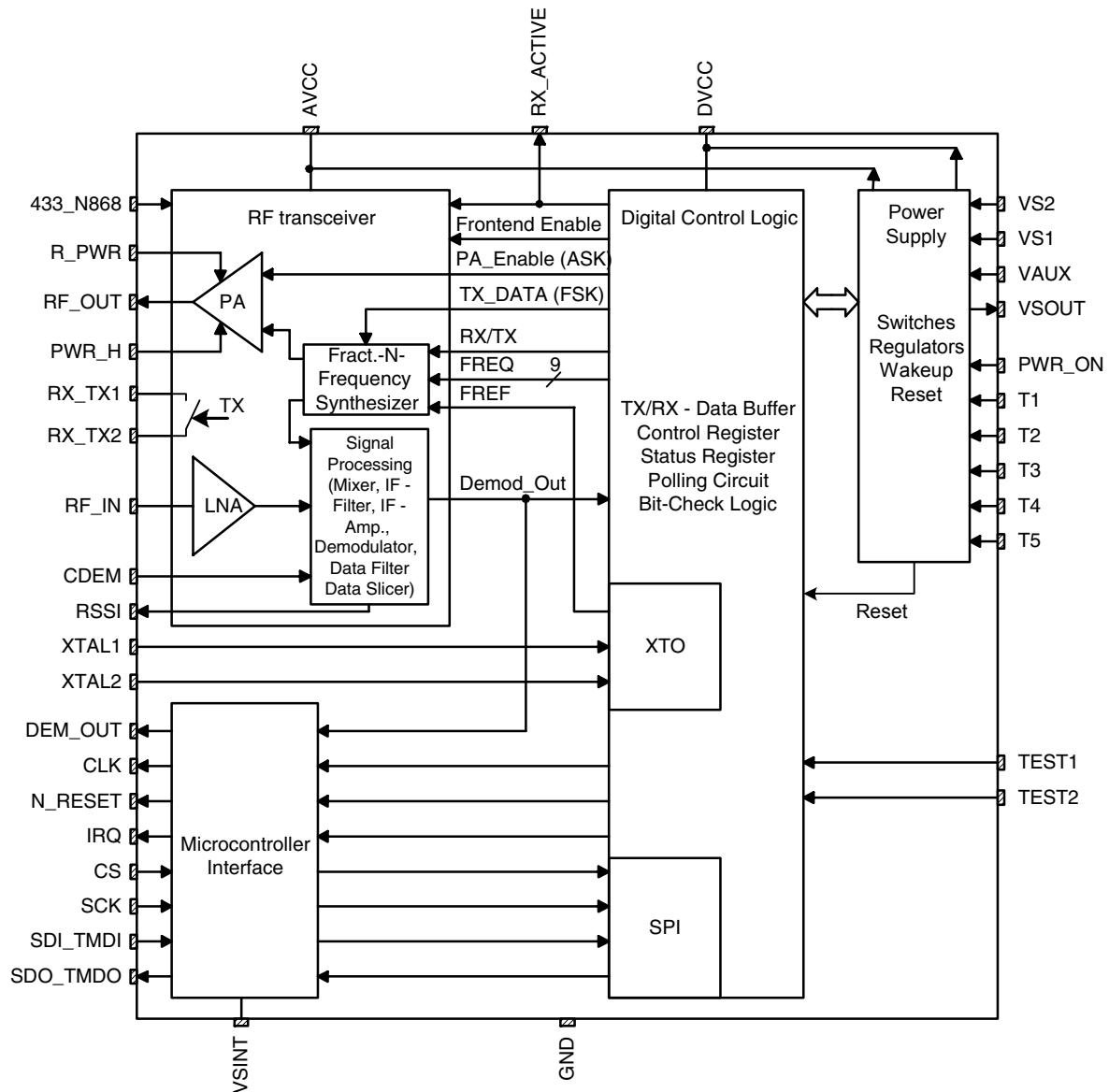
Table 1-1. Pin Description

| Pin | Symbol | Function |
|-----|----------|---|
| 1 | NC | Not connected |
| 2 | NC | Not connected |
| 3 | NC | Not connected |
| 4 | RF_IN | RF input |
| 5 | NC | Not connected |
| 6 | 433_N868 | Selects RF input/output frequency range |
| 7 | NC | Not connected |
| 8 | R_PWR | Resistor to adjust output power |
| 9 | PWR_H | Pin to select output power |
| 10 | RF_OUT | RF output |
| 11 | NC | Not connected |
| 12 | NC | Not connected |
| 13 | NC | Not connected |
| 14 | NC | Not connected |
| 15 | NC | Not connected |
| 16 | AVCC | Blocking of the analog voltage supply |
| 17 | VS2 | Power supply input for voltage range 4.4V to 6.6V |
| 18 | VS1 | Power supply input for voltage range 2.4V to 3.6V |
| 19 | VAUX | Auxiliary supply voltage input |
| 20 | TEST1 | Test input, at GND during operation |
| 21 | DVCC | Blocking of the digital voltage supply |
| 22 | VSOUT | Output voltage power supply for external devices |
| 23 | TEST2 | Test input, at GND during operation |
| 24 | XTAL1 | Reference crystal |
| 25 | XTAL2 | Reference crystal |
| 26 | NC | Not connected |
| 27 | VSINT | Microcontroller Interface supply voltage |
| 28 | N_RESET | Output pin to reset a connected microcontroller |
| 29 | IRQ | Interrupt request |
| 30 | CLK | Output to clock a connected microcontroller |
| 31 | SDO_TMDO | Serial data out/transparent mode data out |
| 32 | SDI_TMDI | Serial data in/transparent mode data in |
| 33 | SCK | Serial clock |
| 34 | DEM_OUT | Demodulator open drain output signal |
| 35 | CS | Chip select for serial interface |
| 36 | RSSI | Output of the RSSI amplifier |
| 37 | CDEM | Capacitor to adjust the lower cut-off frequency data filter |
| 38 | RX_TX2 | GND pin to decouple LNA in TX mode |
| 39 | RX_TX1 | Switch pin to decouple LNA in TX mode |
| 40 | PWR_ON | Input to switch on the system (active high) |
| 41 | T5 | Key input 5 (can also be used to switch on the system (active low)) |

Table 1-1. Pin Description (Continued)

| Pin | Symbol | Function |
|-----|-----------|---|
| 42 | T4 | Key input 4 (can also be used to switch on the system (active low)) |
| 43 | T3 | Key input 3 (can also be used to switch on the system (active low)) |
| 44 | T2 | Key input 2 (can also be used to switch on the system (active low)) |
| 45 | T1 | Key input 1 (can also be used to switch on the system (active low)) |
| 46 | RX_ACTIVE | Indicates RX operation mode |
| 47 | NC | Not connected |
| 48 | NC | Not connected |
| | GND | Ground/backplane |

Figure 1-3. Block Diagram



2. Typical Key Fob or Sensor Application with 1 Battery

Figure 2-1. Typical RKE Key Fob or Sensor Application, 433.92 MHz, 1 Battery

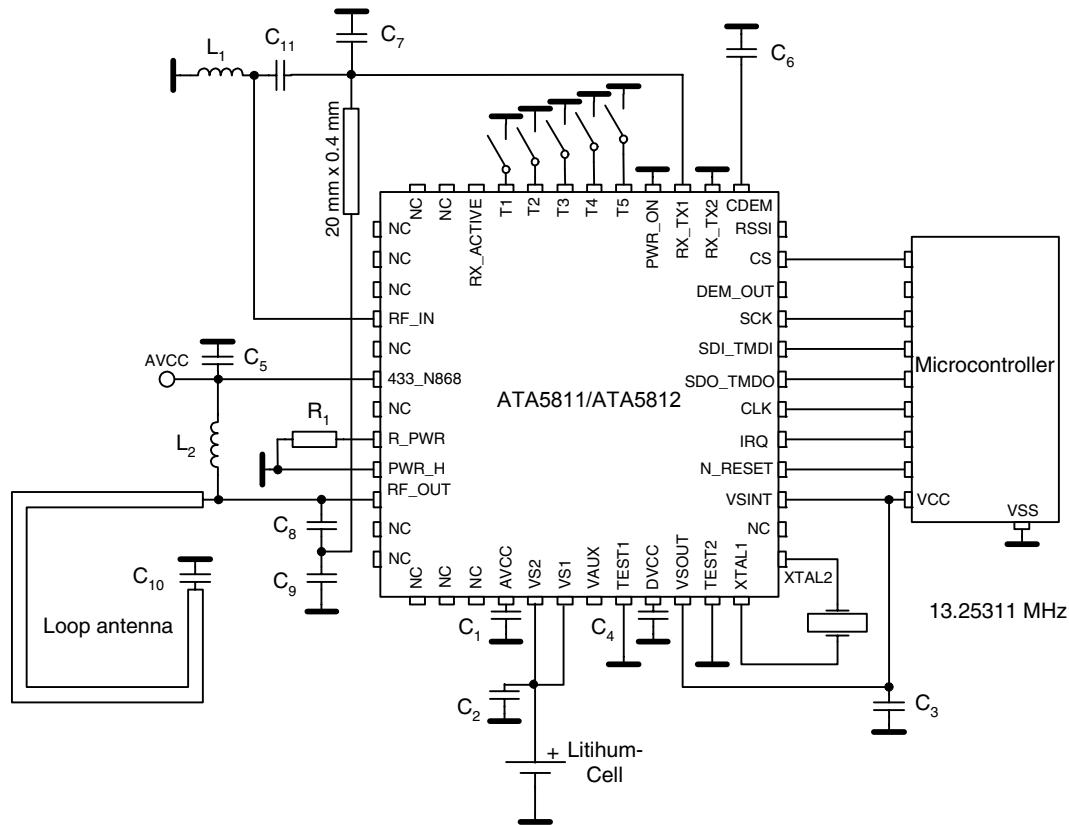


Figure 2-1 shows a typical 433.92 MHz RKE key fob or sensor application with one battery. The external components are 11 capacitors, 1 resistor, 2 inductors and a crystal. C_1 to C_4 are 68 nF voltage supply blocking capacitors. C_5 is a 10 nF supply blocking capacitor. C_6 is a 15 nF fixed capacitor used for the internal quasi peak detector and for the highpass frequency of the data filter. C_7 to C_{11} are RF matching capacitors in the range of 1 pF to 33 pF. L_1 is a matching inductor of about 5.6 nH to 56 nH. L_2 is a feed inductor of about 120 nH. A load capacitor of 9 pF for the crystal is integrated. R_1 is typically 22 k Ω and sets the output power to about 5.5 dBm. The loop antenna's quality factor is somewhat reduced by this application due to the quality factor of L_2 and the RX/TX switch. On the other hand, this lower quality factor is necessary to have a robust design with a bandwidth that is broad enough for production tolerances. Due to the single-ended and ground-referenced design, the loop antenna can be a free-form wire around the application as it is usually employed in RKE uni-directional systems. The ATA5811/ATA5812 provides sufficient isolation and robust pulling behavior of internal circuits from the supply voltage as well as an integrated VCO inductor to allow this. Since the efficiency of a loop antenna is proportional to the square of the surrounded area it is beneficial to have a large loop around the application board with a lower quality factor to relax the tolerance specification of the RF components and to get a high antenna efficiency in spite of their lower quality factor.

3. Typical Car or Sensor Base-station Application

Figure 3-1. Typical RKE Car or Sensor Base-station Application, 433.92 MHz

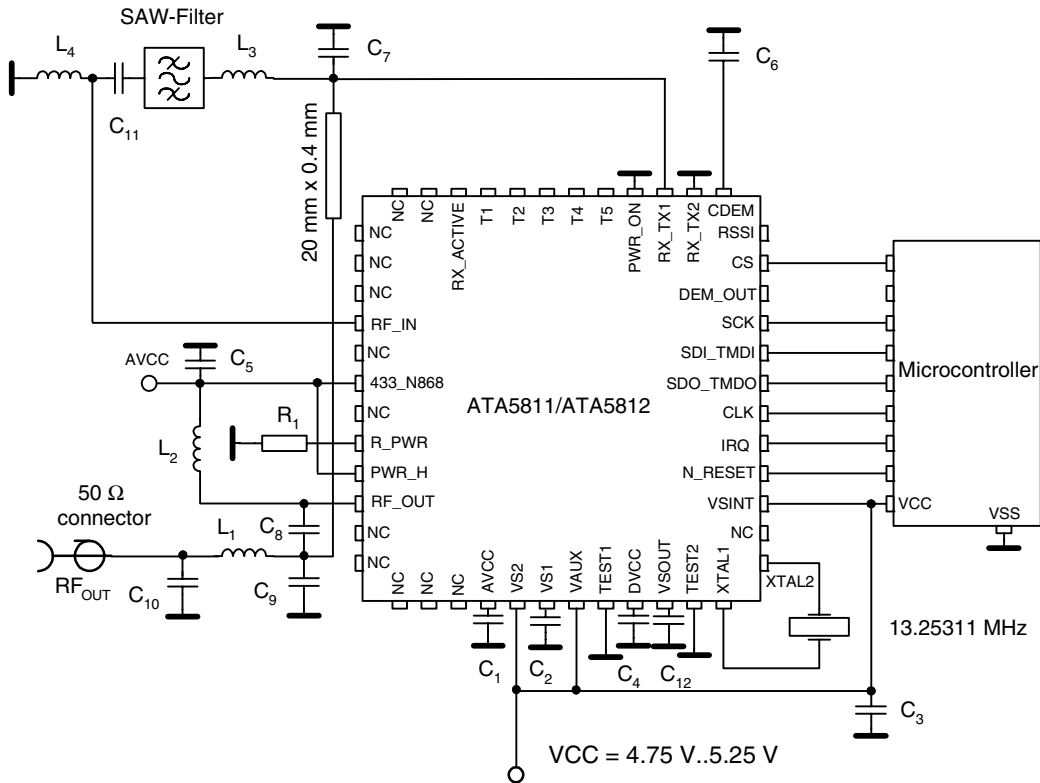


Figure 3-1 shows a typical 433.92 MHz $V_{CC} = 4.75\text{V}$ to 5.25V RKE car or sensor base-station application. The external components are 12 capacitors, 1 resistor, 4 inductors, a SAW filter and a crystal. C_1 and C_3 to C_4 are 68 nF voltage supply blocking capacitors. C_2 and C_{12} are 2.2 μF supply blocking capacitors for the internal voltage regulators. C_5 is a 10 nF supply blocking capacitor. C_6 is a 15 nF fixed capacitor used for the internal quasi peak detector and for the highpass frequency of the data filter. C_7 to C_{11} are RF matching capacitors in the range of 1 pF to 33 pF. L_2 to L_4 are matching inductors of about 5.6 nH to 56 nH. A load capacitor for the crystal of 9 pF is integrated. R_1 is typically 22 k Ω and sets the output power at RF_OUT to about 10 dBm. Since a quarter wave or PCB antenna, which has high efficiency and wide band operation, is typically used here, it is recommended to use a SAW filter to achieve high sensitivity in case of powerful out-of-band blockers. L_1 , C_{10} and C_9 together form a lowpass filter, which is needed to filter out the harmonics in the transmitted signal to meet regulations. An internally regulated voltage at pin VSOUT can be used in case the microcontroller only supports 3.3V operation, a blocking capacitor with a value of $C_{12} = 2.2 \mu\text{F}$ has to be connected to VSOUT in any case.

4. Typical Key Fob Application, 2 Batteries

Figure 4-1. Typical RKE Key Fob Application, 433.92 MHz, 2 Batteries

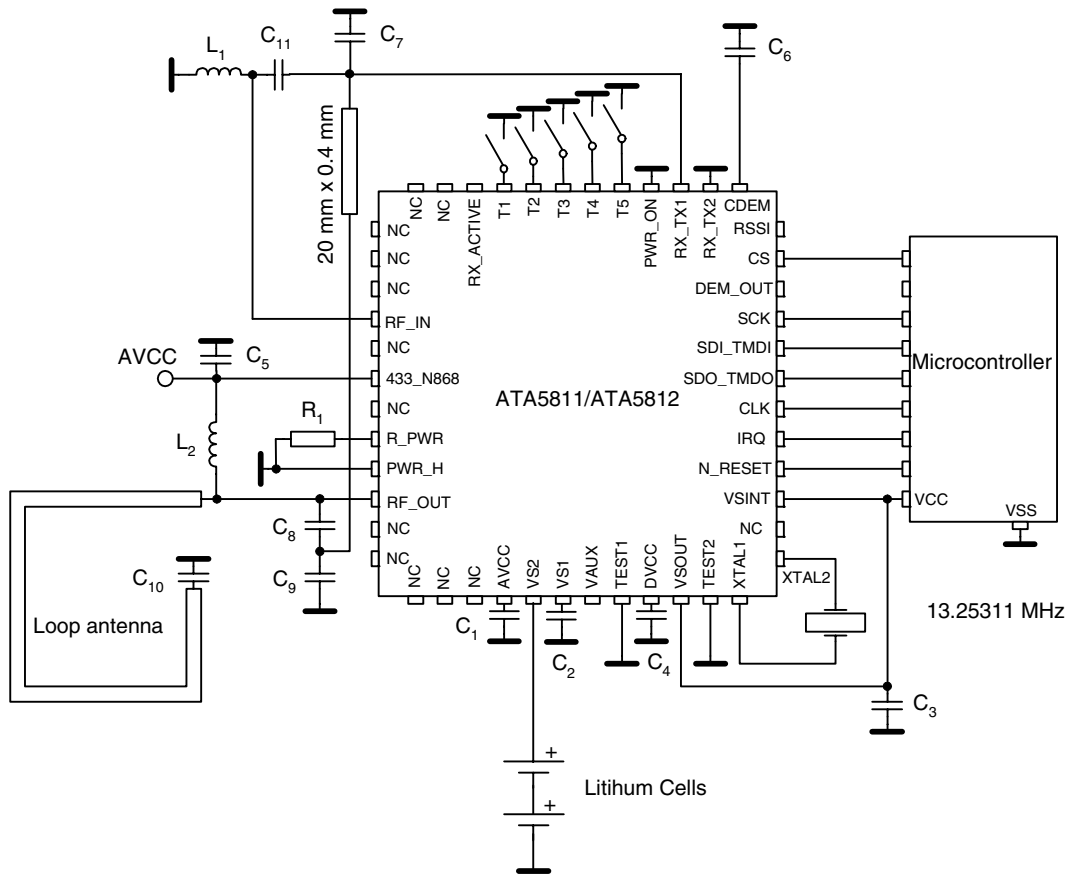


Figure 4-1 shows a typical 433.92 MHz 2-battery RKE key fob or sensor application. The external components are 11 capacitors, 1 resistor, 2 inductors and a crystal. C_1 and C_4 are 68 nF voltage supply blocking capacitors. C_2 and C_3 are 2.2 μ F supply blocking capacitors for the internal voltage regulators. C_5 is a 10 nF supply blocking capacitor. C_6 is a 15 nF fixed capacitor used for the internal quasi peak detector and for the highpass frequency of the data filter. C_7 to C_{11} are RF matching capacitors in the range of 1 pF to 33 pF. L_1 is a matching inductor of about 5.6 nH to 56 nH. L_2 is a feed inductor of about 120 nH. A load capacitor for the crystal of 9 pF is integrated. R_1 is typically 22 k Ω and sets the output power to about 5.5 dBm.

5. RF Transceiver

According to [Figure 1-3 on page 5](#), the RF transceiver consists of an LNA (Low-Noise Amplifier), PA (Power Amplifier), RX/TX switch, fractional-N frequency synthesizer and the signal processing part with mixer, IF filter, IF amplifier, FSK/ASK demodulator, data filter and data slicer.

In receive mode the LNA pre-amplifies the received signal which is converted down to 226 kHz, filtered and amplified before it is fed into an FSK/ASK demodulator, data filter and data slicer. The RSSI (Received Signal Strength Indicator) signal and the raw digital output signal of the demodulator are available at the pins RSSI and DEM_OUT. The demodulated data signal Demod_Out is fed to the digital control logic where it is evaluated and buffered as described in section [“Digital Control Logic” on page 33](#).

In transmit mode the fractional-N frequency synthesizer generates the TX frequency which is fed to the PA. In ASK mode the PA is modulated by the signal PA_Enable. In FSK mode the PA is enabled and the signal TX_DATA (FSK) modulates the fractional-N frequency synthesizer. The frequency deviation is digitally controlled and internally fixed to about ± 16 kHz (see [Table 6-1 on page 25](#) for exact values). The transmit data can also be buffered as described in section [“Digital Control Logic” on page 33](#). A lock detector within the synthesizer ensures that the transmission will only start if the synthesizer is locked.

The RX/TX switch can be used to combine the LNA input and the PA output to a single antenna with a minimum of losses.

Transparent modes without buffering of RX and TX data are also available to allow protocols and coding schemes other than the internal supported Manchester encoding.

5.1 Low-IF Receiver

The receive path consists of a fully integrated low-IF receiver. It fulfills the sensitivity, blocking, selectivity, supply voltage and supply current specification needed to manufacture an automotive key fob without the use of SAW blocking filter (see [Figure 2-1 on page 6](#)). The receiver can be connected to the roof antenna in the car when using an additional blocking SAW front-end filter as shown in [Figure 3-1 on page 7](#).

At 433.92 MHz the receiver has a typical system noise figure of 7.0 dB, a system I1dBCP of -30 dBm and a system IIP3 of -20 dBm. There is no AGC or switching of the LNA needed, thus, a better blocking performance is achieved. This receiver uses an IF (Intermediate Frequency) of 226 kHz, the typical image rejection is 30 dB and the typical 3 dB IF filter bandwidth is 185 kHz ($f_{IF} = 226 \text{ kHz} \pm 92.5 \text{ kHz}$, $f_{lo_IF} = 133.5 \text{ kHz}$ and $f_{hi_IF} = 318.5 \text{ kHz}$). The demodulator needs a signal to Gaussian noise ratio of 8 dB for 20 kBaud Manchester with ± 16 kHz frequency deviation in FSK mode, thus, the resulting sensitivity at 433.92 MHz is typically -106 dBm at 20 kBaud Manchester.

Due to the low phase noise and spurious of the synthesizer in receive mode⁽¹⁾ together with the eighth order integrated IF filter the receiver has a better selectivity and blocking performance than more complex double superhet receivers but without external components and without numerous spurious receiving frequencies.

A low-IF architecture is also less sensitive to second-order intermodulation (IIP2) than direct conversion receivers where every pulse or AM-modulated signal (especially the signals from TDMA systems like GSM) demodulates to the receiving signal band at second-order nonlinearities.

Note: 1. -120 dBC/Hz at ± 1 MHz and -75 dBC at $\pm \text{FREF}$ at 433.92 MHz

5.2 Input Matching at RF_IN

The measured input impedances as well as the values of a parallel equivalent circuit of these impedances can be seen in [Table 5-1](#). The highest sensitivity is achieved with power matching of these impedances to the source impedance of 50Ω

Table 5-1. Measured Input Impedances of the RF_IN Pin

| f_{RF}/MHz | $Z(\text{RF_IN})$ | R_p/C_p |
|---------------------|--------------------|----------------------------|
| 315 | $(44-j233)\Omega$ | $1278\Omega/2.1\text{ pF}$ |
| 433.92 | $(32-j169)\Omega$ | $925\Omega/2.1\text{ pF}$ |
| 868.3 | $(21-j78)\Omega$ | $311\Omega/2.2\text{ pF}$ |

The matching of the LNA Input to 50Ω was done with the circuit according to [Figure 5-1](#) and with the values given in [Table 5-2](#). The reflection coefficients were always $\leq 10\text{ dB}$. Note that value changes of C_1 and L_1 may be necessary to for compensate individual board layouts. The measured typical FSK and ASK Manchester code sensitivities with a Bit Error Rate (BER) of 10^{-3} are shown in [Table 5-3 on page 11](#) and [Table 5-4 on page 11](#). These measurements were done with inductors having a quality factor according to [Table 5-2](#), resulting in estimated matching losses of 1.0 dB at 315 MHz, 1.2 dB at 433.92 MHz and 0.6 dB at 868.3 MHz. These losses can be estimated when calculating the parallel equivalent resistance of the inductor with $R_{\text{loss}} = 2 \times \pi \times f \times L \times Q_L$ and the matching loss with $10 \log(1 + R_p/R_{\text{loss}})$.

With an ideal inductor, for example, the sensitivity at 433.92 MHz/FSK/20 kBaud/ $\pm 16\text{ kHz}$ /Manchester can be improved from -106 dBm to -107.2 dBm . The sensitivity depends on the control logic which examines the incoming data stream. The examination limits must be programmed in control registers 5 and 6. The measurements in [Table 5-3](#) and [Table 5-4 on page 11](#) are based on the values of registers 5 and 6 according to [Table 11-3 on page 58](#).

Figure 5-1. Input Matching to 50Ω

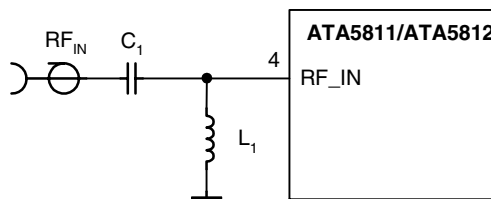


Table 5-2. Input Matching to 50Ω

| f_{RF}/MHz | C_1/pF | L_1/nH | Q_{L1} |
|---------------------|-----------------|-----------------|----------|
| 315 | 2.2 | 56 | 43 |
| 433.92 | 1.8 | 27 | 40 |
| 868.3 | 1.2 | 6.8 | 58 |

Table 5-3. Measured Sensitivity FSK, ± 16 kHz, Manchester, dBm, BER = 10^{-3}

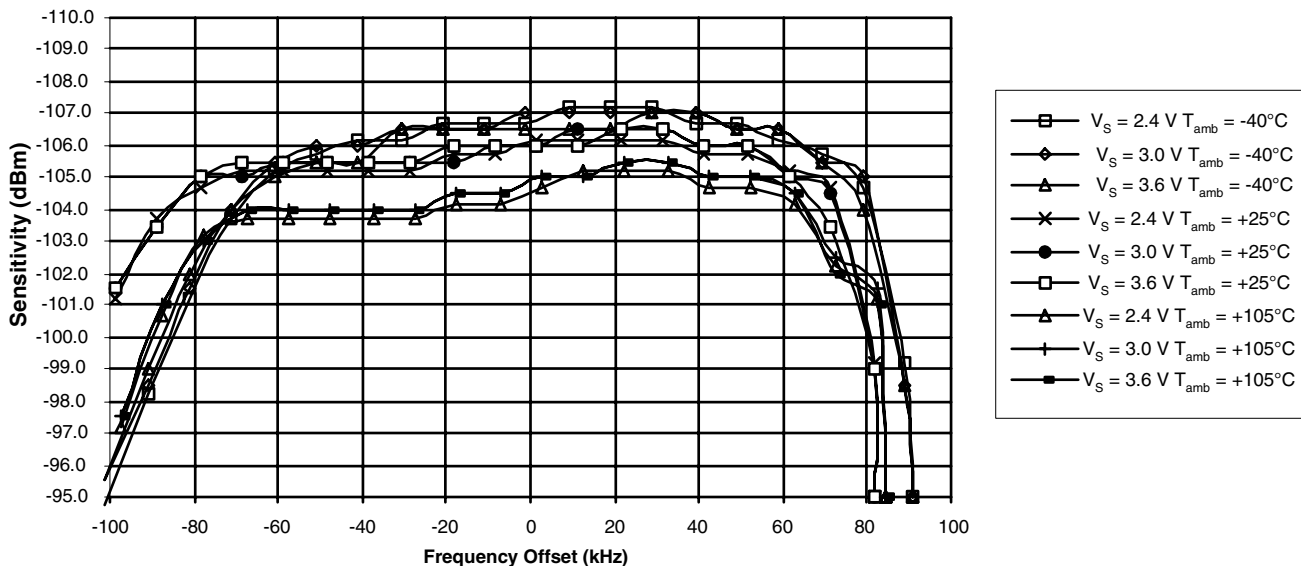
| RF Frequency | BR_Range_0 1.0 kBaud | BR_Range_0 2.4 kBaud | BR_Range_1 5.0 kBaud | BR_Range_2 10 kBaud | BR_Range_3 20 kBaud |
|--------------|-------------------------|-------------------------|-------------------------|------------------------|------------------------|
| 315 MHz | -110.0 dBm | -110.5 dBm | -109.0 dBm | -108.0 dBm | -107.0 dBm |
| 433.92 MHz | -109.0 dBm | -109.5 dBm | -108.0 dBm | -107.0 dBm | -106.0 dBm |
| 868.3 MHz | -106.0 dBm | -106.5 dBm | -105.5 dBm | -104.0 dBm | -103.5 dBm |

Table 5-4. Measured Sensitivity 100% ASK, Manchester, dBm, BER = 10^{-3}

| RF Frequency | BR_Range_0 1.0 kBaud | BR_Range_0 2.4 kBaud | BR_Range_1 5.0 kBaud | BR_Range_2 10 kBaud |
|--------------|-------------------------|-------------------------|-------------------------|------------------------|
| 315 MHz | -117.0 dBm | -117.5 dBm | -115 dBm | -113.5 dBm |
| 433.92 MHz | -116.0 dBm | -116.5 dBm | -114.0 dBm | -112.5 dBm |
| 868.3 MHz | -112.5 dBm | -113.0 dBm | -111.5 dBm | -109.5 dBm |

5.3 Sensitivity versus Supply Voltage, Temperature and Frequency Offset

To calculate the behavior of a transmission system it is important to know the reduction of the sensitivity due to several influences. The most important are frequency offset due to crystal oscillator (XTO) and crystal frequency (XTAL) errors, temperature and supply voltage dependency of the noise figure and IF filter bandwidth of the receiver. Figure 5-2 shows the typical sensitivity at 433.92 MHz/FSK/20kBaud/ ± 16 kHz/Manchester versus the frequency offset between transmitter and receiver with $T_{amb} = -40^{\circ}\text{C}$, $+25^{\circ}\text{C}$ and $+105^{\circ}\text{C}$ and supply voltage $V_{S1} = V_{S2} = 2.4\text{V}$, 3.0V and 3.6V .

Figure 5-2. Measured Sensitivity 433.92 MHz/FSK/20 kBaud/ ± 16 kHz/Manchester versus Frequency Offset, Temperature and Supply Voltage

As can be seen in [Figure 5-2 on page 11](#) the supply voltage has almost no influence. The temperature has an influence of about +1.5/–0.7 dB and a frequency offset of ±65 kHz also influences by about ±1 dB. All these influences, combined with the sensitivity of a typical IC, are then within a range of –103.7 dBm and –107.3 dBm over temperature, supply voltage and frequency offset which is –105.5 dBm ±1.8dB. The integrated IF filter has an additional production tolerance of only ±7 kHz, hence, a frequency offset between the receiver and the transmitter of ±58 kHz can be accepted for XTAL and XTO tolerances.

Note: For the demodulator used in the ATA5811/ATA5812, the tolerable frequency offset does not change with the data frequency, hence, the value of ±58 kHz is valid for up to 1 kBaud.

This small sensitivity spread over supply voltage, frequency offset and temperature is very unusual in such a receiver. It is achieved by an internal, very fast and automatic frequency correction in the FSK demodulator after the IF filter, which leads to a higher system margin. This frequency correction tracks the input frequency very quickly, if however, the input frequency makes a larger step (e.g., if the system changes between different communication partners), the receiver has to be restarted. This can be done by switching back to Idle mode and then again to RX mode. For that purpose, an automatic mode is also available. This automatic mode switches to Idle mode and back into RX mode every time a bit error occurs (see section [“Digital Control Logic” on page 33](#)).

5.4 Frequency Accuracy of the Crystals

The XTO is an amplitude regulated Pierce oscillator with integrated load capacitors. The initial tolerances (due to the frequency tolerance of the XTAL, the integrated capacitors on XTAL1, XTAL2 and the XTO’s initial transconductance gm) can be compensated to a value within ±0.5 ppm by measuring the CLK output frequency and programming the control registers 2 and 3 (see [Table 9-7 on page 36](#) and [Table 9-10 on page 36](#)). The XTO then has a remaining influence of less than ±2 ppm over temperature and supply voltage due to the bandgap controlled gm of the XTO.

The needed frequency stability of the used crystals over temperature and aging is hence $\pm 58 \text{ kHz} / 433.92 \text{ MHz} - 2 \times \pm 2.5 \text{ ppm} = \pm 128.66 \text{ ppm}$ for 433.92 MHz and $\pm 58 \text{ kHz} / 868.3 \text{ MHz} - 2 \times \pm 2.5 \text{ ppm} = \pm 61.8 \text{ ppm}$ for 868.3 MHz. Thus, the used crystals in receiver and transmitter each need to be better than ±64.33 ppm for 433.92 MHz and ±30.9 ppm for 868.3 MHz. In access control systems it may be advantageous to have a more tight tolerance at the base-station in order to relax the requirement for the key fob.

5.5 RX Supply Current versus Temperature and Supply Voltage

[Table 5-5](#) shows the typical supply current at 433.92 MHz of the transceiver in RX mode versus supply voltage and temperature with VS = VS1 = VS2. As you can see the supply current at 2.4V and –40°C is less than the typical one which helps because this is also the operation point where a lithium cell has the worst performance. The typical supply current at 315 MHz or 868.3 MHz in RX mode is about the same as for 433.92 MHz.

Table 5-5. Measured 433.92 MHz Receive Supply Current in FSK Mode

| VS = | 2.4 V | 3.0 V | 3.6 V |
|--------------------------|---------|---------|---------|
| T _{amb} = –40°C | 8.4 mA | 8.8 mA | 9.2 mA |
| T _{amb} = 25°C | 9.9 mA | 10.3 mA | 10.8 mA |
| T _{amb} = 105°C | 11.4 mA | 11.9 mA | 12.4 mA |

5.6 Blocking, Selectivity

As can be seen in [Figure 5-3](#) and [Figure 5-4](#), the receiver can receive signals 3 dB higher than the sensitivity level in presence of very large blockers of -47 dBm/ -34 dBm with small frequency offsets of $\pm 1/ \pm 10$ MHz.

[Figure 5-3](#) shows narrow band blocking and [Figure 5-4](#) wide band blocking characteristics. The measurements were done with a useful signal of 433.92 MHz/FSK/20 kBaud/ ± 16 kHz/Manchester with a level of -106 dBm + 3 dB = -103 dBm which is 3 dB above the sensitivity level. The figures show how much a continuous wave signal can be larger than -103 dBm until the BER is higher than 10^{-3} . The measurements were done at the 50 Ω input according to [Figure 5-1 on page 10](#). At 1 MHz, for example, the blocker can be 56 dB higher than -103 dBm which is -103 dBm + 56 dB = -47 dBm. These values, together with the good intermodulation performance, avoid the need for a SAW filter in the key fob application.

Figure 5-3. Narrow Band 3 dB Blocking Characteristic at 433.92 MHz

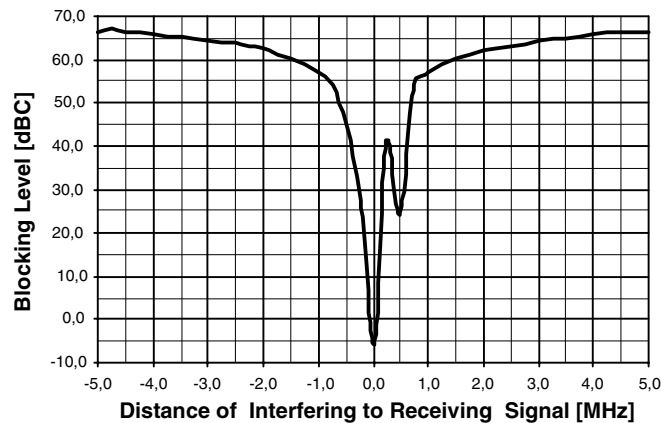


Figure 5-4. Wide Band 3 dB Blocking Characteristic at 433.92 MHz

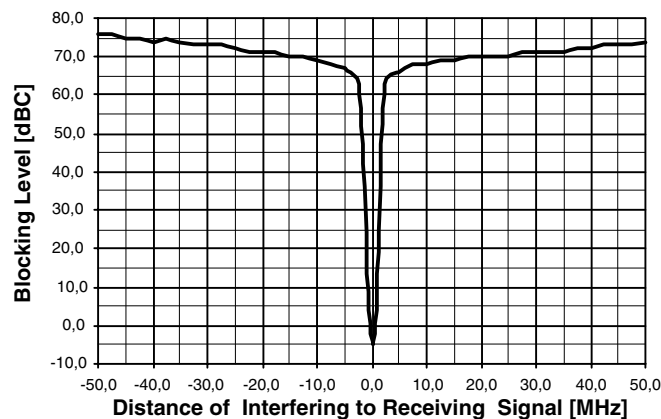


Figure 5-5 shows the blocking measurement close to the received frequency to illustrate the selectivity and image rejection. This measurement was done 6 dB above the sensitivity level with a useful signal of 433.92 MHz/FSK/20kBaud/ ± 16 kHz/ Manchester with a level of $-106 \text{ dBm} + 6 \text{ dB} = -100 \text{ dBm}$. The figure shows to which extent a continuous wave signal can surpass -100 dBm until the BER is higher than 10^{-3} . For example, at 1 MHz the blocker can then be 59 dB higher than -100 dBm which is $-100 \text{ dBm} + 59 \text{ dB} = -41 \text{ dBm}$.

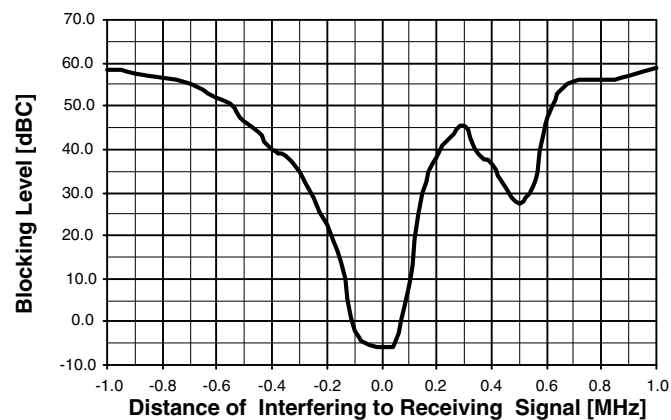
Table 5-6 shows the blocking performance measured relative to -100 dBm for some other frequencies. Note that sometimes the blocking is measured relative to the sensitivity level (dBS) instead of the carrier (dBC).

Table 5-6. Blocking 6 dB Above Sensitivity Level with $\text{BER} < 10^{-3}$

| Frequency Offset | Blocker Level | Blocking |
|---------------------|-------------------|---------------|
| +0.75 MHz | -45 dBm | 55 dBC/61 dBS |
| -0.75 MHz | -45 dBm | 55 dBC/61 dBS |
| +1.5 MHz | -38 dBm | 62 dBC/68 dBS |
| -1.5 MHz | -38 dBm | 62 dBC/68 dBS |
| +10 MHz | -30 dBm | 70 dBC/76 dBS |
| -10 MHz | -30 dBm | 70 dBC/76 dBS |

The ATA5811/ATA5812 can also receive FSK and ASK modulated signals if they are much higher than the 11 dBm . It can typically receive useful signals at 10 dBm . This is often referred to as the nonlinear dynamic range which is the maximum to minimum receiving signal which is 116 dB for 20 kBaud Manchester. This value is useful if two transceivers have to communicate and are very close to each other.

Figure 5-5. Close In 6 dB Blocking Characteristic and Image Response at 433.92 MHz



This high blocking performance makes it even possible for some applications using quarter wave whip antennas to use a simple LC band-pass filter instead of a SAW filter in the receiver. When designing such an LC filter take into account that the 3 dB blocking at $433.92 \text{ MHz}/2 = 216.96 \text{ MHz}$ is 43 dBC and at $433.92 \text{ MHz}/3 = 144.64 \text{ MHz}$ is 48 dBC and at $2 \times (433.92 \text{ MHz} + 226 \text{ kHz}) + -226 \text{ kHz} = 868.066 \text{ MHz}/868.518 \text{ MHz}$ is 56 dBC. And especially that at $3 \times (433.92 \text{ MHz} + 226 \text{ kHz}) + 226 \text{ kHz} = 1302.664 \text{ MHz}$ the receiver has its second LO harmonic receiving frequency with only 12 dBC blocking.

5.7 Inband Disturbance, Data Filter, Quasi Peak Detector, Data Slicer

If a disturbing signal falls into the received band or a blocker is not continuous wave the performance of a receiver strongly depends on the circuits after the IF filter. Hence the demodulator, data filter and data slicer are important in that case.

The data filter of the ATA5811/ATA5812 implies a quasi peak detector. This results in a good suppression of the above mentioned disturbers and exhibits a good carrier to Gaussian noise performance. The required useful signal to disturbing signal ratio to be received with a BER of 10^{-3} is less than 12 dB in ASK mode and less than 3 dB (BR_Range_0 ... BR_Range_2)/6 dB (BR_Range_3) in FSK mode. Due to the many different waveforms possible these numbers are measured for signal as well as for disturbers with peak amplitude values. Note that these values are worst case values and are valid for any type of modulation and modulating frequency of the disturbing signal as well as the receiving signal. For many combinations, lower carrier to disturbing signal ratios are needed.

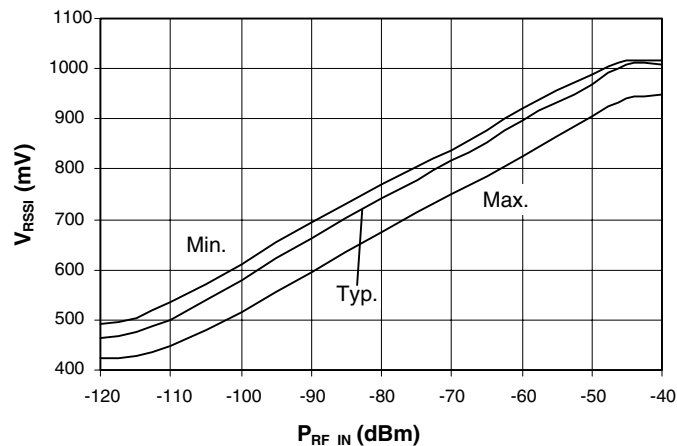
5.8 DEM_OUT Output

The internal raw output signal of the demodulator Demod_Out is available at pin DEM_OUT. DEM_OUT is an open drain output and must be connected to a pull-up resistor if it is used (typically 100 k Ω) otherwise no signal is present at that pin.

5.9 RSSI Output

The output voltage of the pin RSSI is an analog voltage, proportional to the input power level. Using the RSSI output signal, the signal strength of different transmitters can be distinguished. The usable dynamic range of the RSSI amplifier is 70 dB, the input power range $P(RF_{IN})$ is -115 dBm to -45 dBm and the gain is 8 mV/dB. [Figure 5-6 on page 16](#) shows the RSSI characteristic of a typical device at 433.92 MHz with $VS1 = VS2 = 2.4 \text{ V}$ to 3.6 V and $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$ with a matched input according to [Table 5-2 on page 10](#) and [Figure 5-1 on page 10](#). At 868.3 MHz about 2.7 dB more signal level and at 315 MHz about 1 dB less signal level is needed for the same RSSI results.

Figure 5-6. Typical RSSI Characteristic versus Temperature and Supply Voltage



5.10 Frequency Synthesizer

The synthesizer is a fully integrated fractional-N design with internal loop filters for receive and transmit mode. The XTO frequency f_{XTO} is the reference frequency FREF for the synthesizer. The bits FR0 to FR8 in control registers 2 and 3 (see [Table 9-7 on page 36](#) and [Table 9-10 on page 36](#)) are used to adjust the deviation of f_{XTO} . In transmit mode, at 433.92 MHz, the carrier has a phase noise of -111 dBC/Hz at 1 MHz and spurious at FREF of -66 dBC with a high PLL loop bandwidth allowing the direct modulation of the carrier with 20 kBaud Manchester data. Due to the closed loop modulation any spurious caused by this modulation are effectively filtered out as can be seen in [Figure 5-9 on page 18](#). In RX mode the synthesizer has a phase noise of -120 dBC/Hz at 1 MHz and spurious of -75 dBC.

The initial tolerances of the crystal oscillator due to crystal tolerances, internal capacitor tolerances and the parasitics of the board have to be compensated at manufacturing setup with control registers 2 and 3 as can be seen in [Table 6-1 on page 25](#). The other control words for the synthesizer needed for ASK, FSK and receive/transmit switching are calculated internally. The RF (Radio Frequency) resolution is equal to the XTO frequency divided by 16384 which is 777.1 Hz at 315.0 MHz, 808.9 Hz at 433.92 MHz and 818.59 Hz at 868.3 MHz.

5.11 FSK/ASK Transmission

Due to the fast modulation capability of the synthesizer and the high resolution, the carrier can be internally FSK modulated which simplifies the application of the transceiver. The deviation of the transmitted signal is ± 20 digital frequency steps of the synthesizer which is equal to ± 15.54 kHz for 315 MHz, ± 16.17 kHz for 433.92 MHz and ± 16.37 kHz for 868.3 MHz.

Due to closed loop modulation with PLL filtering the modulated spectrum is very clean, meeting ETSI and CEPT regulations when using a simple LC filter for the power amplifier harmonics as it is shown in [Figure 3-1 on page 7](#). In ASK mode the frequency is internally connected to the center of the FSK transmission and the power amplifier is switched on and off to perform the modulation. [Figure 5-7 on page 17](#) to [Figure 5-9 on page 18](#) show the spectrum of the FSK modulation with pseudo random data with 20 kBaud/ ± 16.17 kHz/Manchester and 5 dBm output power.

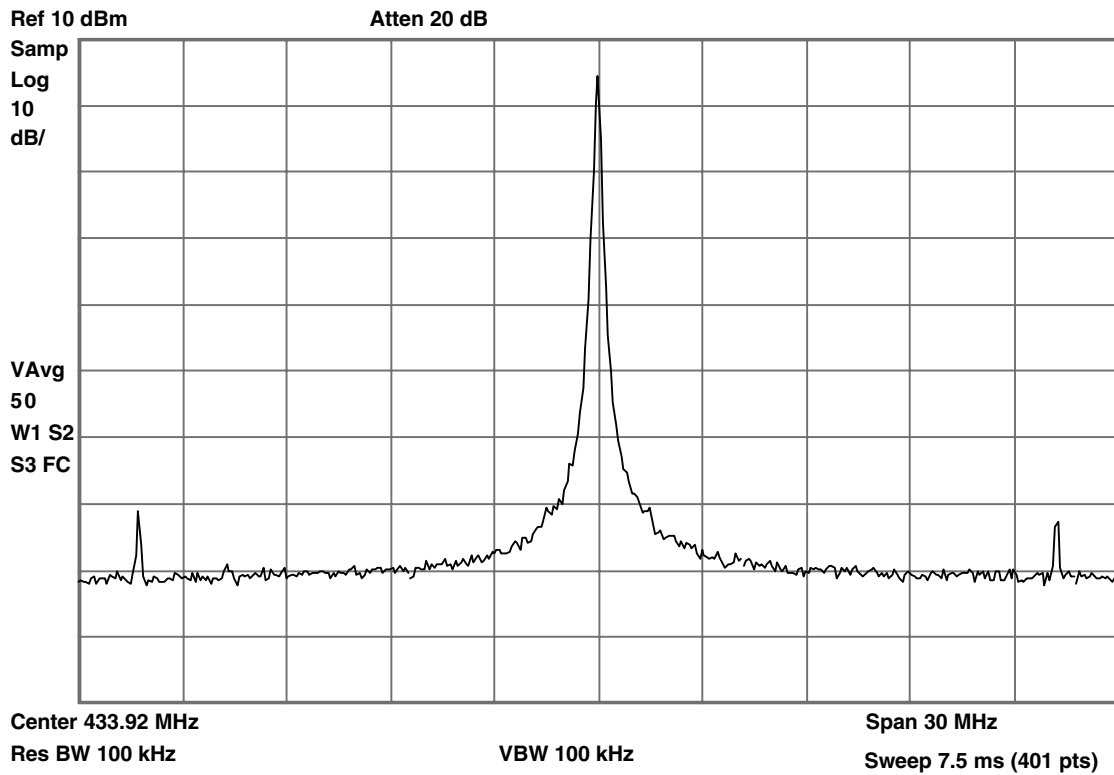
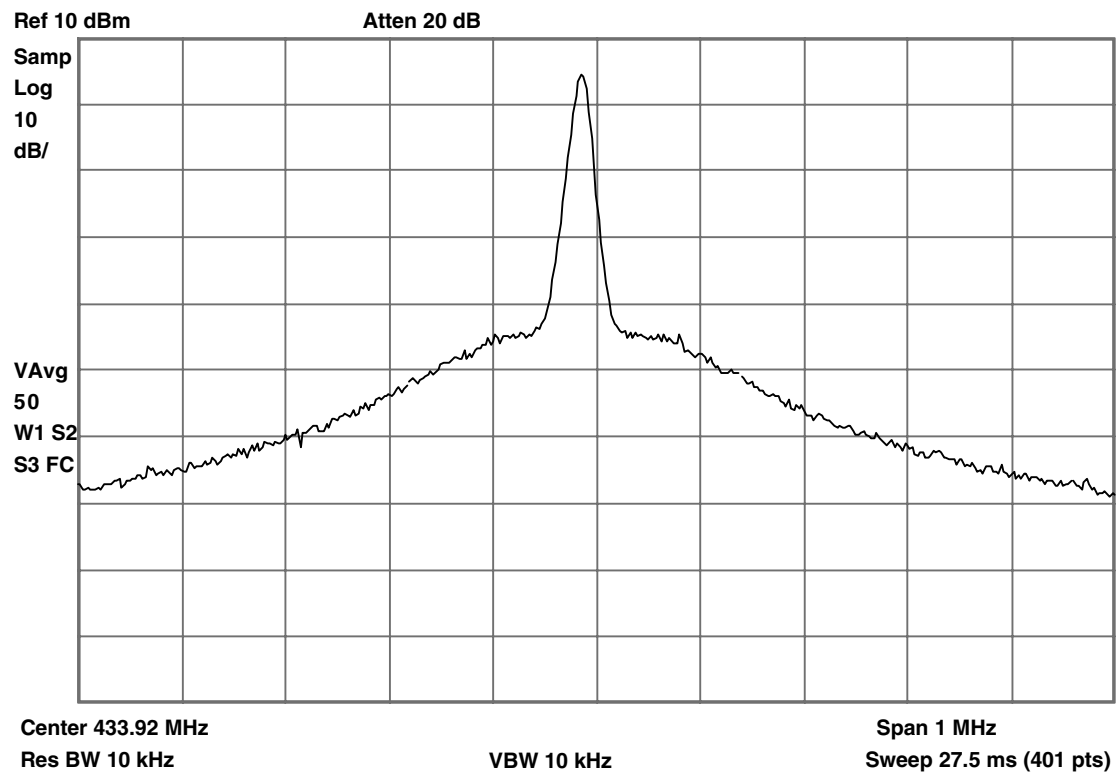
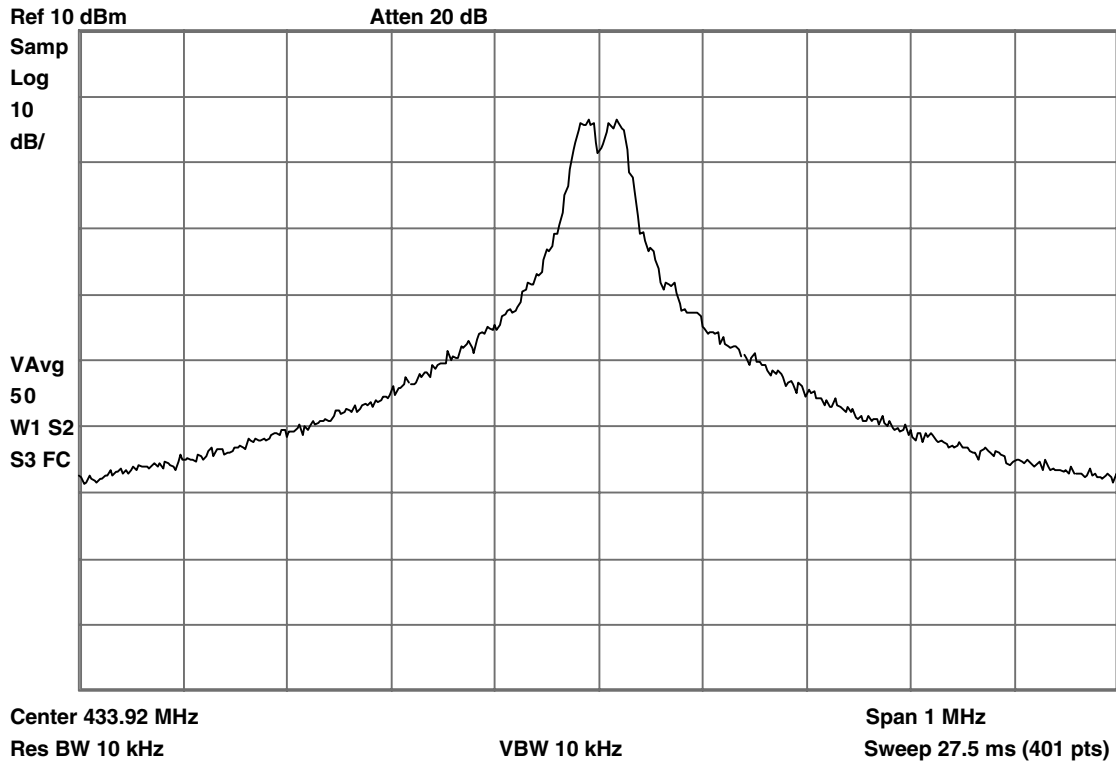
Figure 5-7. FSK-modulated TX Spectrum (20 kBaud/ ± 16.17 kHz/Manchester Code)**Figure 5-8.** Unmodulated TX Spectrum f_{FSK_L} 

Figure 5-9. FSK-modulated TX Spectrum (20 kBaud/ ± 16.17 kHz/Manchester Code)



5.12 Output Power Setting and PA Matching at RF_OUT

The Power Amplifier (PA) is a single-ended open collector stage which delivers a current pulse which is nearly independent of supply voltage, temperature and tolerances due to bandgap stabilization. Resistor R_1 , see [Figure 5-10 on page 19](#), sets a reference current which controls the current in the PA. A higher resistor value results in a lower reference current, a lower output power and a lower current consumption of the PA. The usable range of R_1 is 15 k Ω to 56 k Ω . Pin PWR_H switches the output power range between about 0 dBm to 5 dBm (PWR_H = GND) and 5 dBm to 10 dBm (PWR_H = AVCC) by multiplying this reference current with a factor 1 (PWR_H = GND) and 2.5 (PWR_H = AVCC) which corresponds to about 5 dB more output power.

If the PA is switched off in TX mode, the current consumption without output stage with $VS1 = VS2 = 3V$, $T_{amb} = 25^\circ C$ is typically 6.5 mA for 868.3 MHz and 6.95 mA for 315 MHz and 433.92 MHz.

The maximum output power is achieved with optimum load resistances R_{Lopt} according to [Table 5-7 on page 20](#) with compensation of the 1.0 pF output capacitance of the RF_OUT pin by absorbing it into the matching network consisting of L_1 , C_1 , C_3 as shown in [Figure 5-10 on page 19](#). There must be also a low resistive DC path to AVCC to deliver the DC current of the power amplifier's last stage. The matching of the PA output was done with the circuit according to [Figure 5-10 on page 19](#) with the values in [Table 5-7 on page 20](#). Note that value changes of these elements may be necessary to compensate for individual board layouts.

Example:

According to [Table 5-7 on page 20](#), with a frequency of 433.92 MHz and output power of 11 dBm the overall current consumption is typically 17.8 mA hence the PA needs $17.8 \text{ mA} - 6.95 \text{ mA} = 10.85 \text{ mA}$ in this mode which corresponds to an overall power amplifier efficiency of the PA of $(10^{(11\text{dBm}/10)} \times 1 \text{ mW}) / (3\text{V} \times 10.85 \text{ mA}) \times 100\% = 38.6\%$ in this case.

Using a higher resistor in this example of $R_1 = 1.091 \times 22 \text{ k}\Omega = 24 \text{ k}\Omega$ results in 9.1% less current in the PA of $10.85 \text{ mA} / 1.091 = 9.95 \text{ mA}$ and $10 \times \log(1.091) = 0.38 \text{ dB}$ less output power if using a new load resistance of $300 \Omega \times 1.091 = 327 \Omega$. The resulting output power is then $11 \text{ dBm} - 0.38 \text{ dB} = 10.6 \text{ dBm}$ and the overall current consumption is $6.95 \text{ mA} + 9.95 \text{ mA} = 16.9 \text{ mA}$.

The values of [Table 5-7 on page 20](#) were measured with standard multi-layer chip inductors with quality factors Q according to [Table 5-7 on page 20](#). Looking to the 433.92 MHz/11 dBm case with the quality factor of $Q_{L1} = 43$ the loss in this inductor is estimated with the parallel equivalent resistance of the inductor $R_{\text{loss}} = 2 \times \pi \times f \times L \times Q_{L1}$ and the matching loss with $10 \log(1 + R_{\text{Lopt}}/R_{\text{loss}})$ which is equal to 0.32 dB losses in this inductor. Taking this into account the PA efficiency is then 42% instead of 38.6%.

Be aware that the high power mode (PWR_H = AVCC) can only be used with a supply voltage higher than 2.7V, whereas the low power mode (PWR_H = GND) can be used down to 2.4V as can be seen in the section [“Electrical Characteristics: General” on page 63](#).

The supply blocking capacitor C_2 (10 nF) has to be placed close to the matching network because of the RF current flowing through it.

Figure 5-10. Power Setting and Output Matching

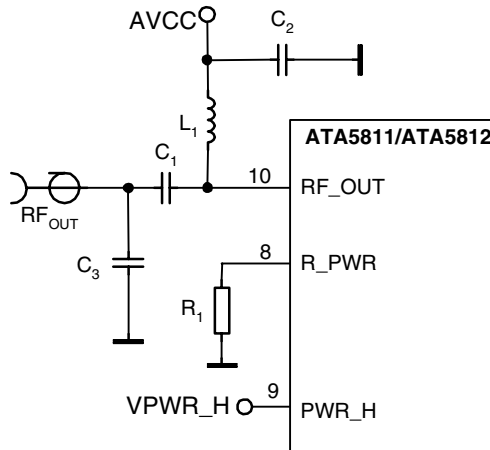


Table 5-7. Measured Output Power and Current Consumption with VS1 = VS2 = 3 V, T_{amb} = 25°C

| Frequency (MHz) | TX Current (mA) | Output Power (dBm) | R1 (kΩ) | VPWR_H | R _{Lopt} (Ω) | L1 (nH) | Q _{L1} | C1 (pF) | C3 (pF) |
|-----------------|-----------------|--------------------|---------|--------|-----------------------|---------|-----------------|---------|---------|
| 315 | 8.5 | 0.4 | 56 | GND | 2500 | 82 | 28 | 1.5 | 0 |
| 315 | 10.5 | 5.7 | 27 | GND | 920 | 68 | 32 | 2.2 | 0 |
| 315 | 16.7 | 10.5 | 27 | AVCC | 350 | 56 | 35 | 3.9 | 0 |
| 433.92 | 8.6 | 0.1 | 56 | GND | 2300 | 56 | 40 | 0.75 | 0 |
| 433.92 | 11.2 | 6.2 | 22 | GND | 890 | 47 | 38 | 1.5 | 0 |
| 433.92 | 17.8 | 11 | 22 | AVCC | 300 | 33 | 43 | 2.7 | 0 |
| 868.3 | 9.3 | -0.3 | 33 | GND | 1170 | 12 | 58 | 1.0 | 3.3 |
| 868.3 | 11.5 | 5.4 | 15 | GND | 471 | 15 | 54 | 1.0 | 0 |
| 868.3 | 16.3 | 9.5 | 22 | AVCC | 245 | 10 | 57 | 1.5 | 0 |

5.13 Output Power and TX Supply Current versus Supply Voltage and Temperature

Table 5-8 on page 20 shows the measurement of the output power for a typical device with VS1 = VS2 = VS in the 433.92 MHz and 6.2 dBm case versus temperature and supply voltage measured according to Figure 5-10 on page 19 with components according to Table 5-7. As opposed to the receiver sensitivity the supply voltage has here the major impact on output power variations because of the large signal behavior of a power amplifier. Thus, a two battery system with voltage regulator or a 5V system shows much less variation than a 2.4V to 3.6V one battery system because the supply voltage is then well within 3.0V and 3.6V.

The reason is that the amplitude at the output RF_OUT with optimum load resistance is AVCC – 0.4V and the power is proportional to (AVCC – 0.4V)² if the load impedance is not changed. This means that the theoretical output power reduction if reducing the supply voltage from 3.0V to 2.4V is $10 \log \left(\frac{(3V - 0.4V)^2}{(2.4V - 0.4V)^2} \right) = 2.2 \text{ dB}$. Table 5-8 shows that principle behavior in the measurement. This is not the same case for higher voltages since here increasing the supply voltage from 3V to 3.6V should theoretical increase the power by 1.8 dB but only 0.8 dB in the measurement shows that the amplitude does not increase with the supply voltage because the load impedance is optimized for 3V and the output amplitude stays more constant.

Table 5-8. Measured Output Power and Supply Current at 433.92 MHz, PWR_H = GND

| VS = | 2.4 V | 3.0 V | 3.6 V |
|---------------------------|---------------------|---------------------|---------------------|
| T _{amb} = -40°C | 10.19 mA 3.8 dBm | 10.19 mA 5.5 dBm | 10.78 mA 6.2 dBm |
| T _{amb} = +25°C | 10.62 mA 4.6 dBm | 11.19 mA 6.2 dBm | 11.79 mA 7.1 dBm |
| T _{amb} = +105°C | 11.4 mA 3.8 dBm | 12.02 mA 5.4 dBm | 12.73 mA 6.3 dBm |

Table 5-9 on page 21 shows the relative changes of the output power of a typical device compared to 3.0V/25°C. As can be seen a temperature change to -40° as well as to +105° reduces the power by less than 1 dB due to the bandgap regulated output current. Measurements of all the cases in Table 5-7 on page 20 over temperature and supply voltage have shown about the same relative behavior as shown in Table 5-9 on page 21.

Table 5-9. Measurements of Typical Output Power Relative to 3V/25°

| VS = | 2.4V | 3.0V | 3.6V |
|---------------------------|---------|---------|---------|
| T _{amb} = -40°C | -2.4 dB | -0.7 dB | 0 dB |
| T _{amb} = +25°C | -1.6 dB | 0 dB | +0.9 dB |
| T _{amb} = +105°C | -2.4 dB | -0.8 dB | +0.1 dB |

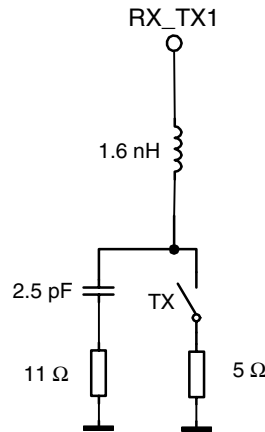
5.14 RX/TX Switch

The RX/TX switch decouples the LNA from the PA in TX mode, and directs the received power to the LNA in RX mode. To do this, it has a low impedance to GND in TX mode and a high impedance to GND in RX mode. To design a proper RX/TX decoupling a linear simulation tool for radio frequency design together with the measured device impedances of [Table 5-1 on page 10](#), [Table 5-7 on page 20](#), [Table 5-10](#) and [Table 5-11 on page 22](#) should be used, but the exact element values have to be found on board. [Figure 5-11 on page 21](#) shows an approximate equivalent circuit of the switch. The principal switching operation is described here according to the application of [Figure 2-1 on page 6](#). The application of [Figure 3-1 on page 7](#) works similarly.

Table 5-10. Impedance of the RX/TX Switch RX_TX2 Shorted to GND

| Frequency | Z(RX_TX1) TX Mode | Z(RX_TX1) RX Mode |
|------------|-------------------|-------------------|
| 315 MHz | (4.8 + j3.2)Ω | (11.3 – j214)Ω |
| 433.92 MHz | (4.5 + j4.3)Ω | (10.3 – j153)Ω |
| 868.3 MHz | (5 + j9)Ω | (8.9 – j73)Ω |

Figure 5-11. Equivalent Circuit of the Switch



5.15 Matching Network in TX Mode

In TX mode the 20 mm long and 0.4 mm wide transmission line which is much shorter than $\lambda/4$ is approximately switched in parallel to the capacitor C_9 to GND. The antenna connection between C_8 and C_9 has an impedance of about 50 Ω looking from the transmission line into the loop antenna with pin RF_OUT, L_2 , C_{10} , C_8 and C_9 connected (using a C_9 without the added 7.6 pF as discussed later). The transmission line can be approximated with a 16 nH inductor in series with a 1.5 Ω resistor, the closed switch can be approximated according to [Table 5-10 on page 21](#) with the series connection of 1.6 nH and 5 Ω in this mode. To have a parallel resonant high impedance circuit with little RF power going into it looking from the loop antenna into the transmission line a capacitor of about 7.6 pF to GND is needed at the beginning of the transmission line (this capacitor is later absorbed into C_9 which is then higher as needed for 50 Ω transformation). To keep the 50 Ω impedance in RX mode at the end of this transmission line C_7 has to be also about 7.6 pF. This reduces the TX power by about 0.5 dB at 433.92 MHz compared to the case where the LNA path is completely disconnected.

5.16 Matching Network in RX Mode

In RX mode the RF_OUT pin has a high impedance of about 7 k Ω in parallel with 1.0 pF at 433.92 MHz as can be seen in [Table 5-11 on page 22](#). This together with the losses of the inductor L_2 with 120 nH and $Q_{L2} = 25$ gives about 3.7 k Ω loss impedance at RF_OUT. Since the optimum load impedance in TX mode for the power amplifier at RF_OUT is 890 Ω the loss associated with the inductor L_2 and the RF_OUT pin can be estimated to be $10 \times \log(1 + 890/3700) = 0.95$ dB compared to the optimum matched loop antenna without L_2 and RF_OUT. The switch represents, in this mode at 433.92 MHz, about an inductor of 1.6 nH in series with the parallel connection of 2.5 pF and 2.0 k Ω . Since the impedance level at pin RX_TX1 in RX mode is about 50 Ω this only negligibly dampens the received signal by about 0.1 dB. When matching the LNA to the loop antenna the transmission line and the 7.6 pF part of C_9 has to be taken into account when choosing the values of C_{11} and L_1 so that the impedance seen from the loop antenna into the transmission line with the 7.6 pF capacitor connected is 50 Ω . Since the loop antenna in RX mode is loaded by the LNA input impedance the loaded Q of the loop antenna is lowered by about a factor of 2 in RX mode hence the antenna bandwidth is higher than in TX mode.

Table 5-11. Impedance RF_OUT Pin in RX Mode

| Frequency | Z(RF_OUT)RX | R_p/C_p |
|------------|-------------------------------|-----------------------|
| 315 MHz | 36 Ω – j 502 Ω | 7 k Ω / 1.0 pF |
| 433.92 MHz | 19 Ω – j 366 Ω | 7 k Ω / 1.0 pF |
| 868.3 MHz | 2.8 Ω – j 141 Ω | 7 k Ω / 1.3 pF |

Note that if matching to 50 Ω , like in [Figure 3-1 on page 7](#), a high Q wire wound inductor with a $Q > 70$ should be used for L_2 to minimize its contribution to RX losses which will otherwise be dominant. The RX and TX losses will be in the range of 1.0 dB there.

6. XTO

The XTO is an amplitude regulated Pierce oscillator type with integrated load capacitances (2×18 pF with a tolerance of $\pm 17\%$) hence $C_{Lmin} = 7.4$ pF and $C_{Lmax} = 10.6$ pF. The XTO oscillation frequency f_{XTO} is the reference frequency FREF for the fractional-N synthesizer. When designing the system in terms of receiving and transmitting frequency offset the accuracy of the crystal and XTO have to be considered.

The synthesizer can adjust the local oscillator frequency for more than ± 150 ppm at 433.92 MHz/315 MHz and up to ± 118 ppm at 868.3 MHz of initial frequency error in f_{XTO} . This is done at nominal supply voltage and temperature with the control registers 2 and 3 (see [Table 9-7 on page 36](#) and [Table 9-10 on page 36](#)). The remaining local oscillator tolerance at nominal supply voltage and temperature is then $< \pm 0.5$ ppm. A XTO frequency error of ± 150 ppm/ ± 118 ppm can hence be tolerated due to the crystal tolerance at 25°C and the tolerances of C_{L1} and C_{L2} . The XTO's gm has very low influence of less than ± 2 ppm on the frequency at nominal supply voltage and temperature.

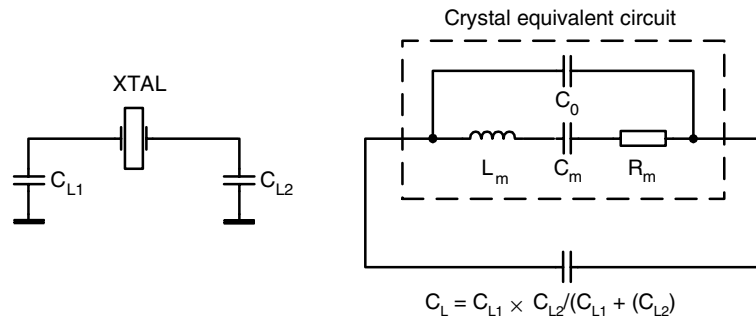
Over temperature and supply voltage, the XTO's additional pulling is only ± 2 ppm if $C_m \leq 7$ fF. The XTAL versus temperature and its aging is then the main source of frequency error in the local oscillator.

The XTO frequency depends on XTAL properties and the load capacitances $C_{L1,2}$ at pin XTAL1 and XTAL2. The pulling of f_{XTO} from the nominal f_{XTAL} is calculated using the following formula:

$$P = \frac{C_m}{2} \times \frac{C_{LN} - C_L}{(C_0 + C_{LN}) \times (C_0 + C_L)} \times 10^6 \text{ ppm.}$$

C_m is the crystal's motional, C_0 the shunt and C_{LN} the nominal load capacitance of the XTAL found in its data sheet. C_L is the total actual load capacitance of the crystal in the circuit and consists of C_{L1} and C_{L2} in series connection.

Figure 6-1. XTAL with Load Capacitance



With $C_m \leq 14$ fF, $C_0 \geq 1.5$ pF, $C_{LN} = 9$ pF and $C_L = 7.6$ pF to 10.6 pF the pulling amounts to $P \leq \pm 100$ ppm and with $C_m \leq 7$ fF, $C_0 \geq 1.5$ pF, $C_{LN} = 9$ pF and $C_L = 7.4$ pF to 10.6 pF the pulling is $P \leq \pm 50$ ppm.

Since typical crystals have less than ± 50 ppm tolerance at 25° the compensation is not critical.

C_0 of the XTAL has to be lower than $C_{Lmin}/2 = 3.8$ pF for a Pierce oscillator type in order to not enter the steep region of pulling versus load capacitance where there is a risk of an unstable oscillation.

To ensure proper start-up behavior the small signal gain and thus the negative resistance provided by this XTO at start is very large, for example oscillation starts up even in worst case with a crystal series resistance of 1.5 k Ω at $C_0 \leq 2.2$ pF with this XTO. The negative resistance is approximately given by

$$\text{Re}\{Z_{\text{xtocore}}\} = \text{Re}\left\{\frac{Z_1 \times Z_3 + Z_2 \times Z_3 + Z_1 \times Z_2 \times g_m}{Z_1 + Z_2 + Z_3 + Z_1 \times Z_2 \times g_m}\right\}$$

with Z_1 , Z_2 as complex impedances at pin XTAL1 and XTAL2 hence

$$Z_1 = -j/(2 \times \pi \times f_{\text{XTO}} \times C_{L1}) + 5\Omega \text{ and } Z_2 = -j/(2 \times \pi \times f_{\text{XTO}} \times C_{L2}) + 5\Omega$$

Z_3 consists of crystals C_0 in parallel with an internal 110 k Ω resistor hence

$Z_3 = -j/(2 \times \pi \times f_{\text{XTO}} \times C_0) / 110 \text{ k}\Omega$, g_m is the internal transconductance between XTAL1 and XTAL2 with typically 19 ms at 25°C.

With $f_{\text{XTO}} = 13.5$ MHz, $g_m = 19$ ms, $CL = 9$ pF, $C_0 = 2.2$ pF this results in a negative resistance of about 2 k Ω . The worst case for technological, supply voltage and temperature variations is then for $C_0 \leq 2.2$ pF always higher than 1.5 k Ω .

Due to the large gain at start the XTO is able to meet a very low start-up time. The oscillation start-up time can be estimated with the time constant τ .

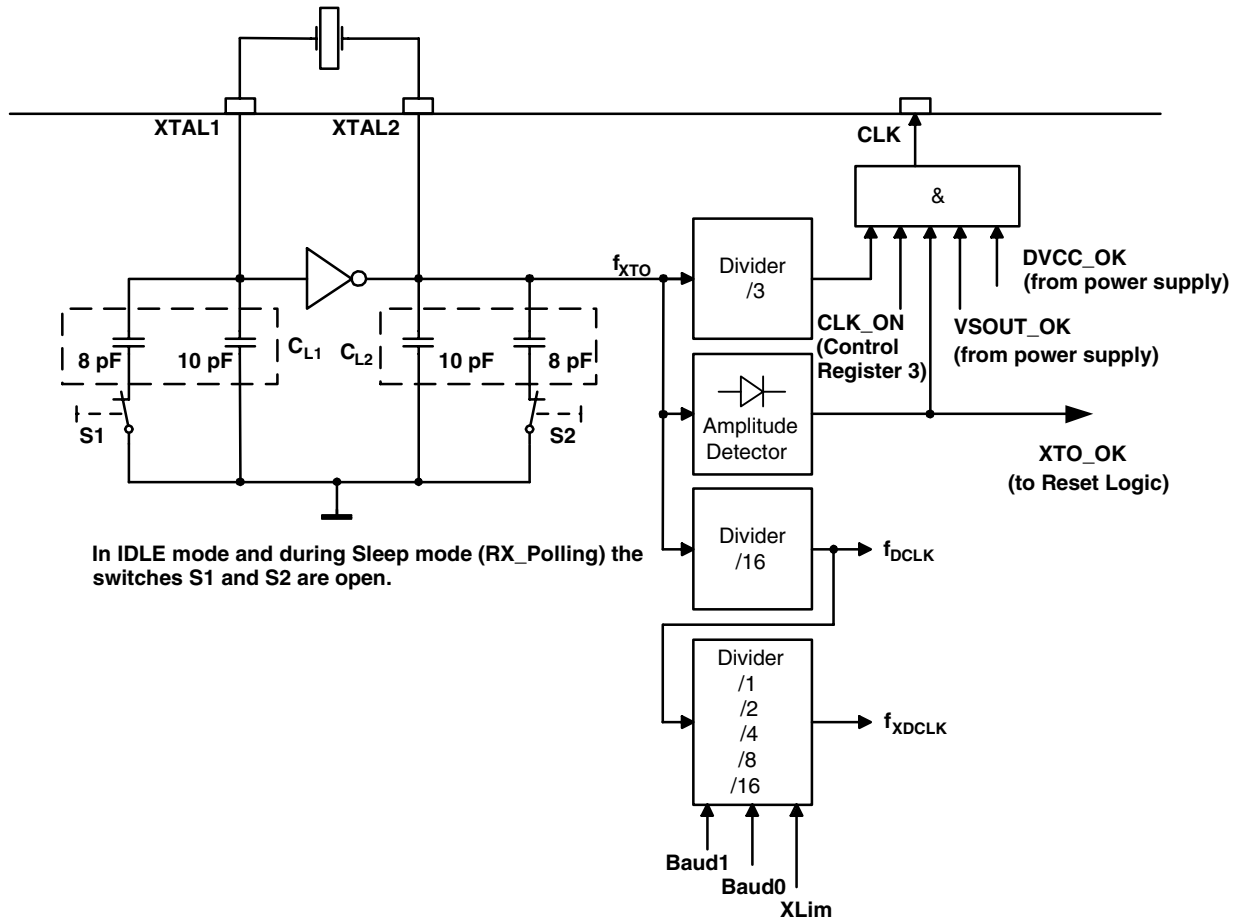
$$\tau = \frac{2}{4 \times \pi^2 \times f_m^2 \times C_m \times (\text{Re}(Z_{\text{xtocore}}) + R_m)}$$

After 10 τ to 20 τ an amplitude detector detects the oscillation amplitude and sets XTO_OK to High if the amplitude is large enough, this sets N_RESET to High and activates the CLK output if CLK_ON in control register 3 is High (see [Table 9-7 on page 36](#)). Note that the necessary conditions of the VSOUT and DVCC voltage also have to be fulfilled (see [Figure 6-2 on page 25](#) and [Figure 7-1 on page 27](#)).

To save current in Idle and sleep mode, the load capacitors partially are switched off in this modes with S1 and S2 seen in [Figure 6-2 on page 25](#).

It is recommended to use a crystal with $C_m = 4.0$ fF to 7.0 fF, $C_{LN} = 9$ pF, $R_m < 120\Omega$ and $C_0 = 1.5$ pF to 2.2 pF.

Figure 6-2. XTO Block Diagram



To find the right values used in the control registers 2 and 3 (see [Table 9-7 on page 36](#) and [Table 9-10 on page 36](#)) the relationship between f_{XTO} and the f_{RF} is shown in [Table 6-1](#). To determine the right content the frequency at pin CLK as well as the output frequency at RF_OUT in ASK mode can be measured, then the FREQ value can be calculated according to [Table 6-1](#) so that f_{RF} is exactly the desired radio frequency

Table 6-1. Calculation of f_{RF}

| Frequency (MHz) | Pin 6 433_N868 | CREG1 Bit(4) FS | f_{XTO} (MHz) | $f_{RF} = f_{TX_ASK} = f_{RX}$ | $f_{TX_FSK_L}$ | $f_{TX_FSK_H}$ |
|-----------------|-------------------|-----------------------|-----------------|---|------------------------------|------------------------------|
| 433.92 | AVCC | 0 | 13.25311 | $f_{XTO} \times \left(32, 5 + \frac{FREQ + 20,5}{16384} \right)$ | $f_{RF} - 16.17 \text{ kHz}$ | $f_{RF} + 16.17 \text{ kHz}$ |
| 868.3 | GND | 0 | 13.41191 | $f_{XTO} \times \left(64, 5 + \frac{FREQ + 20,5}{16384} \right)$ | $f_{RF} - 16.37 \text{ kHz}$ | $f_{RF} + 16.37 \text{ kHz}$ |
| 315.0 | AVCC | 1 | 12.73193 | $f_{XTO} \times \left(24, 5 + \frac{FREQ + 20,5}{16384} \right)$ | $f_{RF} - 15.54 \text{ kHz}$ | $f_{RF} + 15.54 \text{ kHz}$ |

The variable FREQ depends on FREQ2 and FREQ3, which are defined by the bits FR0 to FR8 in control register 2 and 3 and is calculated as follows:

$$\text{FREQ} = 3584 + \text{FREQ2} + \text{FREQ3}$$

Only the range of FREQ = 3803 to 4053 of this register should be used because otherwise harmonics of f_{XTO} and f_{CLK} can cause interference with the received signals (FREQ_min = 3803, FREQ_max = 4053). The resulting tuning range is ± 118 ppm at 868.3 MHz and more than ± 150 ppm at 433.92 MHz or 315 MHz.

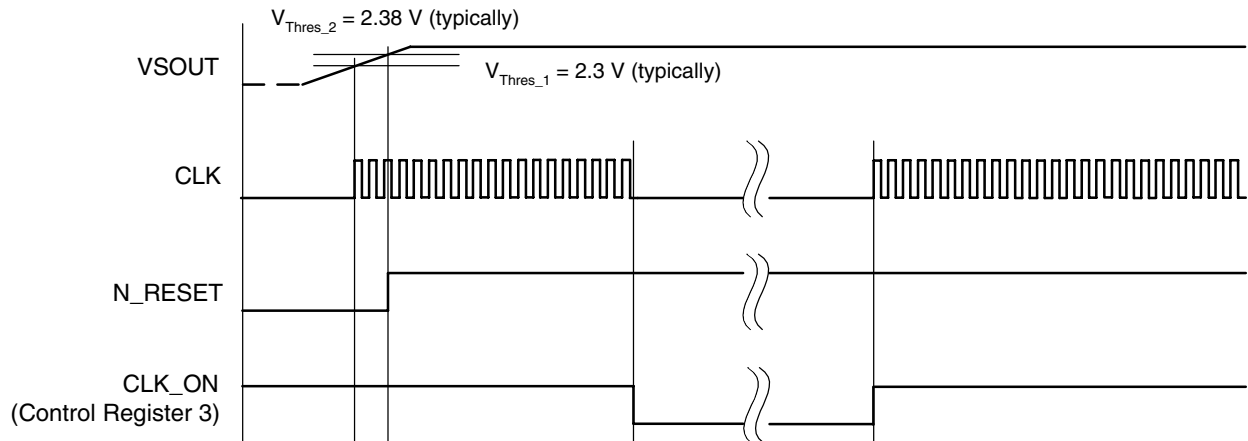
6.1 Pin CLK

Pin CLK is an output to clock a connected microcontroller. The clock frequency f_{CLK} is calculated as follows:

$$f_{\text{CLK}} = \frac{f_{\text{XTO}}}{3}$$

Because the enabling of pin CLK is asynchronous the first clock cycle may be incomplete. The signal at CLK output has a nominal 50% duty cycle.

Figure 6-3. Clock Timing



6.2 Basic Clock Cycle of the Digital Circuitry

The complete timing of the digital circuitry is derived from one clock. According to [Figure 6-2 on page 25](#), this clock cycle T_{DCLK} is derived from the crystal oscillator (XTO) in combination with a divider.

$$f_{\text{DCLK}} = \frac{f_{\text{XTO}}}{16}$$

T_{DCLK} controls the following application relevant parameters:

- Timing of the polling circuit including Bit-check
- TX baud rate

The clock cycle of the Bit-check and the TX baud rate depends on the selected baud-rate range (BR_Range) which is defined in control register 6 (see [Table 9-20 on page 39](#)) and XLim which is defined in control register 4 (see [Table 9-13 on page 37](#)). This clock cycle T_{XDCLK} is defined by the following formulas for further reference:

BR_Range \Rightarrow

$$\text{BR_Range 0: } T_{XDCLK} = 8 \times T_{DCLK} \times X\text{Lim}$$

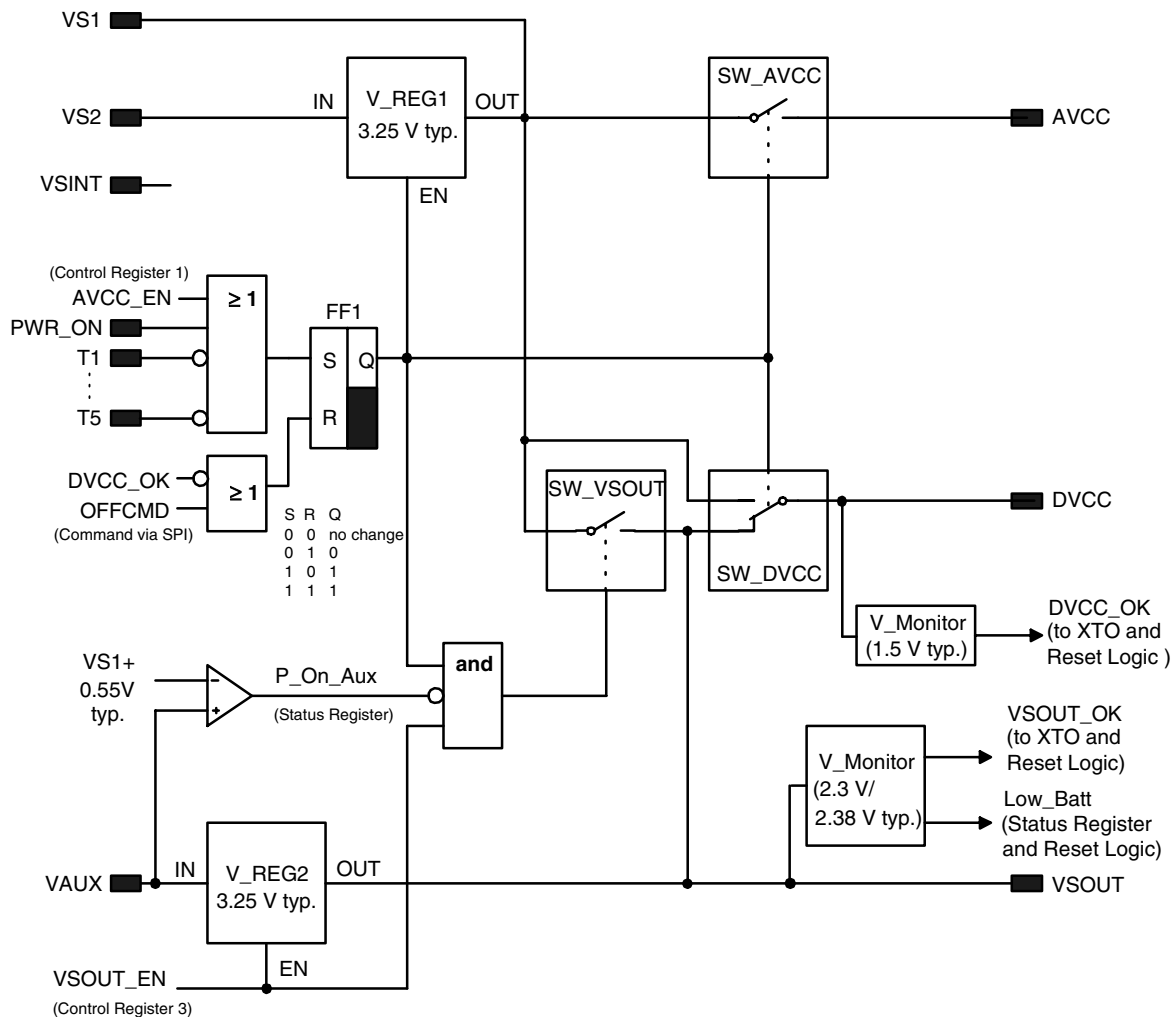
$$\text{BR_Range 1: } T_{XDCLK} = 4 \times T_{DCLK} \times X\text{Lim}$$

$$\text{BR_Range 2: } T_{XDCLK} = 2 \times T_{DCLK} \times X\text{Lim}$$

$$\text{BR_Range 3: } T_{XDCLK} = 1 \times T_{DCLK} \times X\text{Lim}$$

7. Power Supply

Figure 7-1. Power Supply



The supply voltage range of the ATA5811/ATA5812 is 2.4V to 3.6V or 4.4V to 6.6V.

Pin VS1 is the supply voltage input for the range 2.4V to 3.6V and is used in battery applications using a single lithium 3V cell. Pin VS2 is the voltage input for the range 4.4V to 6.6V (2 Battery Application and Car Applications) in this case the voltage regulator V_REG1 regulates VS1 to typically 3.25 V. If the voltage regulator is active a blocking capacitor of 2.2 μ F has to be connected to VS1.

Pin VAUX is an input for an additional auxiliary voltage supply and can be connected e.g., to an inductive supply (see [Figure 7-6 on page 33](#)). This input can only be used together with a rectifier or as in the application of [Figure 3-1 on page 7](#) and must otherwise be left open.

Pin VSINT is the voltage input for the Microcontroller_Interface and must be connected to the power supply of the microcontroller. The voltage range of V_{VSINT} is 2.4V to 5.25V (see [Figure 7-5 on page 32](#) and [Figure 7-6 on page 33](#)).

AVCC is the internal operation voltage of the RF transceiver and is feed via the switch SW_AVCC by VS1. AVCC must be blocked with a 68 nF capacitor (see [Figure 2-1 on page 6](#), [Figure 3-1 on page 7](#) and [Figure 4-1 on page 8](#)).

DVCC is the internal operation voltage of the digital control logic and is feed via the switch SW_DVCC by VS1 or VSOUT. DVCC must be blocked on pin DVCC with 68 nF (see [Figure 2-1 on page 6](#), [Figure 3-1 on page 7](#) and [Figure 4-1 on page 8](#)).

Pin VSOUT is a power supply output voltage for external devices (e.g., microcontroller) and is fed via the switch SW_VSOUT by VS1 or via V_REG2 by the a auxiliary voltage supply VAUX. The voltage regulator V_REG2 regulates VSOUT to typically 3.25V. If the voltage regulator is active a blocking capacitor of 2.2 μ F has to be connected to VSOUT. VSOUT can be switched off by the VSOUT_EN bit in control register 3 and is then reactivated by conditions found in [Figure 7-2 on page 29](#).

Pin N_RESET is set to low if the voltage V_{VSOUT} at pin VSOUT drops below 2.3V (typically) and can be used as a reset signal for a connected microcontroller (see [Figure 7-3 on page 31](#) and [Figure 7-4 on page 32](#)).

Pin PWR_ON is an input to switch on the transceiver (active high).

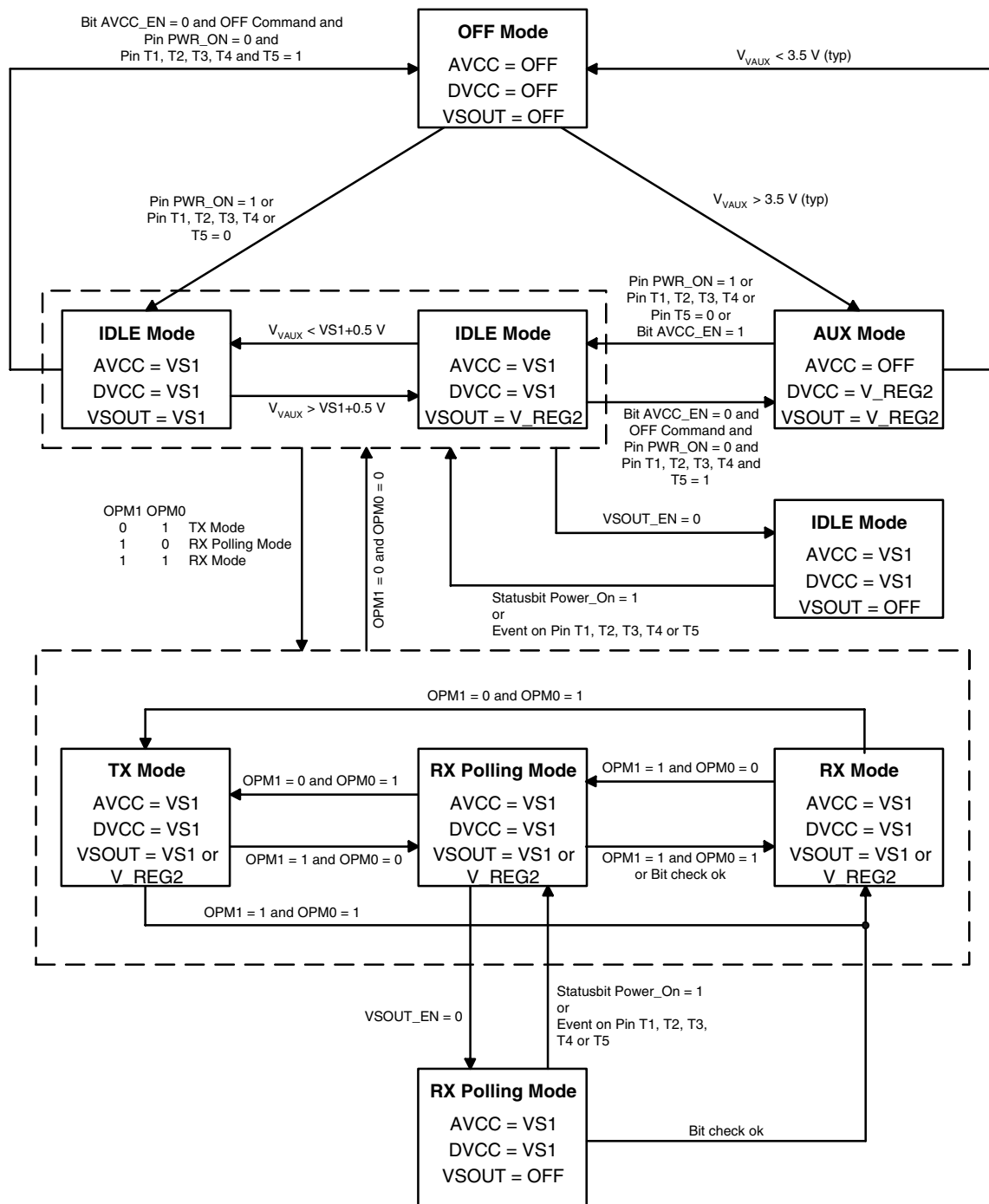
Pin T1 to T5 are inputs for push buttons and can also be used to switch on the transceiver (active low).

For current consumption reasons it is recommended to set T1 to T5 to GND or PWR_ON to VCC only temporarily. Otherwise an additional current flows.

There are two voltage monitors generating the following signals (see [Figure 7-1 on page 27](#)):

- DVCC_OK if DVCC > 1.5V typically
- VSOUT_OK if VSOUT > V_{Thres1} (2.3V typically)
- Low_Batt if VSOUT < V_{Thres2} (2.38V typically)

Figure 7-2. Flow Chart Operation Modes



7.1 OFF Mode

After connecting the power supply (battery) to pin VS1 and/or VS2 and if the voltage on pin VAUX $V_{VAUX} < 3.5\text{ V}$ (typically) the transceiver is in OFF mode. In OFF mode AVCC, DVCC and VSOUT are disabled, resulting in very low power consumption (I_{S_OFF} is typically 10 nA). In OFF mode the transceiver is not programmable via the 4-wire serial interface.

7.2 AUX Mode

The transceiver changes from OFF mode to AUX mode if the voltage at pin VAUX $V_{VAUX} > 3.5V$ (typically). In AUX mode DVCC and VSOUT are connected to the auxiliary power supply input (VAUX) via the voltage regulator V_REG2. In AUX mode the transceiver is programmable via the 4-wire serial interface, but no RX or TX operations are possible because AVCC = OFF.

The state transition OFF mode to AUX mode is indicated by an interrupt at pin IRQ and the status bit P_On_Aux = 1.

7.3 Idle Mode

In Idle mode AVCC and DVCC are connected to the battery voltage (VS1).

From OFF mode the transceiver changes to Idle mode if pin PWR_ON is set to 1 or pin T1, T2, T3, T4 or T5 is set to 0. This state transition is indicated by an interrupt at pin IRQ and the status bits Power_On = 1 or ST1, ST2, ST3, ST4 or ST5 = 1.

From AUX mode the transceiver changes to Idle mode by setting AVCC_EN = 1 in control register 1 via the 4-wire serial interface or if pin PWR_ON is set to 1 or pin T1, T2, T3, T4 or T5 is set to 0.

VSOUT is either connected to VS1 or to the auxiliary power supply (V_REG2).

If $V_{VAUX} < VS1 + 0.5V$, VSOUT is connected to VS1. If $V_{VAUX} > VS1 + 0.5V$, VSOUT is connected to V_REG2 and the status bit P_On_Aux is set to 1.

In Idle mode the RF transceiver is disabled and the power consumption I_{S_IDLE} is about 230 μA (VSOUT OFF and CLK output OFF VS1 = VS2 = 3V). The exact value of this current is strongly dependent on the application and the exact operation mode, therefore check the section [“Electrical Characteristics: General” on page 63](#) for the appropriate application case.

Via the 4-wire serial interface a connected microcontroller can program the required parameter and enable the TX, RX polling or RX mode.

The transceiver can be set back to OFF mode by an OFF command via the 4-wire serial interface (the bit AVCC_EN must be set to 0, the input level of pin PWR_ON must be 0 and pin T1, T2, T3, T4 and T5 = 1 before writing the OFF command).

Table 7-1. Control Register 1

| OPM1 | OPM0 | Function |
|------|------|-----------|
| 0 | 0 | Idle mode |

7.4 Reset Timing and Reset Logic

If the transceiver is switched on (OFF mode to Idle mode, OFF mode to AUX mode) DVCC and VSOUT are ramping up as illustrated in [Figure 7-3 on page 31](#) (AVCC only ramps up if the transceiver is set to the Idle mode). The internal signal DVCC_RESET resets the digital control logic and sets the control register to default values.

A voltage monitor generates a low level at pin N_RESET until the voltage at pin VSOUT exceeds 2.38V (typically) and the start-up time of the XTO has elapsed (amplitude detector, see [Figure 6-2 on page 25](#)). After the voltage at pin VSOUT exceeds 2.3V (typically) and the start-up time of the XTO has elapsed the output clock at pin CLK is available. Because the enabling of pin CLK is asynchronous the first clock cycle may be incomplete.

The status bit Low_Batt is set to 1 if the voltage at pin VSOUT V_{VSOUT} drops below V_{Thres_2} (typically 2.38V). Low_Batt is set to 0 if V_{VSOUT} exceeds V_{Thres_2} and the status register is read via the 4-wire serial interface or N_RESET is set to low.

If V_{VSOUT} drops below V_{Thres_1} (typically 2.3V), N_RESET is set to low. If bit VSOUT_EN in control register 3 is 1, a DVCC_RESET is also generated. If V_{VSOUT} was prior disabled by the connected microcontroller by setting bit VSOUT_EN = 0, no DVCC_RESET is generated.

Note: If $VSOUT < V_{Thres_1}$ (typically 2.3V) the output of the pin CLK is low, the Microcontroller_Interface is disabled and the transceiver is not programmable via the 4-wire serial interface.

Figure 7-3. Reset Timing

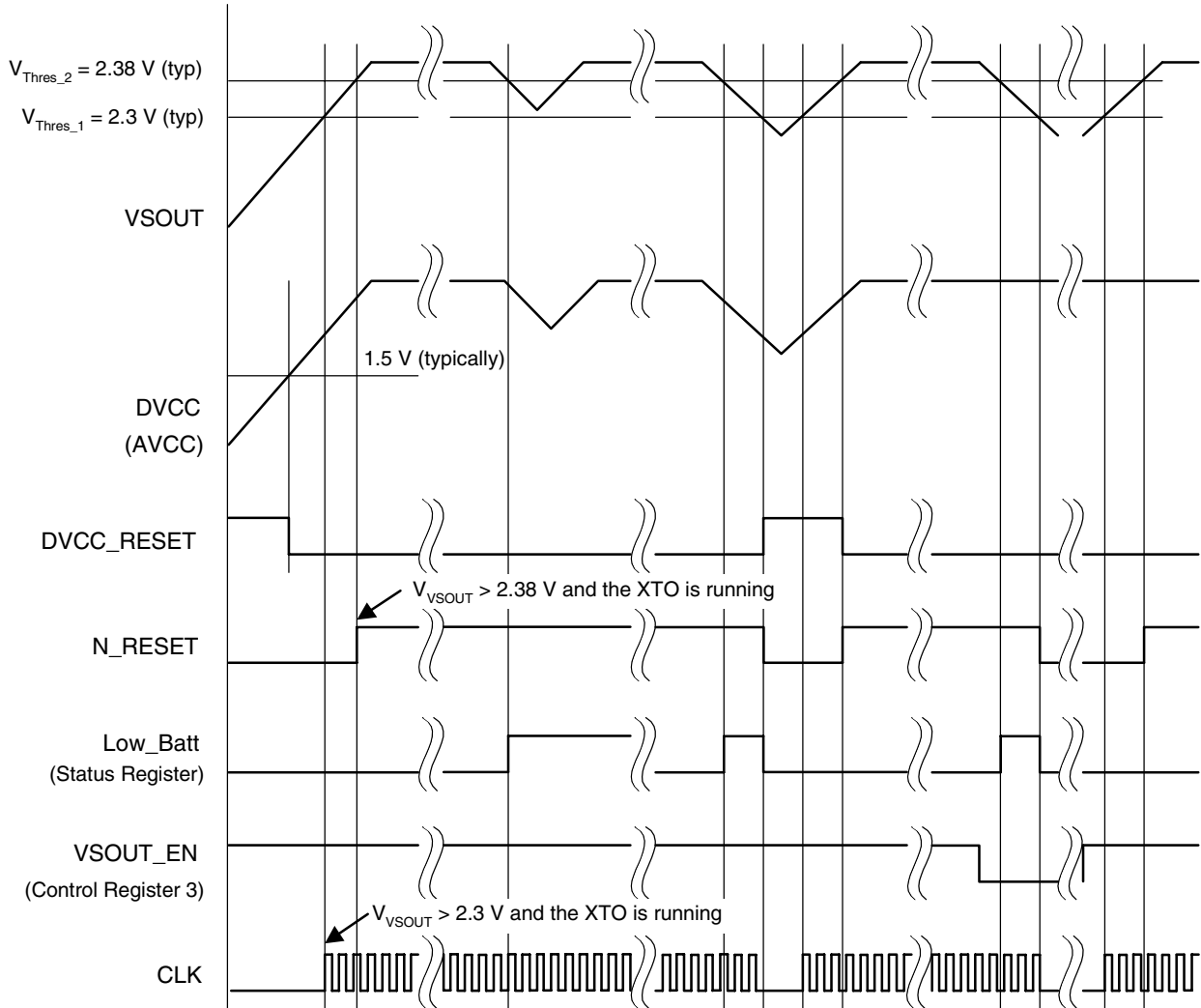
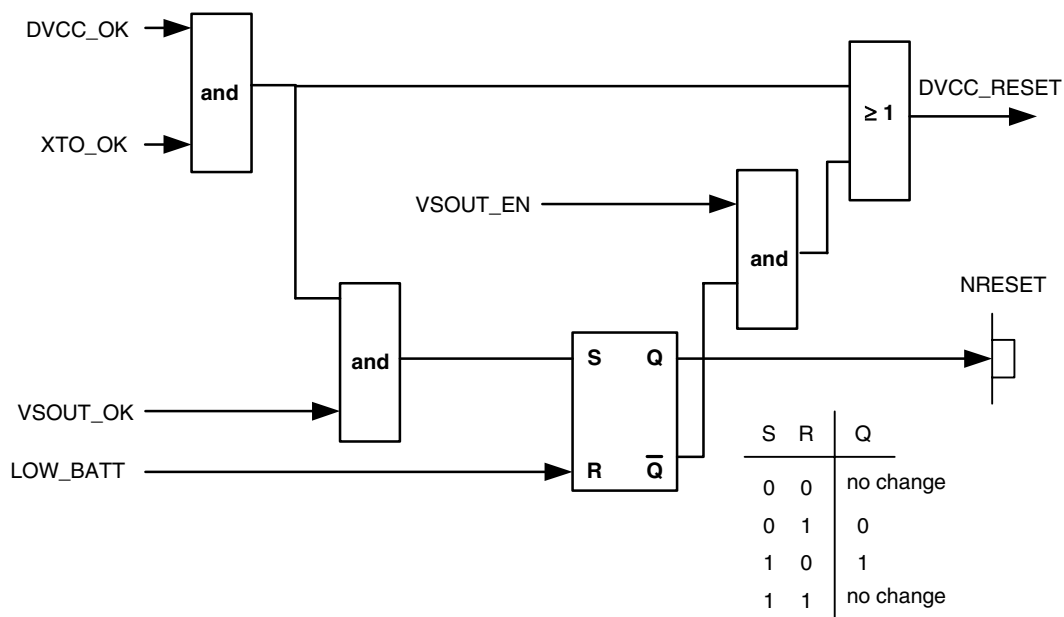


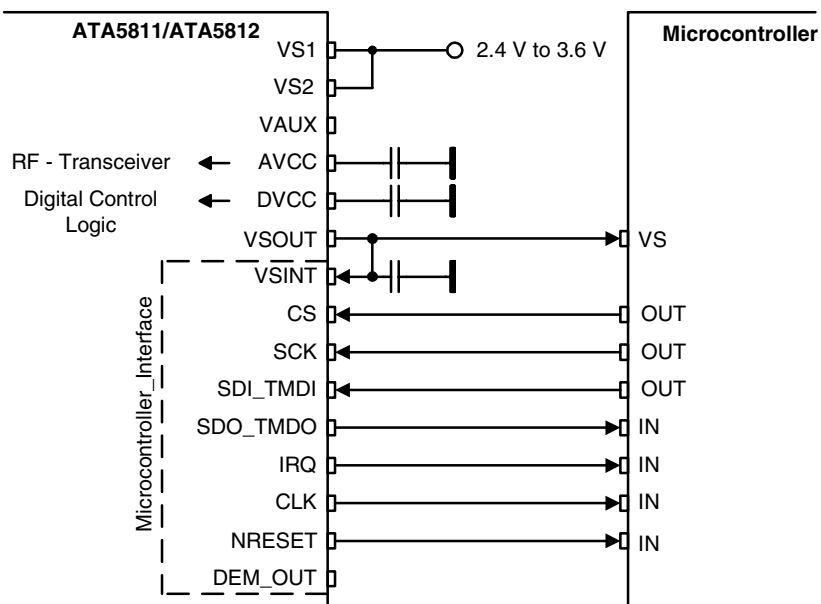
Figure 7-4. Reset Logic, SR Latch Generates the Hysteresis in the NRESET Signal



7.5 1-Battery Application

The supply voltage range is 2.4V to 3.6V and VAUX is not used.

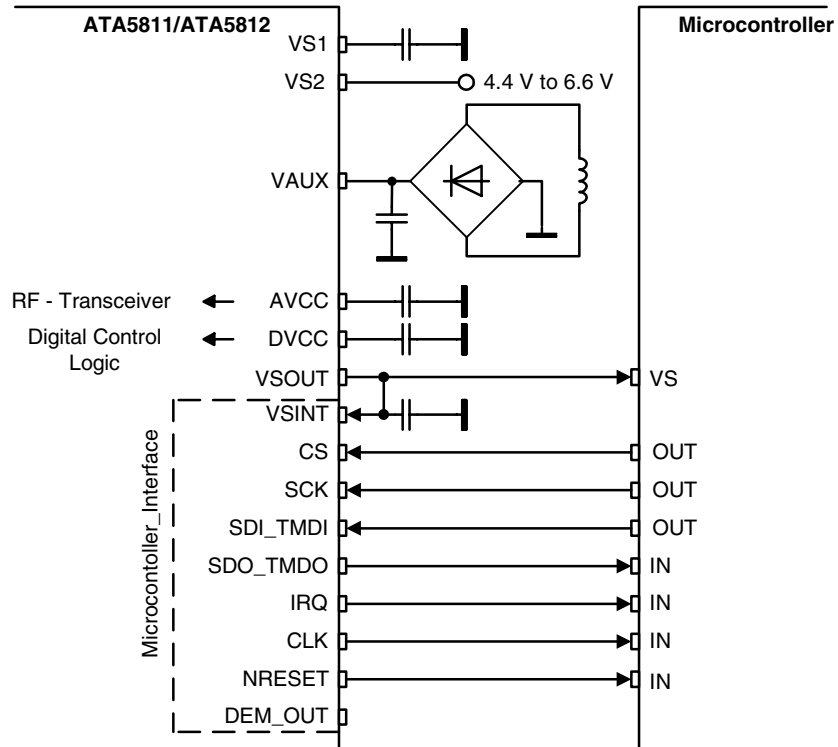
Figure 7-5. 1-Battery Application



7.6 2-Battery Application

The supply voltage range is 4.4V to 6.6V and VAUX is connected to an inductive supply.

Figure 7-6. 2-Battery Application with Inductive Emergency Supply



8. Microcontroller Interface

The microcontroller interface is a level converter which converts all internal digital signals which are referred to the DVCC voltage, into the voltage used by the microcontroller. Therefore, the pin VSINT has to be connected to the supply voltage of the microcontroller.

This makes it possible to use the internal voltage regulator/switch at pin VSOUT as in [Figure 2-1 on page 6](#) and [Figure 4-1 on page 8](#) or to connect the microcontroller and the pin VSINT directly to the supply voltage of the microcontroller as in [Figure 3-1 on page 7](#).

9. Digital Control Logic

9.1 Register Structure

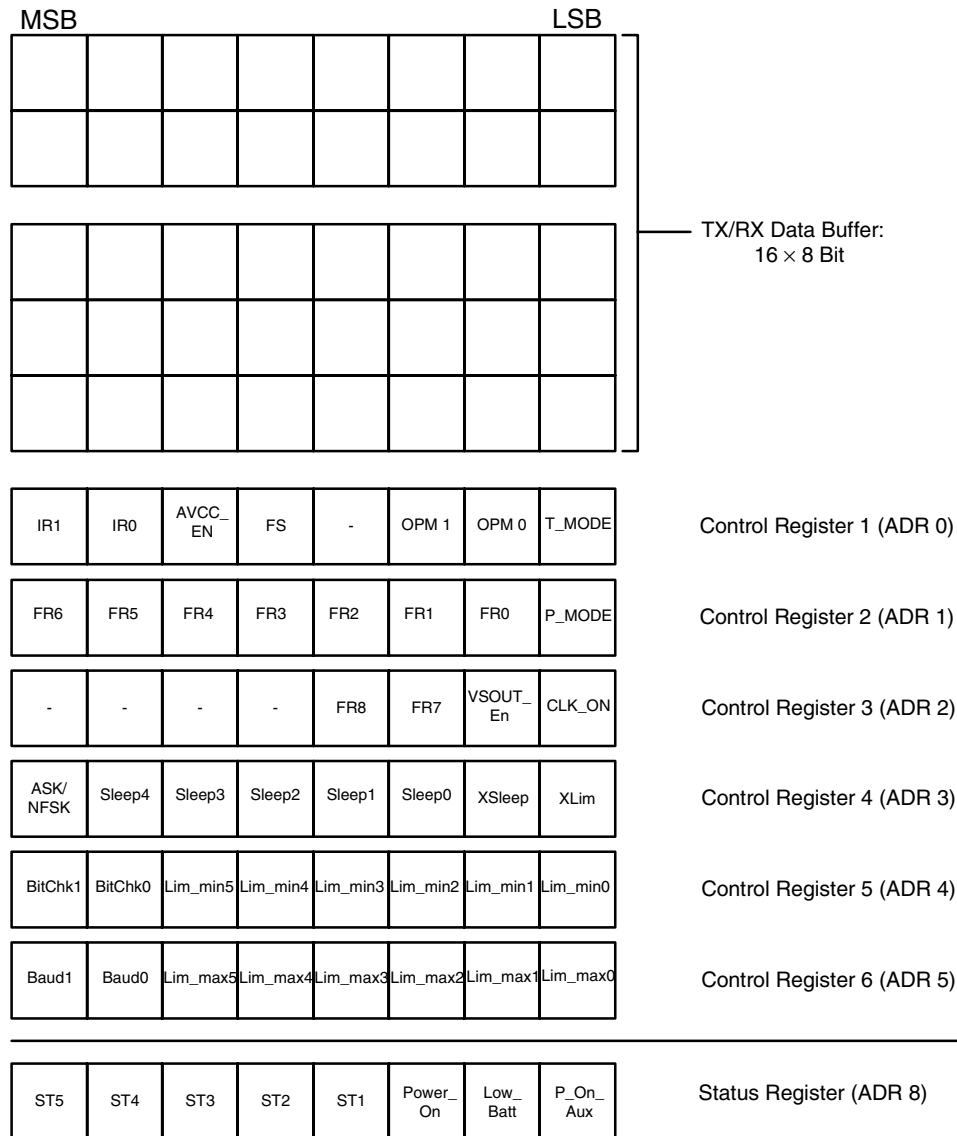
The configuration of the transceiver is stored in RAM cells. The RAM contains a 16×8 -bit TX/RX data buffer and a 6×8 -bit control register and is write and readable via a 4-wire serial interface (CS, SCK, SDI_TMDI, SDO_TMDO).

The 1×8 -bit status register is not part of the RAM and is readable via the 4-wire serial interface.

The RAM and the status information is stored as long as the transceiver is in any active mode (DVCC = VS1 or DVCC = V_REG2) and gets lost if the transceiver is in OFF mode (DVCC = OFF).

After the transceiver is turned on via pin PWR_ON = High, T1 = Low, T2 = Low, T3 = Low, T4 = Low or T5 = Low or the voltage at pin VAUX $V_{VAUX} > 3.5V$ (typically) the control registers are in the default state.

Figure 9-1. Register Structure



9.2 TX/RX Data Buffer

The TX/RX data buffer is used to handle the data transfer during RX and TX operations.

9.3 Control Register

To use the transceiver in different applications it can be configured by a connected microcontroller via the 4-wire serial interface.

9.3.1 Control Register 1 (ADR 0)

Table 9-1. Control Register 1 (Function of Bit 7 and Bit 6 in RX Mode)

| IR1 | IR0 | Function (RX Mode) |
|-----|-----|---|
| 0 | 0 | Pin IRQ is set to 1 if 4 received bytes are in the TX/RX data buffer or a receiving error occurred |
| 0 | 1 | Pin IRQ is set to 1 if 8 received bytes are in the TX/RX data buffer or a receiving error occurred |
| 1 | 0 | Pin IRQ is set to 1 if 12 received bytes are in the TX/RX data buffer or a receiving error occurred (default) |
| 1 | 1 | Pin IRQ is set to 1 if a receiving error occurred |

Table 9-2. Control Register 1 (Function of Bit 7 and Bit 6 in TX Mode)

| IR1 | IR0 | Function (TX Mode) |
|-----|-----|---|
| 0 | 0 | Pin IRQ is set to 1 if 4 bytes still are in the TX/RX data buffer or the TX data buffer is empty |
| 0 | 1 | Pin IRQ is set to 1 if 8 bytes still are in the TX/RX data buffer or the TX data buffer is empty |
| 1 | 0 | Pin IRQ is set to 1 if 12 bytes still are in the TX/RX data buffer or the TX data buffer is empty (default) |
| 1 | 1 | Pin IRQ is set to 1 if the TX data buffer is empty |

Table 9-3. Control Register 1 (Function of Bit 5)

| AVCC_EN | Function |
|---------|---|
| 0 | (default) |
| 1 | Enables AVCC, if the ATA5811/ATA5812 is in AUX mode |

Table 9-4. Control Register 1 (Function of Bit 4)

| FS | Function |
|----|-------------|
| 0 | 433/868 MHz |
| 1 | 315 MHz |

Table 9-5. Control Register 1 (Function of Bit 2 and Bit 1)

| OPM1 | OPM0 | Function |
|------|------|---------------------|
| 0 | 0 | Idle mode (default) |
| 0 | 1 | TX mode |
| 1 | 0 | RX polling mode |
| 1 | 1 | RX mode |

Table 9-6. Control Register 1 (Function of Bit 0)

| T_MODE | Function |
|--------|--|
| 0 | TX and RX function via TX/RX data buffer (default) |
| 1 | Transparent mode, TX/RX data buffer disabled, TX modulation data stream via pin SDI_TMDI, RX modulation data stream via pin SDO_TMDO |

9.3.2 Control Register 2 (ADR 1)

Table 9-7. Control Register 2 (Function of Bit 7, Bit 6, Bit 5, Bit 4, Bit 3, Bit 2 and Bit 1)

| FR6 | FR5 | FR4 | FR3 | FR2 | FR1 | FR0 | Function |
|-----|-----|-----|-----|-----|-----|-----|----------------------|
| 0 | 0 | 0 | 0 | 0 | 0 | 0 | FREQ2 = 0 |
| 0 | 0 | 0 | 0 | 0 | 0 | 1 | FREQ2 = 1 |
| . | . | . | . | . | . | . | |
| 1 | 0 | 1 | 1 | 0 | 0 | 0 | FREQ2 = 88 (default) |
| . | . | . | . | . | . | . | |
| 1 | 1 | 1 | 1 | 1 | 1 | 1 | FREQ2 = 127 |

Note: Tuning of f_{RF} LSB's (total 9 bits), frequency trimming, resolution of f_{RF} is $f_{XTO}/16384$ which is approximately 800 Hz (see "XTO" on page 23, Table 6-1 on page 25)

Table 9-8. Control Register 2 (Function of Bit 0 in RX Mode)

| P_MODE | Function (RX Mode) |
|--------|--|
| 0 | Pin IRQ is set to 1 if the Bit-check is successful (default) |
| 1 | No effect on pin IRQ if the Bit-check is successful |

Table 9-9. Control Register 2 (Function of Bit 0 in TX Mode)

| P_MODE | Function (TX Mode) |
|--------|-------------------------------------|
| 0 | Manchester modulator on (default) |
| 1 | Manchester modulator off (NRZ mode) |

9.3.3 Control Register 3 (ADR 2)

Table 9-10. Control Register 3 (Function of Bit 3 and Bit 2)

| FR8 | FR7 | Function |
|-----|-----|-----------------------|
| 0 | 0 | FREQ3 = 0 |
| 0 | 1 | FREQ3 = 128 |
| 1 | 0 | FREQ3 = 256 (default) |
| 1 | 1 | FREQ3 = 384 |

Note: Tuning of f_{RF} MSB's

Table 9-11. Control Register 3 (Function of Bit 1)

| VSOUT_EN | Function |
|----------|--|
| 0 | Output voltage power supply for external devices off (pin VSOUT) |
| 1 | Output voltage power supply for external devices on (default) |

Note: This bit is set to 1 if the Bit-check is ok (RX_Polling, RX mode), an event at pin T1, T2, T3, T4 or T5 occurs or the bit Power_On in the status register is 1.
Setting VSOUT_EN = 0 in AUX mode is not allowed

Table 9-12. Control Register 3 (Function of Bit 0)

| CLK_ON | Function |
|--------|----------------------------|
| 0 | Clock output off (pin CLK) |
| 1 | Clock output on (default) |

Note: This bit is set to 1 if the Bit-check is ok (RX_Polling, RX mode), an event at pin T1, T2, T3, T4 or T5 occurs or the bit Power_On in the status register is 1.

9.3.4 Control Register 4 (ADR 3)

Table 9-13. Control Register 4 (Function of Bit 7)

| ASK_NFSK | Function |
|----------|--------------------|
| 0 | FSK mode (default) |
| 1 | ASK mode |

Table 9-14. Control Register 4 (Function of Bit 6, Bit 5, Bit 4, Bit 3 and Bit 2)

| Sleep4 | Sleep3 | Sleep2 | Sleep1 | Sleep0 | Function Sleep ($T_{Sleep} = Sleep \times 1024 \times T_{DCLK} \times X_{Sleep}$) |
|--------|--------|--------|--------|--------|--|
| 0 | 0 | 0 | 0 | 0 | 0 |
| 0 | 0 | 0 | 0 | 1 | 1 |
| . | . | . | . | . | |
| 0 | 1 | 0 | 1 | 0 | 10 ($T_{Sleep} = 10 \times 1024 \times T_{DCLK} \times X_{Sleep}$) (default) |
| . | . | . | . | . | |
| 1 | 1 | 1 | 1 | 1 | 31 |

Table 9-15. Control Register 4 (Function of Bit 1)

| XSleep | Function |
|--------|--|
| 0 | $X_{Sleep} = 1$; extended T_{Sleep} off (default) |
| 1 | $X_{Sleep} = 8$; extended T_{Sleep} on |

Table 9-16. Control Register 4 (Function of Bit 0)

| XLim | Function |
|------|--|
| 0 | $X_{Lim} = 1$; extended T_{Lim_min} , T_{Lim_max} off (default) |
| 1 | $X_{Lim} = 2$; extended T_{Lim_min} , T_{Lim_max} on |

9.3.5 Control Register 5 (ADR 4)

Table 9-17. Control Register 5 (Function of Bit 7 and Bit 6)

| BitChk1 | BitChk0 | Function |
|---------|---------|--|
| 0 | 0 | $N_{\text{Bit-check}} = 0$ (0 bits checked during Bit-check) |
| 0 | 1 | $N_{\text{Bit-check}} = 3$ (3 bits checked during Bit-check (default)) |
| 1 | 0 | $N_{\text{Bit-check}} = 6$ (6 bits checked during Bit-check) |
| 1 | 1 | $N_{\text{Bit-check}} = 9$ (9 bits checked during Bit-check) |

Table 9-18. Control Register 5 (Function of Bit 5, Bit 4, Bit 3, Bit 2, Bit 1 and Bit 0 in RX Mode)

| Lim_min5 | Lim_min4 | Lim_min3 | Lim_min2 | Lim_min1 | Lim_min0 | Function (RX Mode) Lim_min (Lim_min < 10 are not applicable) ($T_{\text{Lim_min}} = \text{Lim_min} \times T_{\text{XDCLK}}$) |
|----------|----------|----------|----------|----------|----------|---|
| 0 | 0 | 1 | 0 | 1 | 0 | 10 |
| 0 | 0 | 1 | 0 | 1 | 1 | 11 |
| . | . | . | . | . | . | |
| 0 | 1 | 0 | 0 | 0 | 0 | 16 ($T_{\text{Lim_min}} = 16 \times T_{\text{XDCLK}}$) (default) |
| . | . | . | . | . | . | |
| 1 | 1 | 1 | 1 | 1 | 1 | 63 |

Table 9-19. Control Register 5 (Function of Bit 5, Bit 4, Bit 3, Bit 2, Bit 1 and Bit 0 in TX Mode)

| Lim_min5 | Lim_min4 | Lim_min3 | Lim_min2 | Lim_min1 | Lim_min0 | Function (TX Mode) Lim_min (Lim_min < 10 are not applicable) ($\text{TX_Baudrate} = 1/((\text{Lim_min} + 1) \times T_{\text{XDCLK}} \times 2)$) |
|----------|----------|----------|----------|----------|----------|---|
| 0 | 0 | 1 | 0 | 1 | 0 | 10 |
| 0 | 0 | 1 | 0 | 1 | 1 | 11 |
| . | . | . | . | . | . | |
| 0 | 1 | 0 | 0 | 0 | 0 | 16 ($\text{TX_Baudrate} = 1/((16 + 1) \times T_{\text{XDCLK}} \times 2)$) (default) |
| . | . | . | . | . | . | |
| 1 | 1 | 1 | 1 | 1 | 1 | 63 |

9.3.6 Control Register 6 (ADR 5)

Table 9-20. Control Register 6 (Function of Bit 7 and Bit 6)

| Baud1 | Baud0 | Function |
|-------|-------|---|
| 0 | 0 | Baud-rate range 0 (B0) 1.0 kBaud to 2.5 kBaud; $T_{XDCLK} = 8 \times T_{DCLK} \times X_{Lim}$ |
| 0 | 1 | Baud-rate range 1 (B1) 2.0 kBaud to 5.0 kBaud; $T_{XDCLK} = 4 \times T_{DCLK} \times X_{Lim}$ |
| 1 | 0 | Baud-rate range 2 (B2) 4.0 kBaud to 10.0 kBaud; $T_{XDCLK} = 2 \times T_{DCLK} \times X_{Lim}$; (default) |
| 1 | 1 | Baud-rate range 3 (B3) 8.0 kBaud to 20.0 kBaud; $T_{XDCLK} = 1 \times T_{DCLK} \times X_{Lim}$; Note that the receiver is not working with >10 kBaud in ASK mode |

Table 9-21. Control Register 6 (Function of Bit 5, Bit 4, Bit 3, Bit 2, Bit 1 and Bit 0)

| Lim_max5 | Lim_max4 | Lim_max3 | Lim_max2 | Lim_max1 | Lim_max0 | Function Lim_max (Lim_max < 12 Are Not Applicable) ($T_{Lim_max} = (Lim_max - 1) \times T_{XDCLK}$) |
|----------|----------|----------|----------|----------|----------|---|
| 0 | 0 | 1 | 1 | 0 | 0 | 12 |
| 0 | 0 | 1 | 1 | 0 | 1 | 13 |
| . | . | . | . | . | . | |
| 0 | 1 | 1 | 1 | 0 | 0 | 28 ($T_{Lim_max} = (28 - 1) \times T_{XDCLK}$) (default) |
| . | . | . | . | . | . | |
| 1 | 1 | 1 | 1 | 1 | 1 | 63 |

9.3.7 Status Register

The status register indicates the current status of the transceiver and is readable via the 4-wire serial interface. Setting Power_On or P_On_Aux or an event on ST1, ST2, ST3, ST4 or ST5 is indicated by an IRQ.

Reading the status register resets the bits Power_On, Low_Batt, P_On_Aux and the IRQ

9.3.8 Status Register (ADR 8)

Table 9-22. Status Register

| Status Bit | Function |
|------------|--|
| ST5 | Status of pin T5 Pin T5 = 0 → ST5 = 1 Pin T5 = 1 → ST5 = 0 (see Figure 9-3 on page 42) |
| ST4 | Status of pin T4 Pin T4 = 0 → ST4 = 1 Pin T4 = 1 → ST4 = 0 (see Figure 9-3 on page 42) |
| ST3 | Status of pin T3 Pin T3 = 0 → ST3 = 1 Pin T3 = 1 → ST3 = 0 (see Figure 9-3 on page 42) |
| ST2 | Status of pin T2 Pin T2 = 0 → ST2 = 1 Pin T2 = 1 → ST2 = 0 (see Figure 9-3 on page 42) |
| ST1 | Status of pin T1 Pin T1 = 0 → ST1 = 1 Pin T1 = 1 → ST1 = 0 (see Figure 9-3 on page 42) |
| Power_On | Indicates that the transceiver was woken up by pin PWR_ON (rising edge on pin PWR_ON). During Power_On = 1, the bits VSOUT_EN and CLK_ON in control register 3 are set to 1. (see Figure 9-4 on page 43) |
| Low_Batt | Indicates that output voltage on pin VSOUT is too low ($V_{VSOUT} < 2.38V$ typically) (see Figure 9-5 on page 44) |
| P_On_Aux | Indicates that the auxiliary supply voltage on pin VAUX is high enough to operate. State transition: a) OFF mode → AUX mode (see Figure 7-2 on page 29) b) Idle mode ($VSOUT = VS1$) → Idle mode ($VSOUT = V_REG2$) (see Figure 9-6 on page 45) |

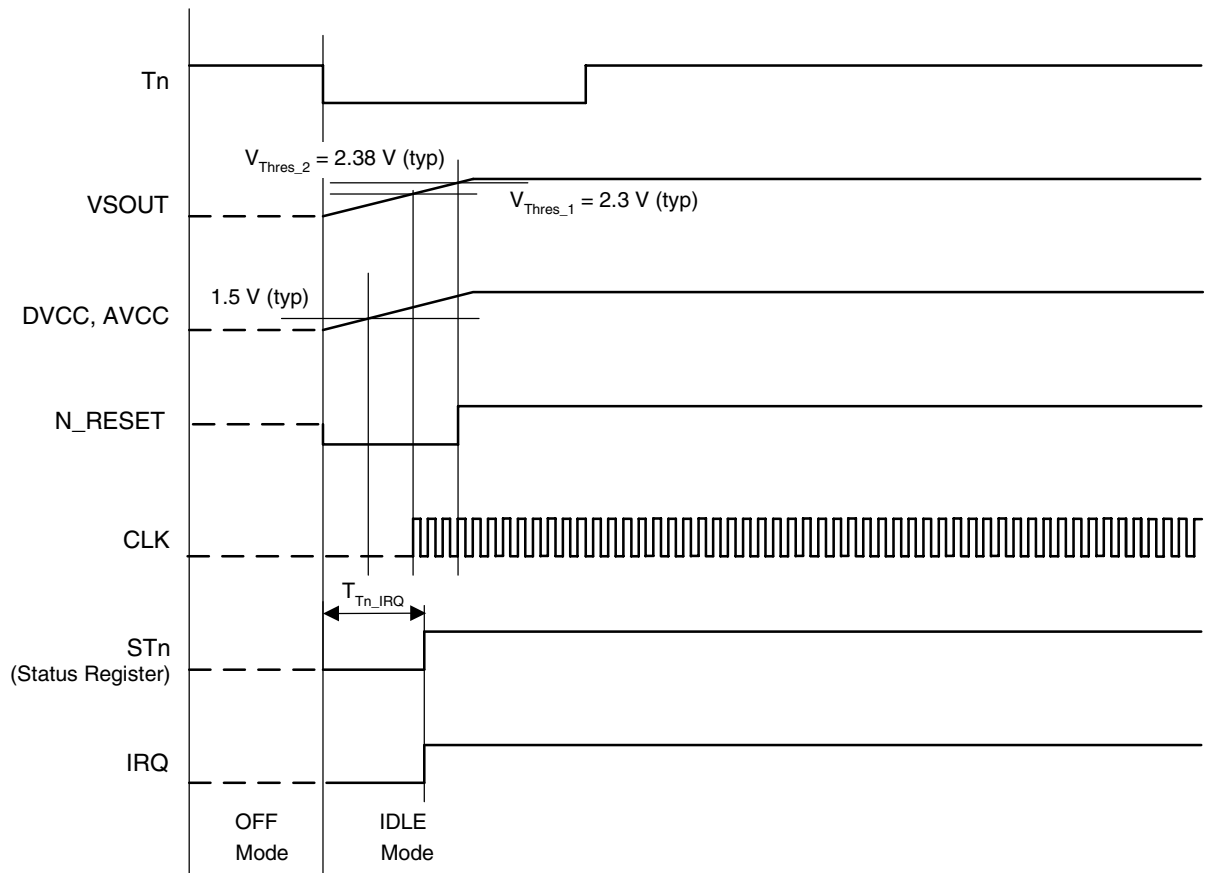
9.4 Pin Tn

To switch the transceiver from OFF to Idle mode, pin Tn must set to 0 (maximum $0.2 \times V_{VS2}$) for at least T_{Tn_IRQ} (see Figure 9-2). The transceiver recognize the negative edge, sets pin N_RESET to low and switches on DVCC, AVCC and the power supply for external devices VSOUT.

If V_{DVCC} exceeds 1.5V (typically) and the XTO is settled, the digital control logic is active and sets the status bit STn to 1 and an interrupt is issued (T_{Tn_IRQ}).

After the voltage on pin VSOUT exceeds 2.3V (typically) and the start-up time of the XTO is elapsed the output clock on pin CLK is available. Because the enabling of pin CLK is asynchronous the first clock cycle may be incomplete. N_RESET is set to high if V_{VSOUT} exceeds 2.38V (typically) and the XTO is settled.

Figure 9-2. Timing Pin Tn, Status Bit STn



If the transceiver is in any active mode (Idle, AUX, TX, RX, RX_Polling), an integrated debounce logic is active. If there is an event on pin Tn a debounce counter is set to 0 ($T = 0$) and started. The status is updated, an interrupt is issued and the debounce counter is stopped after reaching the counter value $T = 8195 \times T_{DCLK}$.

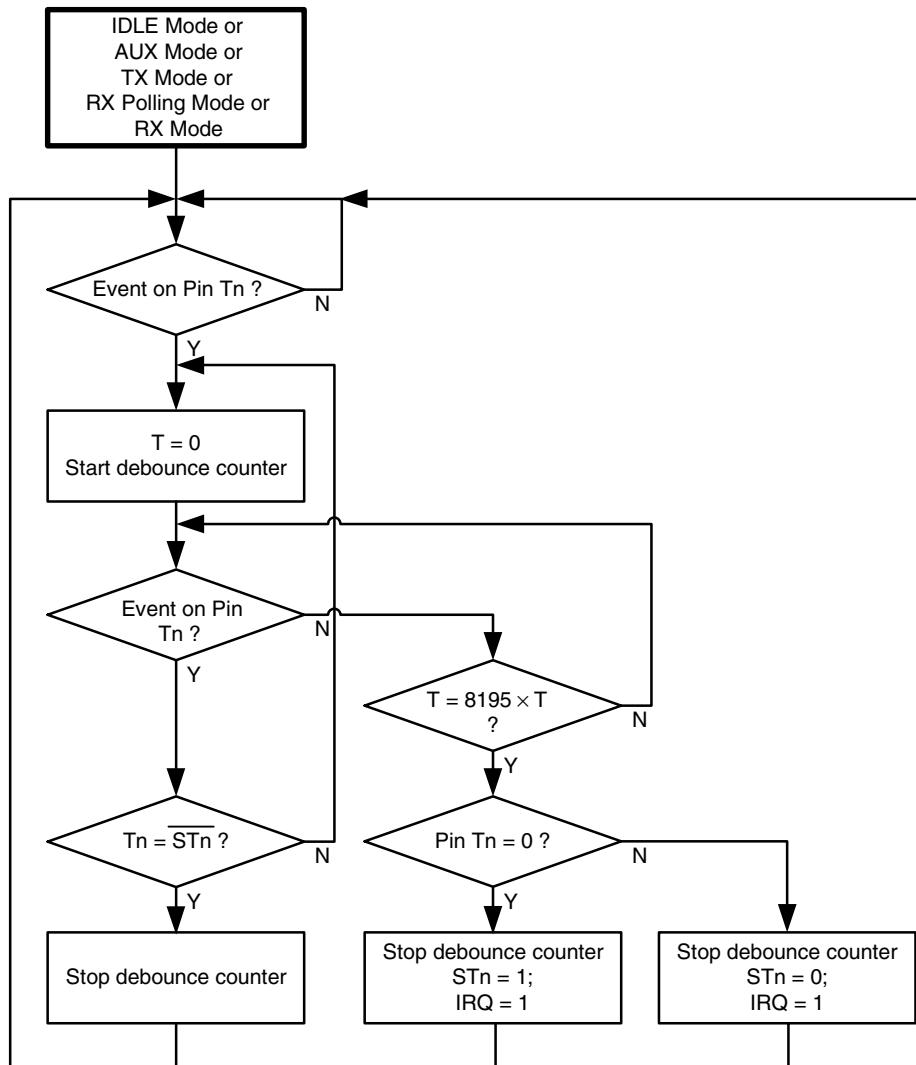
An event on the same key input before reaching $T = 8195 \times T_{DCLK}$ stops the debounce counter. An event on an other key input before reaching $T = 8195 \times T_{DCLK}$ resets and restarts the debounce counter.

While the debounce counter is running, the bits VSOUT_EN and CLK_ON in control register 3 are set to 1.

The interrupt is deleted after reading the status register or executes the command Delete_IRQ.

If a pin Tn is not used, it can be left open because of an internal pull-up resistor (typically 50 k Ω).

Figure 9-3. Timing Flow Pin Tn, Status Bit STn



9.5 Pin PWR_ON

To switch the transceiver from OFF to Idle mode, pin PWR_ON must set to 1 (minimum $0.8 \times V_{VS2}$) for at least T_{PWR_ON} (see Figure 9-4). The transceiver recognize the positive edge, sets pin N_RESET to low and switches on DVCC, AVCC and the power supply for external devices VSOUT.

If V_{DVCC} exceeds 1.5 V (typically) and the XTO is settled, the digital control logic is active and sets the status bit Power_On to 1 and an interrupt is issued ($T_{PWR_ON_IRQ_1}$).

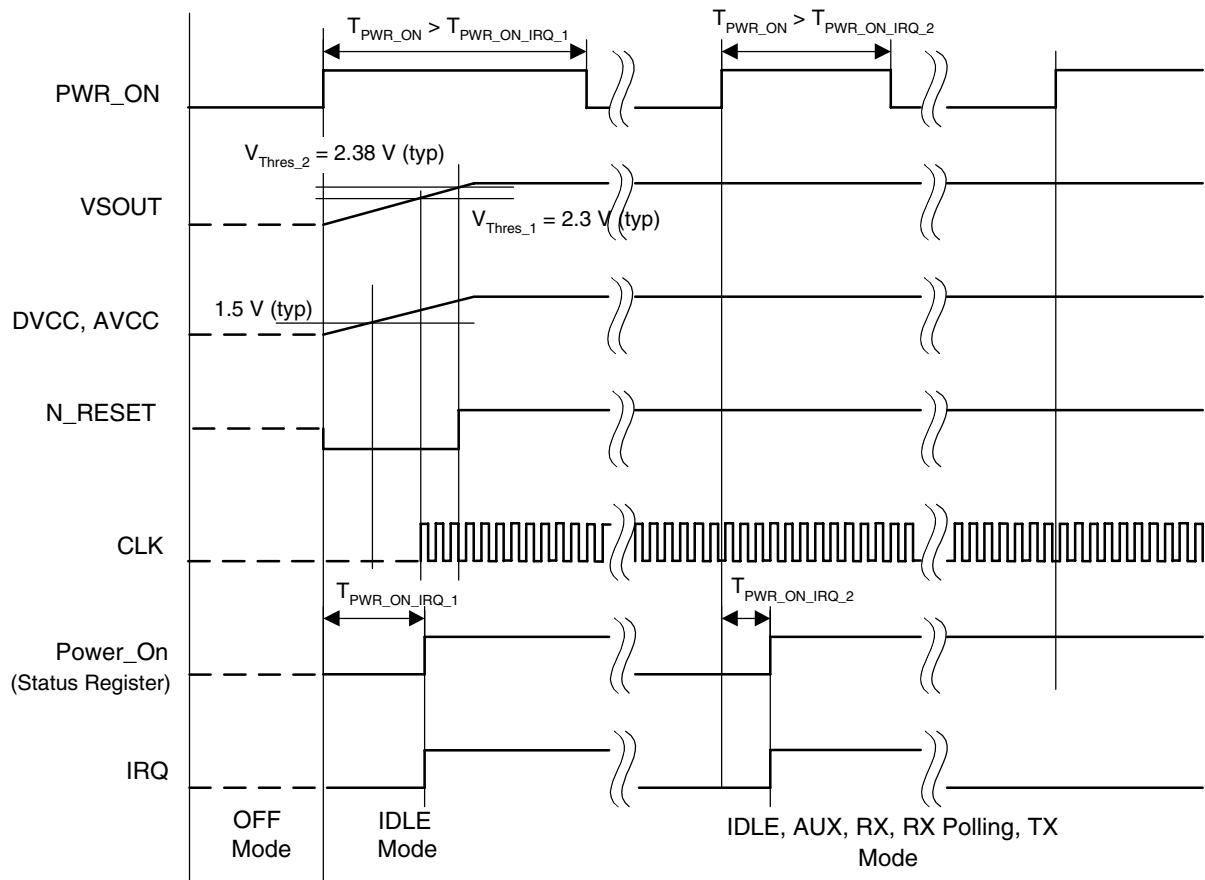
After the voltage on pin VSOUT exceeds 2.3 V (typically) and the start-up time of the XTO is elapsed the output clock on pin CLK is available. Because the enabling of pin CLK is asynchronous the first clock cycle may be incomplete. N_RESET is set to high if V_{VSOUT} exceeds 2.38 V (typically) and the XTO is settled.

If the transceiver is in any active mode (Idle, AUX, RX, RX_Polling, TX), a positive edge on pin PWR_ON sets Power_On to 1 (after $T_{PWR_ON_IRQ_2}$). The state transition Power_On 0 \rightarrow 1 generates an interrupt. If Power_On is still 1 during the positive edge on pin PWR_ON no interrupt is issued. Power_On and the interrupt is deleted after reading the status register.

During Power_On = 1, the bits VSOUT_EN and CLK_ON in control register 3 are set to 1.

Note: It is not possible to set the transceiver to OFF mode by setting pin PWR_ON to 0. If pin PWR_ON is not used, it must be connected to GND.

Figure 9-4. Timing Pin PWR_ON, Status Bit Power_On

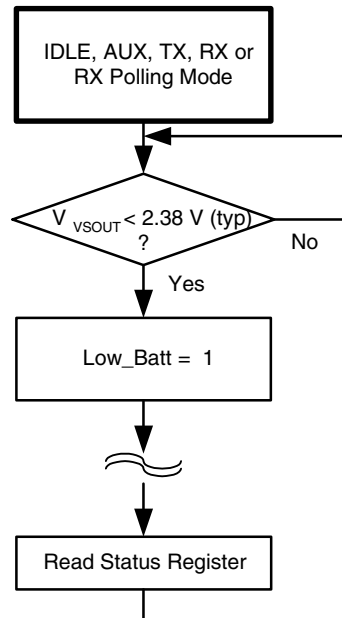


9.6 Low Battery Indicator

The status bit Low_Batt is set to 1 if the voltage on pin VSOUT V_{VSOUT} drops under 2.38V (typically).

Low_Batt is set to 0 if V_{VSOUT} exceeds V_{Thres_2} and the status register is read via the 4-wire serial interface (see [Figure 7-3 on page 31](#)).

Figure 9-5. Timing Status Bit Low_Batt



9.7 Pin VAUX

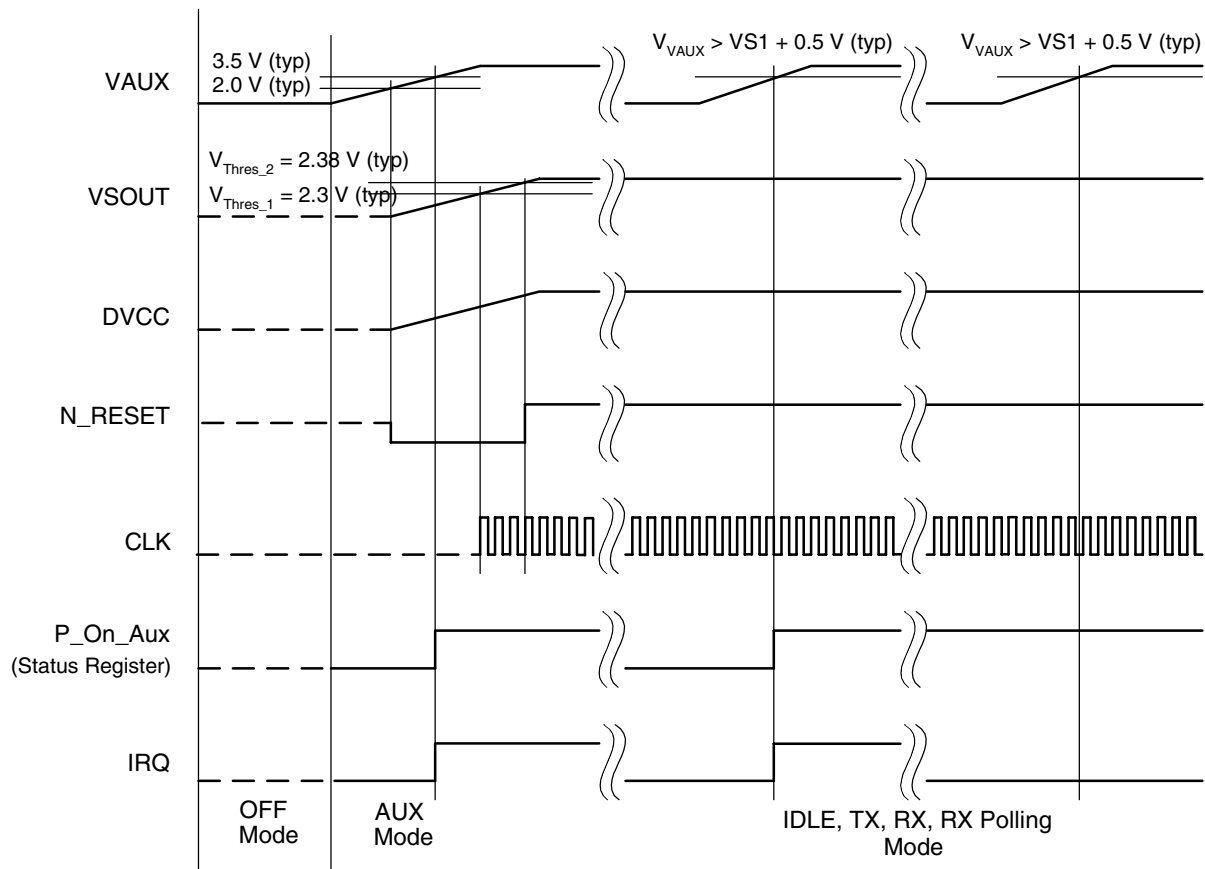
To switch the transceiver from OFF to AUX mode, the voltage on pin VAUX V_{VAUX} must exceed 3.5V (typically) (see Figure 9-6). If V_{VAUX} exceeds 2V (typically) pin N_RESET is set to low, DVCC and the power supply for external devices VSOUT are switched on.

If V_{VAUX} exceeds 3.5V (typically) the status bit P_On_Aux is set to 1 and an interrupt is issued.

After the voltage on pin VSOUT exceeds 2.3 V (typically) and the start-up time of the XTO is elapsed the output clock on pin CLK is available. Because the enabling of pin CLK is asynchronous the first clock cycle may be incomplete. N_RESET is set to high if V_{VSOUT} exceeds 2.38V (typically) and the XTO is settled.

If the transceiver is in any active mode (Idle, TX, RX, RX_Polling), a positive edge on pin VAUX and $V_{VAUX} > VS1 + 0.5V$ sets P_On_Aux to 1. The state transition P_On_Aux 0 → 1 generates an interrupt. If P_On_Aux is still 1 during the positive edge on pin VAUX no interrupt is issued. P_On_Aux and the interrupt is deleted after reading the status register.

Figure 9-6. Timing Pin VAUX, Status Bit P_On_Aux



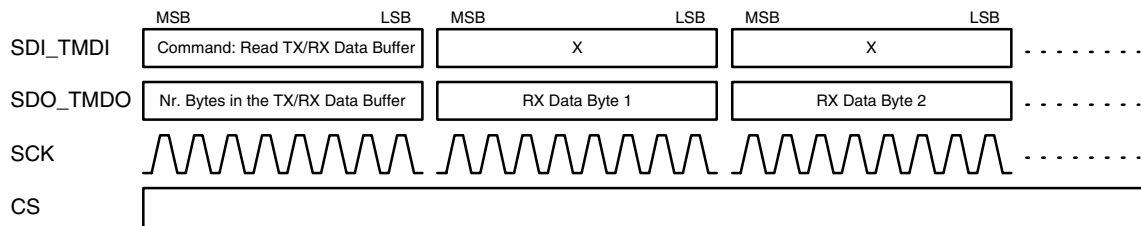
10. Transceiver Configuration

The configuration of the transceiver takes place via a 4-wire serial interface (CS, SCK, SDI_TMDI, SDO_TMDO) and is organized in 8-bit units. The configuration is initiated with a 8-bit command. While shifting the command into pin SDI_TMDI, the number of bytes in the TX/RX data buffer are available on pin SDO_TMDO. The read and write commands are followed by one or more 8-bit data units. Each 8-bit data transmission begins with the MSB. The serial interface is in reset state if the level on pin CS = Low.

10.1 Command: Read TX/RX Data Buffer

During a RX operation the user can read the received bytes in the TX/RX data buffer successively.

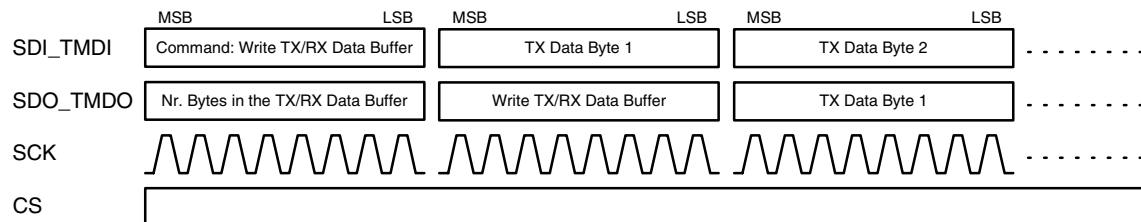
Figure 10-1. Read TX/RX Data Buffer



10.2 Command: Write TX/RX Data Buffer

During a TX operation the user can write the bytes in the TX/RX data buffer successively. An echo of the command and the TX data bytes are provided for the microcontroller on pin SDO_TMDO.

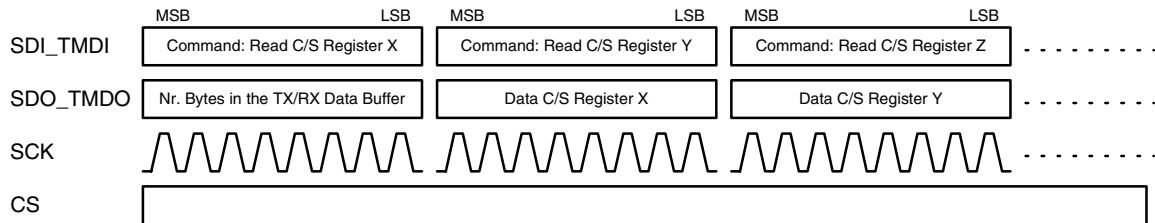
Figure 10-2. Write TX/RX Data Buffer



10.3 Command: Read Control/Status Register

The control and status registers can be read individually or successively.

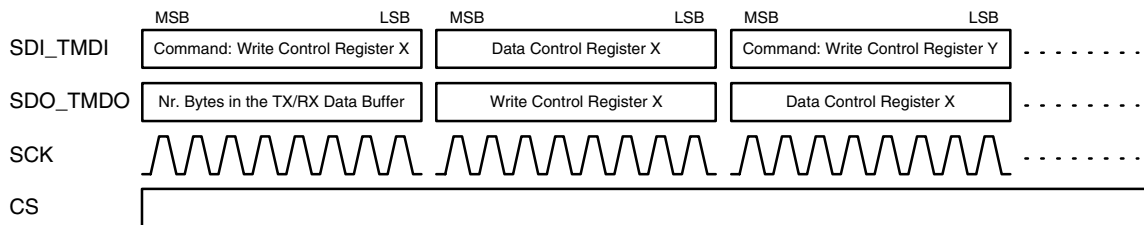
Figure 10-3. Read Control/Status Register



10.4 Command: Write Control Register

The control registers can be written individually or successively. An echo of the command and the data bytes are provided for the microcontroller on pin SDO_TMDO.

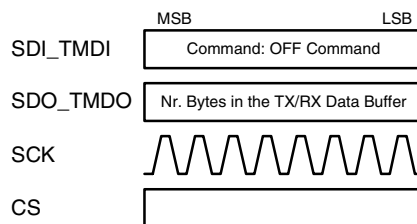
Figure 10-4. Write Control Register



10.5 Command: OFF Command

If AVCC_EN in control register 1 is 0, the input level on pin PWR_ON is low and on the key inputs Tn is high, the OFF command sets the transceiver in the OFF mode.

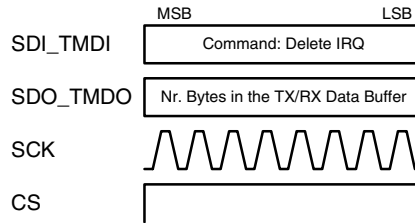
Figure 10-5. OFF Command



10.6 Command: Delete IRQ

The delete IRQ command sets pin IRQ to low.

Figure 10-6. Delete IRQ



10.7 Command Structure

The three most significant bits of the command (Bit 5 to Bit 7) indicates the command type. Bit 0 to Bit 4 describes the target address when reading or writing a control or status register. In all other commands Bit 0 to Bit 4 have no effect and should be set to 0 for compatibility reasons with future products.

Table 10-1. Command Structure

| Command | MSB | | | | | | | LSB |
|------------------------------|-------|-------|-------|-------|-------|-------|-------|-------|
| | Bit 7 | Bit 6 | Bit 5 | Bit 4 | Bit 3 | Bit 2 | Bit 1 | Bit 0 |
| Read TX/RX data buffer | 0 | 0 | 0 | x | x | x | x | x |
| Write TX/RX data buffer | 0 | 0 | 1 | x | x | x | x | x |
| Read control/status register | 0 | 1 | 0 | A4 | A3 | A2 | A1 | A0 |
| Write control register | 0 | 1 | 1 | A4 | A3 | A2 | A1 | A0 |
| OFF command | 1 | 0 | 0 | X | X | X | X | X |
| Delete IRQ | 1 | 0 | 1 | X | X | X | X | X |
| Not used | 1 | 1 | 0 | X | X | X | X | X |
| Not used | 1 | 1 | 1 | X | X | X | X | X |

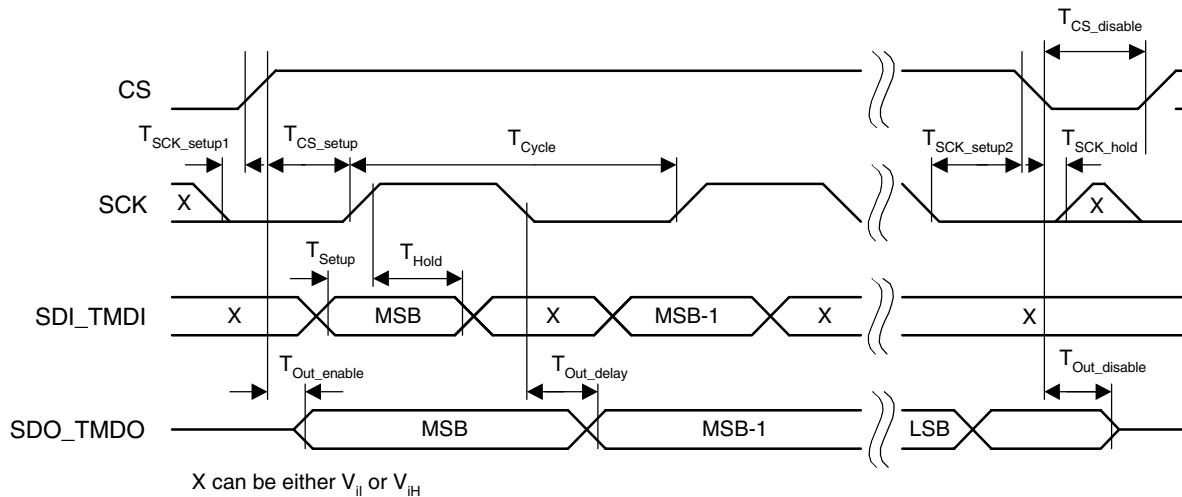
10.8 4-wire Serial Interface

The 4-wire serial interface consists of the Chip Select (CS), the Serial Clock (SCK), the Serial Data Input (SDI_TMDI) and the Serial Data Output (SDO_TMDO). Data is transmitted/received bit by bit in synchronization with the serial clock.

Note: If the output level on pin N_RESET is low, no data communication with the microcontroller is possible.

When CS is low and the transparent mode is inactive (T_MODE = 0), SDO_TMDO is in a high-impedance state. When CS is low and the transparent mode is active (T_MODE = 1), the RX data stream is available on pin SDO_TMDO.

Figure 10-7. Serial Timing



11. Operation Modes

11.1 RX Operation

The transceiver is set to RX operation with the bits OPM0 and OPM1 in control register 1

Table 11-1. Control Register 1

| OPM1 | OPM0 | Function |
|------|------|-----------------|
| 1 | 0 | RX polling mode |
| 1 | 1 | RX mode |

The transceiver is designed to consume less than 1 mA in RX operation while being sensitive to signals from a corresponding transmitter. This is achieved via the polling circuit. This circuit enables the signal path periodically for a short time. During this time the Bit-check logic verifies the presence of a valid transmitter signal. Only if a valid signal is detected the transceiver remains active and transfers the data to the connected microcontroller. This transfer takes place either via the TX/RX data buffer or via the pin SDO_TMDO. If there is no valid signal present the transceiver is in sleep mode most of the time resulting in low current consumption. This condition is called RX polling mode. A connected microcontroller can be disabled during this time.

All relevant parameters of the polling logic can be configured by the connected microcontroller. This flexibility enables the user to meet the specifications in terms of current consumption, system response time, data rate etc.

In RX mode the RF transceiver is enabled permanently and the Bit-check logic verifies the presence of a valid transmitter signal. If a valid signal is detected the transceiver transfers the data to the connected microcontroller. This transfer takes place either via the TX/RX data buffer or via the pin SDO_TMDO.

11.1.1 RX Polling Mode

If the transceiver is in RX polling mode it stays in a continuous cycle of three different modes. In sleep mode the RF transceiver is disabled for the time period T_{Sleep} while consuming low current of $I_S = I_{\text{IDLE_X}}$. During the start-up period, $T_{\text{Startup_PLL}}$ and $T_{\text{Startup_Sig_Proc}}$, all signal processing circuits are enabled and settled. In the following Bit-check mode, the incoming data stream is analyzed bit by bit contra a valid transmitter signal. If no valid signal is present, the transceiver is set back to sleep mode after the period $T_{\text{Bit-check}}$. This period varies check by check as it is a statistical process. An average value for $T_{\text{Bit-check}}$ is given in the electrical characteristics. During $T_{\text{Startup_PLL}}$ the current consumption is $I_S = I_{\text{RX_X}}$. During $T_{\text{Startup_Sig_Proc}}$ and $T_{\text{Bit-check}}$ the current consumption is $I_S = I_{\text{Startup_Sig_Proc_X}}$. The condition of the transceiver is indicated on pin RX_ACTIVE (see [Figure 11-1 on page 51](#) and [Figure 11-2 on page 52](#)). The average current consumption in RX polling mode I_P is different in 1 battery application, 2 battery application or car application. To calculate I_P the index X must be replaced by VS1, 2 in 1 battery application, VS2 in 2 battery application or VS2, VAUX in car application (see section “[Electrical Characteristics: General](#)” on page 63)

$$I_P = \frac{I_{\text{IDLE_X}} \times T_{\text{Sleep}} + I_{\text{Startup_PLL_X}} \times T_{\text{Startup_PLL}} + I_{\text{RX_X}} \times (T_{\text{Startup_Sig_Proc}} + T_{\text{Bitcheck}})}{T_{\text{Sleep}} + T_{\text{Startup_PLL}} + T_{\text{Startup_Sig_Proc}} + T_{\text{Bit_check}}}$$

To save current it is recommended CLK and V_{VSOUT} be disabled during RX polling mode. I_P does not include the current of the Microcontroller_Interface I_{VSINT} and the current of an external device connected to pin VSOUT (e.g., microcontroller). If CLK and/or VSOUT is enabled during RX polling mode the current consumption is calculated as follows:

$$I_{\text{S_Poll}} = I_P + I_{\text{VSINT}} + I_{\text{EXT}}$$

During T_{Sleep} , $T_{\text{Startup_PLL}}$ and $T_{\text{Startup_Sig_Proc}}$ the transceiver is not sensitive to a transmitter signal. To guarantee the reception of a transmitted command the transmitter must start the telegram with an adequate preburst. The required length of the preburst T_{Preamble} depends on the polling parameters T_{Sleep} , $T_{\text{Startup_PLL}}$, $T_{\text{Startup_Sig_Proc}}$ and $T_{\text{Bit-check}}$. Thus, $T_{\text{Bit-check}}$ depends on the actual bit rate and the number of bits ($N_{\text{Bit-check}}$) to be tested

$$T_{\text{Preamble}} \geq T_{\text{Sleep}} + T_{\text{Startup_PLL}} + T_{\text{Startup_Sig_Proc}} + T_{\text{Bit_check}}$$

11.1.2 Sleep Mode

The length of period T_{Sleep} is defined by the 5-bit word sleep in control register 4, the extension factor X_{Sleep} defined by the bit XSleep in control register 4 and the basic clock cycle T_{DCLK} . It is calculated to be:

$$T_{\text{Sleep}} = \text{Sleep} \times 1024 \times T_{\text{DCLK}} \times X_{\text{Sleep}}$$

In US and European applications, the maximum value of T_{Sleep} is about 38 ms if X_{Sleep} is set to 1 (which is done by setting the bit XSleep in control register 4 to 0). The time resolution is about 1.2 ms in that case. The sleep time can be extended to about 300 ms by setting X_{Sleep} to 8 (which is done by setting XSleep in control register 4 to 1), the time resolution is then about 9.6 ms.

11.1.3 Start-up Mode

During $T_{\text{Startup_PLL}}$ the PLL is enabled and starts up. If the PLL is locked, the signal processing circuit starts up ($T_{\text{Startup_Sig_Proc}}$). After the start-up time all circuits are in stable condition and ready to receive.

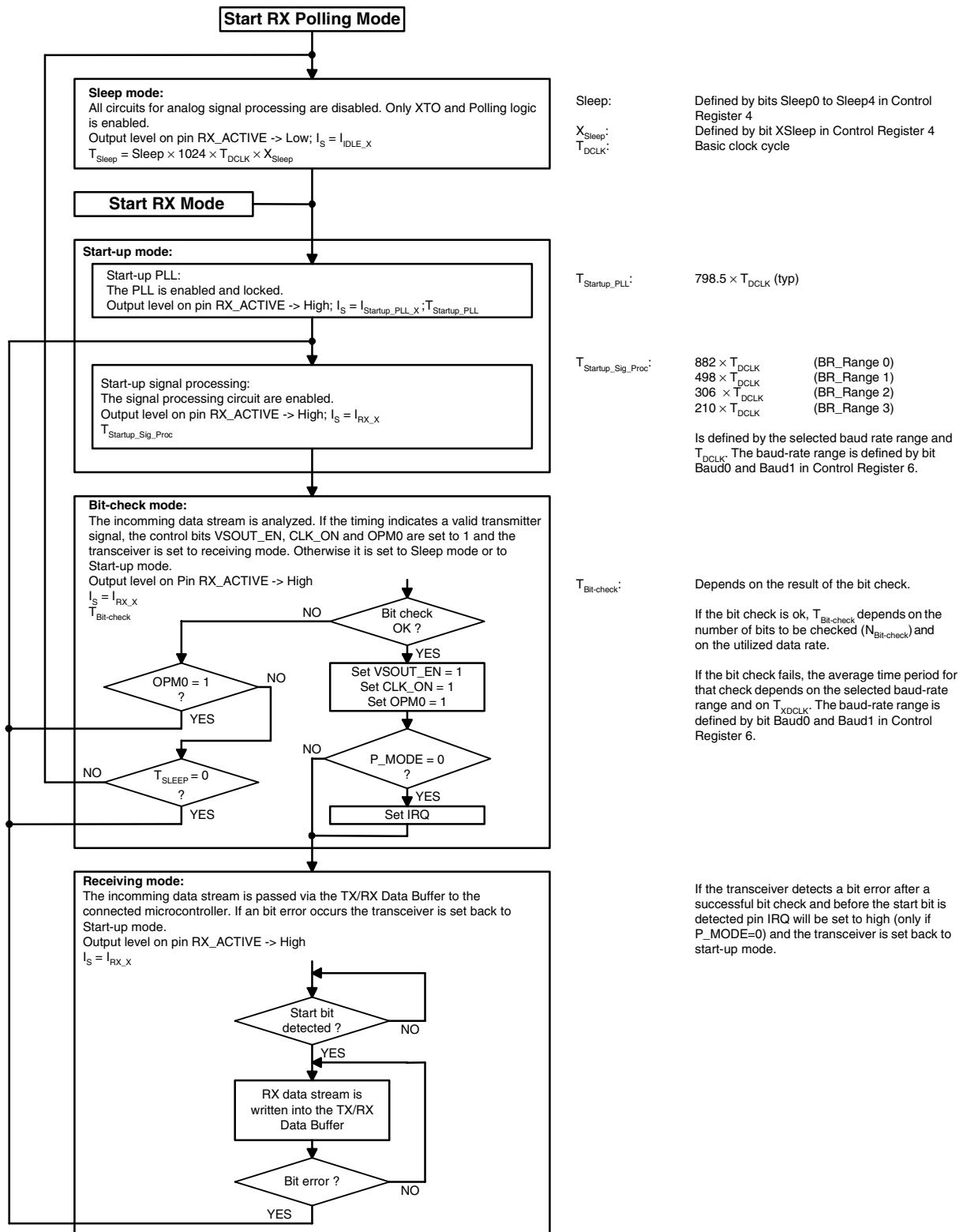
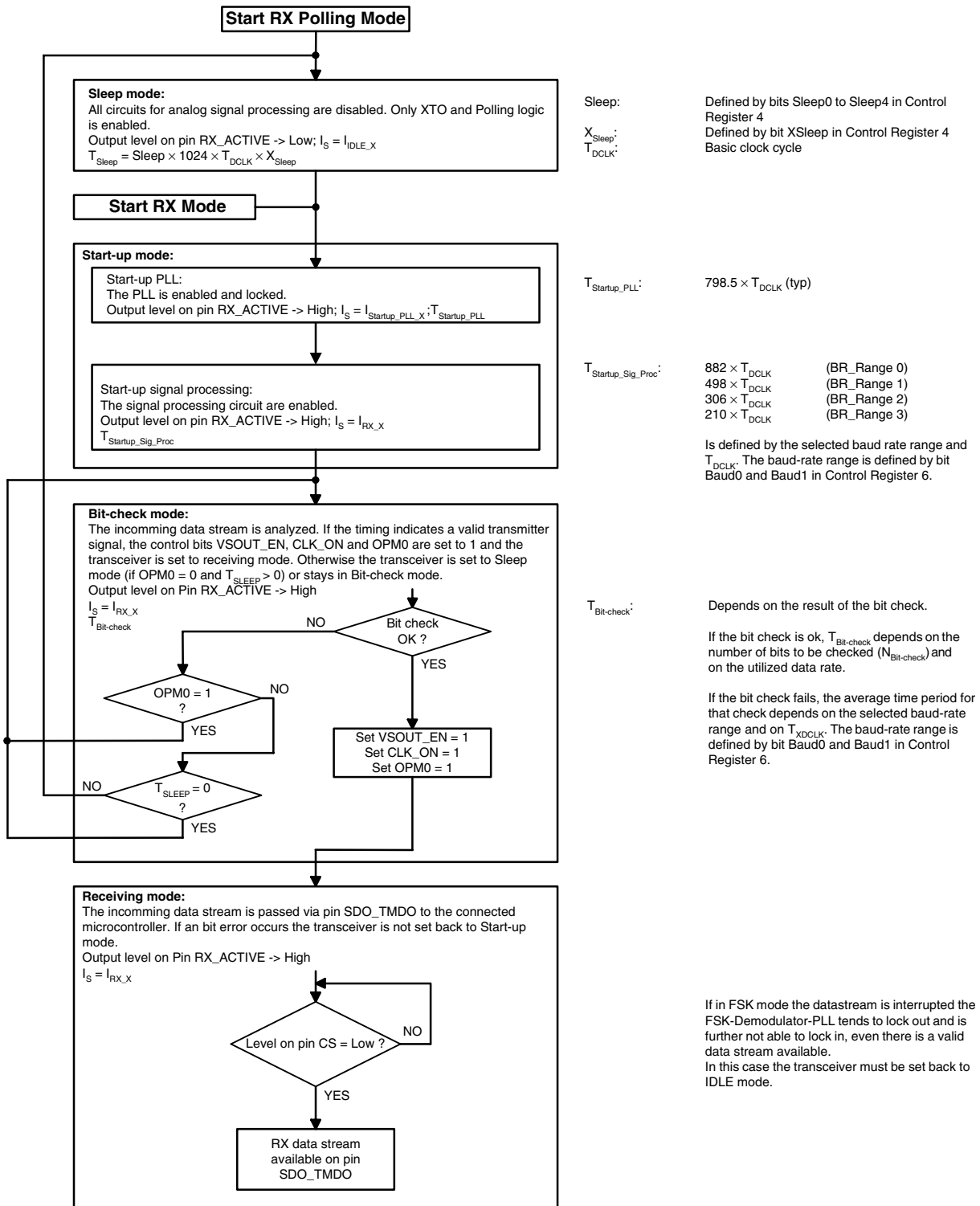
Figure 11-1. Flow Chart Polling Mode/RX Mode ($T_{MODE} = 1$, Transparent Mode Inactive)

Figure 11-2. Flow Chart Polling Mode/RX Mode (T_MODE = 1, Transparent Mode Active)



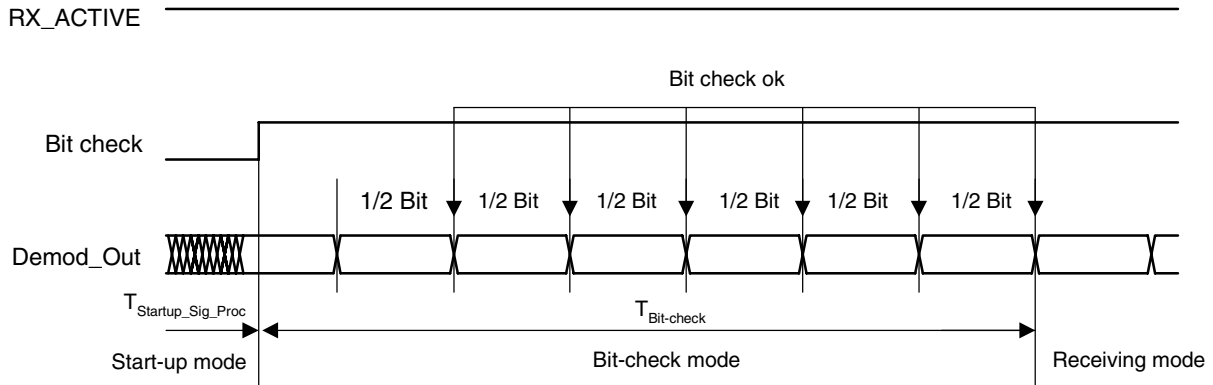
11.1.4 Bit-check Mode

In Bit-check mode the incoming data stream is examined to distinguish between a valid signal from a corresponding transmitter and signals due to noise. This is done by subsequent time frame checks where the distance between 2 signal edges are continuously compared to a programmable time window. The maximum count of this edge to edge test before the transceiver switches to receiving mode is also programmable.

11.1.5 Configuration the Bit-check

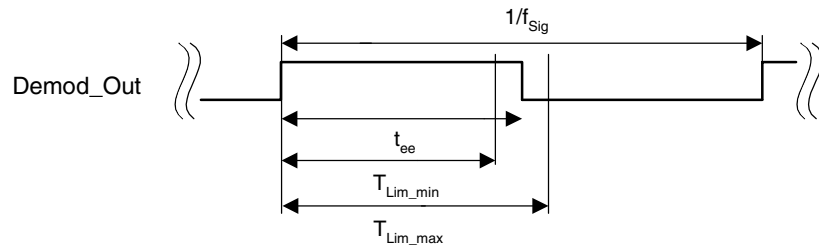
Assuming a modulation scheme that contains 2 edges per bit, two time frame checks are verifying one bit. This is valid for Manchester, Bi-phase and most other modulation schemes. The maximum count of bits to be checked can be set to 0, 3, 6 or 9 bits via the variable $N_{\text{Bit-check}}$ in control register 5. This implies 0, 6, 12 and 18 edge to edge checks respectively. If $N_{\text{Bit-check}}$ is set to a higher value, the transceiver is less likely to switch to receiving mode due to noise. In the presence of a valid transmitter signal, the Bit-check takes less time if $N_{\text{Bit-check}}$ is set to a lower value. In RX polling mode, the Bit-check time is not dependent on $N_{\text{Bit-check}}$. Figure 11-3 shows an example where 3 bits are tested successful.

Figure 11-3. Timing Diagram for Complete Successful Bit-check (Number of Checked Bits: 3)



According to Figure 11-4, the time window for the Bit-check is defined by two separate time limits. If the edge to edge time t_{ee} is in between the lower Bit-check limit $T_{\text{Lim_min}}$ and the upper Bit-check limit $T_{\text{Lim_max}}$, the check will be continued. If t_{ee} is smaller than limit $T_{\text{Lim_min}}$ or exceeds $T_{\text{Lim_max}}$, the Bit-check will be terminated and the transceiver switches to sleep mode.

Figure 11-4. Valid Time Window for Bit-check



For the best noise immunity it is recommended to use a low span between T_{Lim_min} and T_{Lim_max} . This is achieved using a fixed frequency at a 50% duty cycle for the transmitter preburst. A '11111...' or a '10101...' sequence in Manchester or Bi-phase is a good choice concerning that advice. A good compromise between sensitivity and susceptibility to noise regarding the expected edge to edge time t_{ee} is a time window of $\pm 38\%$, to get the maximum sensitivity the time window should be $\pm 50\%$ and then $N_{Bit-check} \geq 6$. Using preburst patterns that contain various edge to edge time periods, the Bit-check limits must be programmed according to the required span.

The Bit-check limits are determined by means of the formula below:

$$T_{Lim_min} = Lim_min \times T_{XDCLK}$$

$$T_{Lim_max} = (Lim_max - 1) \times T_{XDCLK}$$

Lim_min is defined by the bits Lim_min 0 to Lim_min 5 in control register 5.

Lim_max is defined by the bits Lim_max 0 to Lim_max 5 in control register 6.

Using the above formulas, Lim_min and Lim_max can be determined according to the required T_{Lim_min} , T_{Lim_max} and T_{XDCLK} . The time resolution defining T_{Lim_min} and T_{Lim_max} is T_{XDCLK} . The minimum edge to edge time t_{ee} is defined according to the section "Receiving Mode". The lower limit should be set to $Lim_min \geq 10$. The maximum value of the upper limit is $Lim_max = 63$.

Figure 11-5, Figure 11-6 on page 55, and Figure 11-7 on page 55 illustrate the Bit-check for the Bit-check limits $Lim_min = 14$ and $Lim_max = 24$. The signal processing circuits are enabled during $T_{Startup_PLL}$ and $T_{Startup_Sig_Proc}$. The output of the ASK/FSK demodulator (Demod_Out) is undefined during that period. When the Bit-check becomes active, the Bit-check counter is clocked with the cycle T_{XDCLK} .

Figure 11-5 shows how the Bit-check proceeds if the Bit-check counter value CV_Lim is within the limits defined by Lim_min and Lim_max at the occurrence of a signal edge. In Figure 11-6 on page 55 the Bit-check fails as the value CV_Lim is lower than the limit Lim_min . The Bit-check also fails if CV_Lim reaches Lim_max . This is illustrated in Figure 11-7 on page 55.

Figure 11-5. Timing Diagram During Bit-check

($Lim_min = 14$, $Lim_max = 24$)

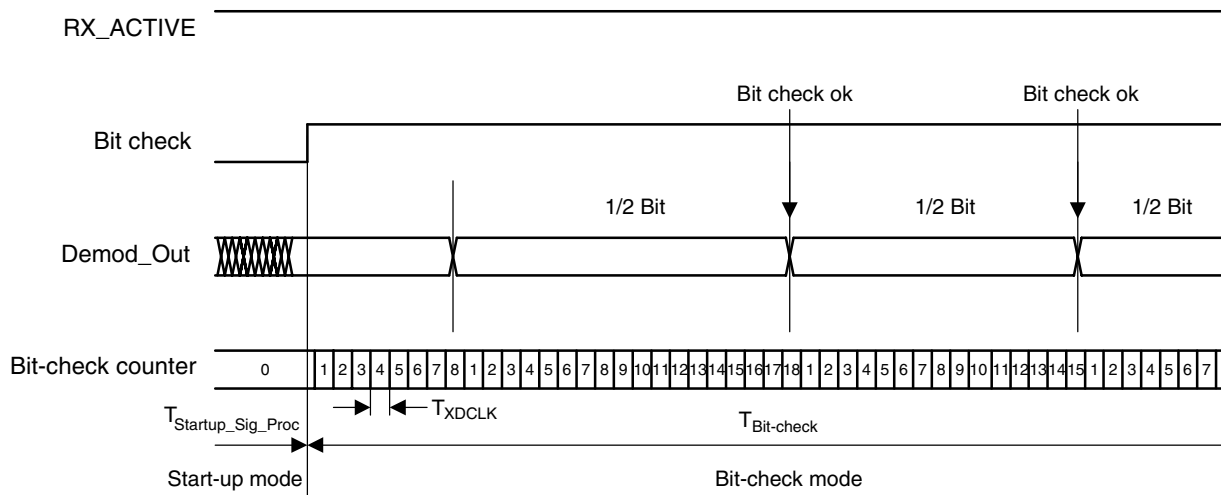
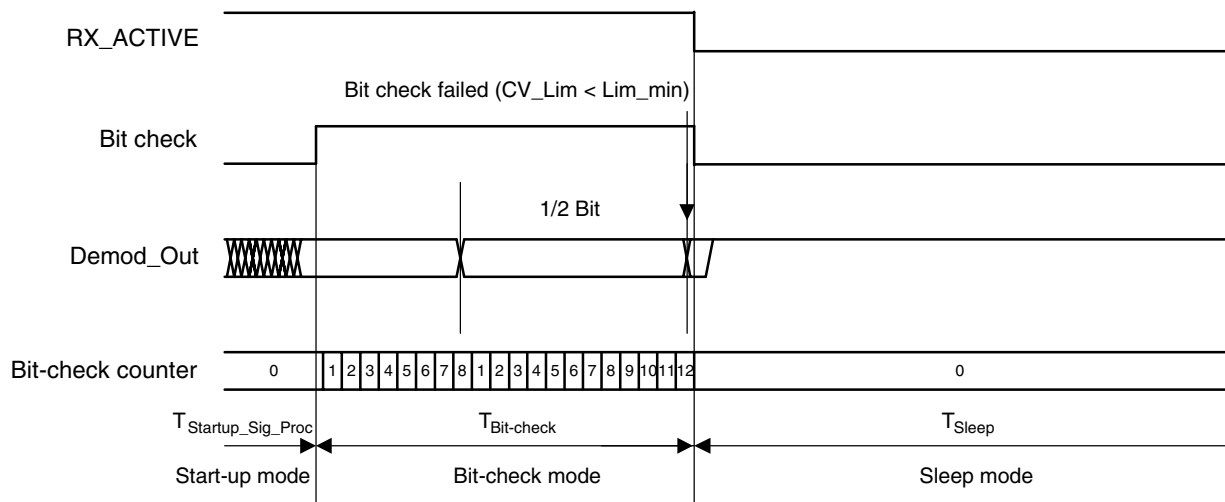
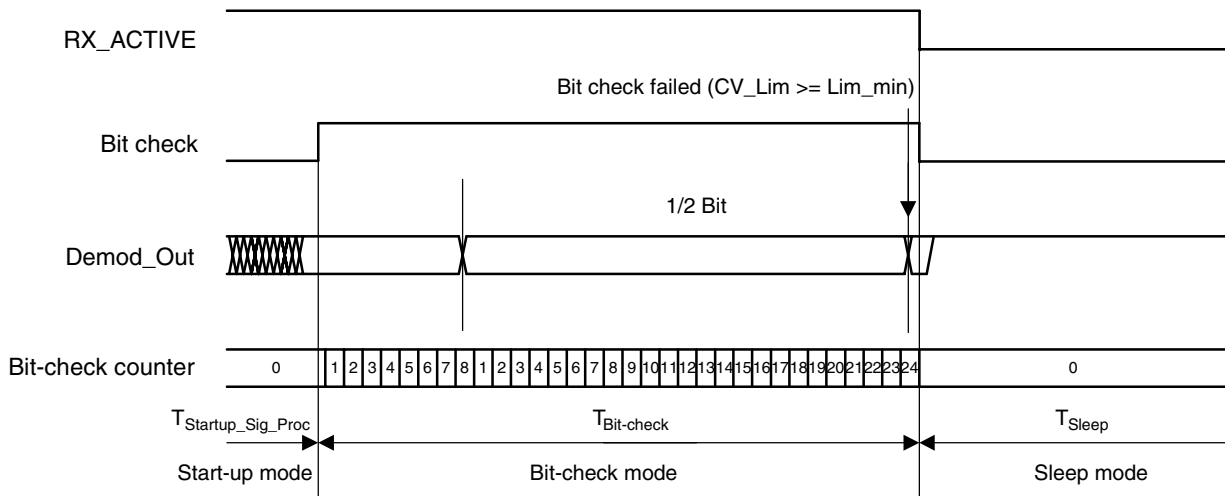


Figure 11-6. Timing Diagram for Failed Bit-check (Condition $CV_Lim < Lim_min$)

(Lim_min = 14, Lim_max = 24)

**Figure 11-7.** Timing Diagram for Failed Bit-check (Condition: $CV_Lim \geq Lim_max$)

(Lim_min = 14, Lim_max = 24)



11.1.6 Duration of the Bit-check

If no transmitter is present during the Bit-check, the output of the ASK/FSK demodulator delivers random signals. The Bit-check is a statistical process and $T_{Bit-check}$ varies for each check. Therefore, an average value for $T_{Bit-check}$ is given in the electrical characteristics. $T_{Bit-check}$ depends on the selected baud rate range and on T_{XDCLK} . A higher baud-rate range causes a lower value for $T_{Bit-check}$ resulting in a lower current consumption in RX polling mode.

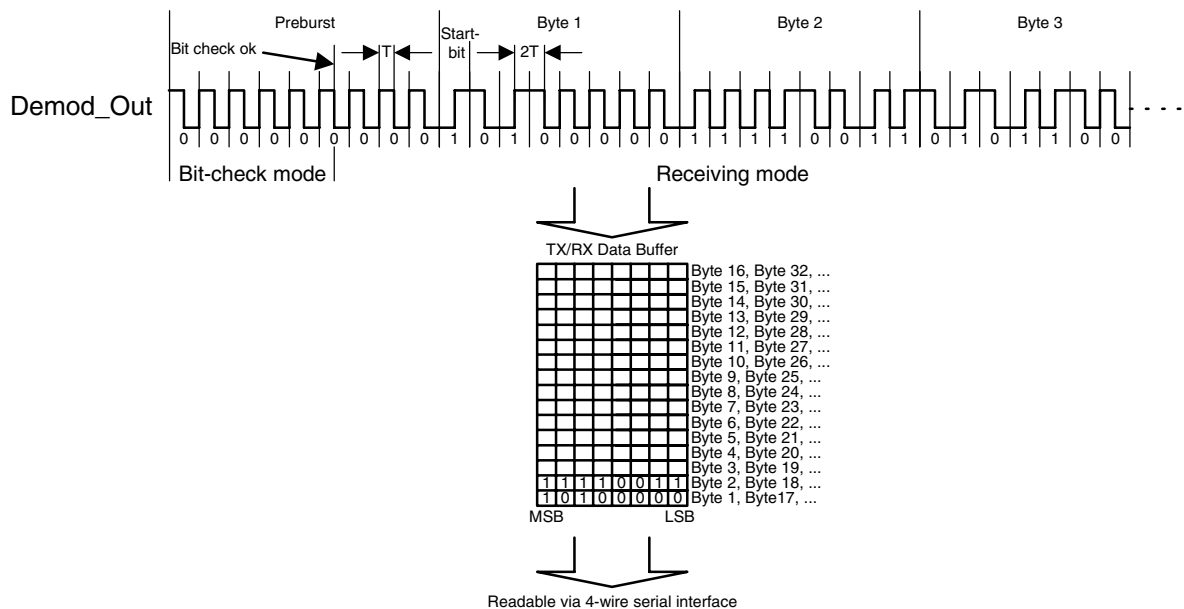
In the presence of a valid transmitter signal, $T_{Bit-check}$ is dependent on the frequency of that signal, f_{Sig} , and the count of the bits, $N_{Bit-check}$. A higher value for $N_{Bit-check}$ thereby results in a longer period for $T_{Bit-check}$ requiring a higher value for the transmitter preburst $T_{Preburst}$.

If the TX/RX data buffer control logic detects the start bit, the data stream is written in the TX/RX data buffer byte by byte. The start bit is part of the first data byte and must be different from the bits of the preburst. If the preburst consists of a sequence of '00000...', the start bit must be a 1. If the preburst consists of a sequence of '11111...', the start bit must be a 0.

If the data stream consists of more than 16 bytes, a buffer overflow occurs and the TX/RX data buffer control logic overwrites the bytes already stored in the TX/RX data buffer. So it is very important to ensure that the data is read in time so that no buffer overflow occurs in that case (see [Figure 10-1 on page 46](#)). There is a counter that indicates the number of received bytes in the TX/RX data buffer (see section "Transceiver Configuration"). If a byte is transferred to the microcontroller, the counter is decremented, if a byte is received, the counter is incremented. The counter value is available via the 4-wire serial interface.

An interrupt is issued, if the counter while counting forwards reaches the value defined by the control bits IR0 and IR1 in control register 1.

Figure 11-9. Receiving Mode (TMODE = 0)



If the TX/RX data buffer control logic detects a bit error, an interrupt is issued and the transceiver is set back to the start-up mode (see [Figure 11-1 on page 51](#), [Figure 11-2 on page 52](#) and [Figure 11-10 on page 58](#)).

- Bit error:
- $t_{ee} < T_{Lim_min}$ or $T_{Lim_max} < t_{ee} < T_{Lim_min_2T}$ or $t_{ee} > T_{Lim_max_2T}$
 - Logical error (no edge detected in the bit center)

Note: The byte consisting of the bit error will not be stored in the TX/RX data buffer. Thus it is not available via the 4-wire serial interface.

Writing the control register 1, 4, 5 or 6 during receiving mode resets the TX/RX data buffer control logic and the counter which indicates the number of received bytes. If the bits OPM0 and OPM1 are still '1' after writing to a control register, the transceiver changes to the start-up mode (start-up signal processing).

Figure 11-10. Bit Error (TMODE = 0)

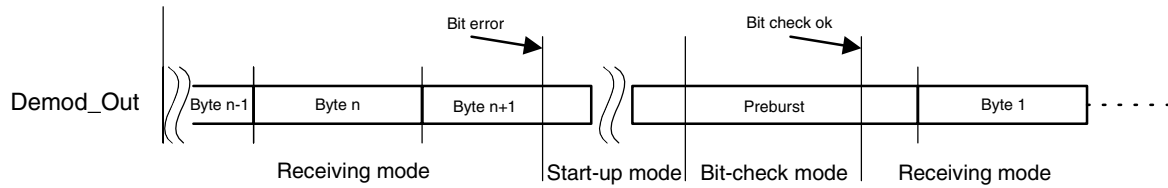


Table 11-2. RX Modulation Scheme

| Mode | ASK/_NFSK | T_MODE | RF _{IN} | Bit in TX/RX Data Buffer | Level on Pin SD0_TMDO |
|------|-----------|--------|--|--------------------------|-----------------------|
| RX | 0 | 0 | $f_{FSK_L} \rightarrow f_{FSK_H}$ | 1 | Z |
| | | 0 | $f_{FSK_H} \rightarrow f_{FSK_L}$ | 0 | Z |
| | | 1 | f_{FSK_H} | — | 1 |
| | | 1 | f_{FSK_L} | — | 0 |
| | 1 | 0 | $f_{ASK} \text{ off} \rightarrow f_{ASK} \text{ on}$ | 1 | Z |
| | | 0 | $f_{ASK} \text{ on} \rightarrow f_{ASK} \text{ off}$ | 0 | Z |
| | | 1 | $f_{ASK} \text{ on}$ | — | 1 |
| | | 1 | $f_{ASK} \text{ off}$ | — | 0 |

11.1.8 Recommended Lim_min and Lim_max for Maximum Sensitivity

The sensitivity measurement in the section “Low-IF Receiver” in [Table 5-3 on page 11](#) and [Table 5-4 on page 11](#) have been done with the Lim_min and Lim_max values according to [Table 11-3](#). These values are optimized for maximum sensitivity. Note that since these Limits are optimized for sensitivity the number of checked bit $N_{\text{Bit-check}}$ has to be at least 6 to prevent the circuit from waking up to a often in polling mode due to noise.

Table 11-3. Recommended Lim_min and Lim_max Values for Different Baud Rates

| $f_{RF} (f_{XTAL})$ / MHz | 1.0 kBaud BR_Range_0/XLim = 1 | 2.4 kBaud BR_Range_0/XLim = 0 | 5 kBaud BR_Range_1/XLim = 0 | 10 Kbaud BR_Range_2/XLim = 0 | 20 kBaud BR_Range_3/XLim = 0 |
|------------------------------|--|--|---|--|--|
| 315.0 (12.73193) | Lim_min = 13 (261 μ s) Lim_max = 38 (744 μ s) | Lim_min = 12 (121 μ s) Lim_max = 34 (332 μ s) | Lim_min = 11 (55 μ s) Lim_max = 32 (156 μ s) | Lim_min = 11 (28 μ s) Lim_max = 32 (78 μ s) | Lim_min = 11 (14 μ s) Lim_max = 31 (38 μ s) |
| 433.92 (13.25311) | Lim_min = 13 (251 μ s) Lim_max = 38 (715 μ s) | Lim_min = 12 (116 μ s) Lim_max = 34 (319 μ s) | Lim_min = 11 (53 μ s) Lim_max = 32 (150 μ s) | Lim_min = 11 (27 μ s) Lim_max = 32 (75 μ s) | Lim_min = 11 (13 μ s) Lim_max = 32 (37 μ s) |
| 868.3 (13.41191) | Lim_min = 13 (248 μ s) Lim_max = 38 (706 μ s) | Lim_min = 12 (115 μ s) Lim_max = 34 (315 μ s) | Lim_min = 11 (52 μ s) Lim_max = 32 (148 μ s) | Lim_min = 11 (26 μ s) Lim_max = 32 (74 μ s) | Lim_min = 11 (13 μ s) Lim_max = 32 (37 μ s) |

11.2 TX Operation

The transceiver is set to TX operation by using the bits OPM0 and OPM1 in the control register 1.

Table 11-4. Control Register 1

| OPM1 | OPM0 | Function |
|------|------|----------|
| 0 | 1 | TX mode |

Before activating TX mode, the TX parameters (baud rate, modulation scheme ...) must be selected as illustrated in [Figure 11-11 on page 60](#). The baud rate depends on Baud 0 and Baud 1 in control register 6, Lim_min0 to Lim_min5 in control register 5 and XLIM in control register 4 (see section [“Control Register” on page 35](#)). The modulation is selected with ASK_/NFSK in control register 4. The FSK frequency deviation is fixed to about ± 16 kHz. If P_Mode is set to 1, the Manchester modulator is disabled and pattern mode is active (NRZ, see [Table 11-5 on page 62](#)).

After the transceiver is set to TX mode the start-up mode is active and the PLL is enabled. If the PLL is locked, the TX mode is active.

If the transceiver is in start-up or TX mode, the TX/RX data buffer can be loaded via the 4-wire serial interface. After the first byte is in the buffer and the TX mode is active, the transceiver starts transmitting automatically (beginning with the MSB). While transmitting it is permanently possible to load new data in the TX/RX data buffer. To prevent a buffer overflow or interruptions during transmitting the user must ensure that data is loaded at the same speed as it is transmitted.

There is a counter that indicates the number of bytes to be transmitted (see section [“Transceiver Configuration” on page 46](#)). If a byte is loaded, the counter is incremented, if a byte is transmitted, the counter is decremented. The counter value is available via the 4-wire serial interface. An IRQ is issued, if the counter while counting backwards reaches the value defined by the control bits IR0 and IR1 in control register 1.

Note: Writing to the control register 1, 4, 5 or 6 during TX mode, resets the TX/RX data buffer and the counter which indicates the number of bytes to be transmitted.

If T_Mode in control register 1 is set to 1, the transceiver is in TX transparent mode. In this mode the TX/RX data buffer is disabled and the TX data stream must be applied on pin SDI_TMDI. [Figure 11-11 on page 60](#) illustrates the flow chart of the TX transparent mode.

Figure 11-11. TX Operation (T_MODE = 0)

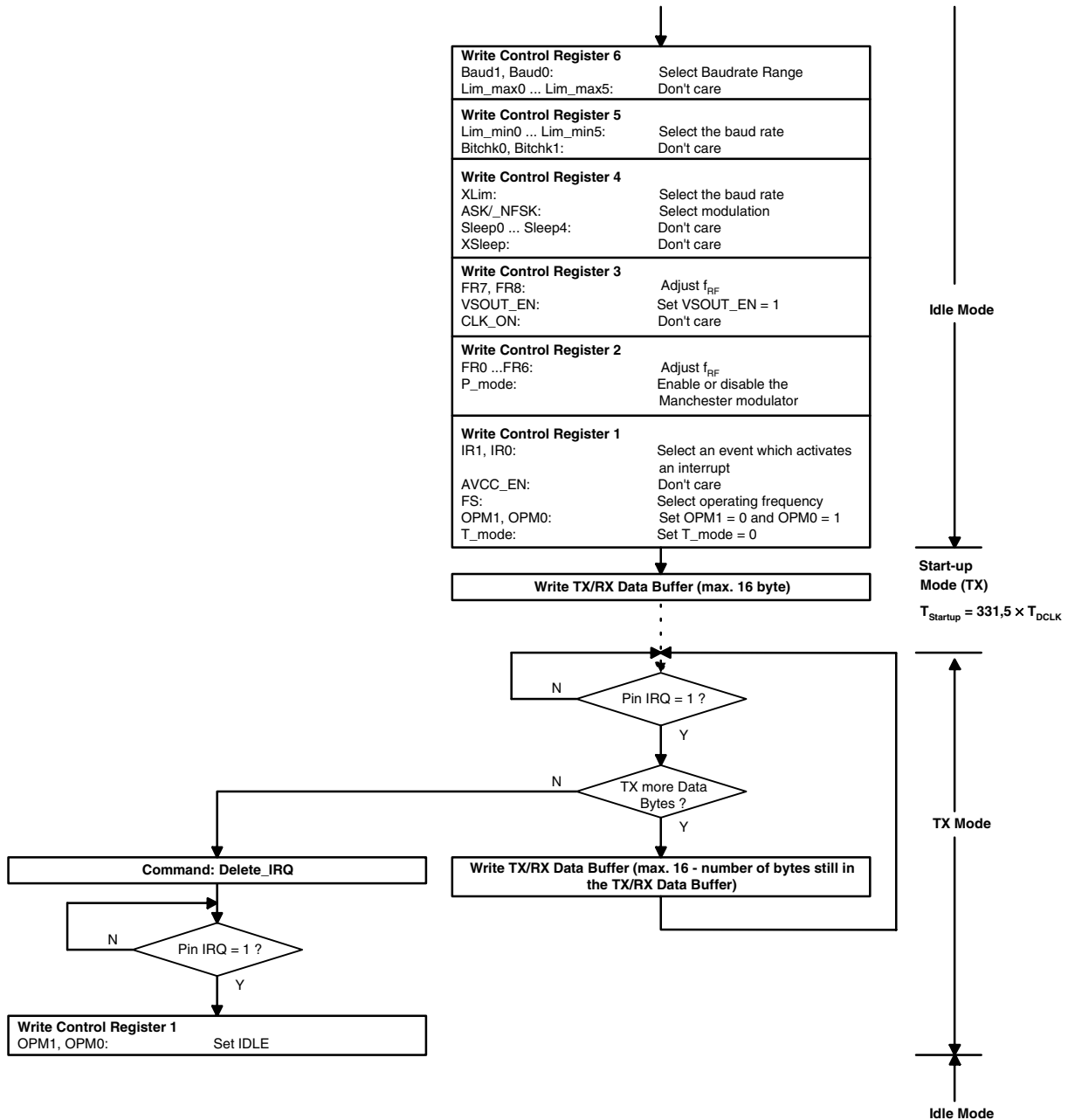


Figure 11-12. TX Transparent Mode (T_MODE = 1)

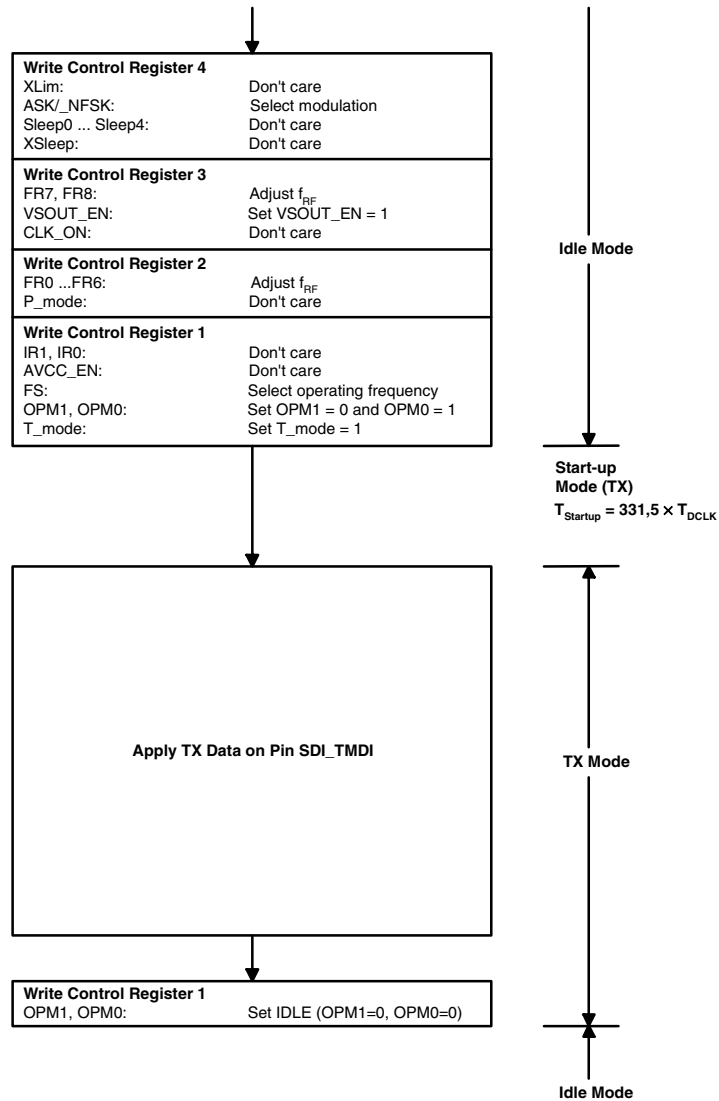


Table 11-5. TX Modulation Schemes

| Mode | ASK/_NFSK | P_Mode | T_Mode | Bit in TX/RX Data Buffer | Level on Pin SDI_TMDI | RF _{OUT} |
|------|-----------|--------|--------|--------------------------|-----------------------|--|
| TX | 0 | 0 | 0 | 1 | X | $f_{FSK_L} \rightarrow f_{FSK_H}$ |
| | | 0 | 0 | 0 | X | $f_{FSK_H} \rightarrow f_{FSK_L}$ |
| | | 1 | 0 | 1 | X | f_{FSK_H} |
| | | 1 | 0 | 0 | X | f_{FSK_L} |
| | | X | 1 | X | 1 | f_{FSK_H} |
| | | X | 1 | X | 0 | f_{FSK_L} |
| | 1 | 0 | 0 | 1 | X | $f_{ASK\ off} \rightarrow f_{ASK\ on}$ |
| | | 0 | 0 | 0 | X | $f_{ASK\ on} \rightarrow f_{ASK\ off}$ |
| | | 1 | 0 | 1 | X | $f_{ASK\ on}$ |
| | | 1 | 0 | 0 | X | $f_{ASK\ off}$ |
| | | X | 1 | X | 1 | $f_{ASK\ on}$ |
| | | X | 1 | X | 0 | $f_{ASK\ off}$ |

11.3 Interrupts

Via pin IRQ, the transceiver signals different operating conditions to a connected microcontroller. If a specific operating condition occurs, pin IRQ is set to high level.

If an interrupt occurs it is recommended to delete the interrupt be immediately deleted by reading the status register, thus the next possible interrupt doesn't get lost. If the Interrupt pin doesn't switch to low level by reading the status register the interrupt was triggered by the RX/TX data buffer. In this case read or write the RX/TX data buffer according to [Table 11-6](#).

Table 11-6. Interrupt Handling

| Operating Conditions Which Sets Pin IRQ to High Level | Operations Which Sets Pin IRQ to Low Level |
|--|---|
| Events in Status Register | |
| State transition of status bit STn (0 → 1; 1 → 0) | Read status register or Command Delete IRQ |
| Appearance of status bit Power_On (0 → 1) | |
| Appearance of status bit P_On_Aux (0 → 1) | |
| Events During TX Operation (T_MODE = 0) | |
| 4, 8 or 12 Bytes are in the TX data buffer or the TX data buffer is empty (depends on IR0 and IR1 in control register 1). | Write TX data buffer or Write control register 1 or Write control register 4 or Write control register 5 or Write control register 6 or Command delete IRQ |
| Events During RX Operation (T_MODE = 0) | |
| 4, 8 or 12 received bytes are in the RX data buffer or a receiving error is occurred (depends on IR0 and IR1 in control register 1). | Read RX data buffer or Write control register 1 or Write control register 4 or Write control register 5 or Write control register 6 or Command delete IRQ |
| Successful Bit-check (P_MODE = 0) | |

12. Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

| Parameters | Symbol | Min. | Max. | Unit |
|---|----------------|------|------|------|
| Junction temperature | T_j | | 150 | °C |
| Storage temperature | T_{stg} | –55 | +125 | °C |
| Ambient temperature | T_{amb} | –40 | +105 | °C |
| Supply voltage VS2 | V_{MaxVS2} | –0.3 | +7.2 | V |
| Supply voltage VS1 | V_{MaxVS1} | –0.3 | +4 | V |
| Supply voltage VAUX | $V_{MaxVAUX}$ | –0.3 | +7.2 | V |
| Supply voltage VSINT | $V_{MaxVSINT}$ | –0.3 | +5.5 | V |
| ESD (Human Body Model ESD S 5.1) every pin | HBM | –2 | +2 | kV |
| ESD (Machine Model JEDEC A115A) every pin | MM | –200 | +200 | V |
| Maximum input level, input matched to 50 Ω | P_{in_max} | | 10 | dBm |

13. Thermal Resistance

| Parameters | Symbol | Value | Unit |
|------------------|------------|-------|------|
| Junction ambient | R_{thJA} | 25 | K/W |

14. Electrical Characteristics: General

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|------------------------------|--|--------------------|--------------|------|------|------|------|-------|
| 1 | RX_TX_IDLE Mode | | | | | | | | |
| 1.1 | RF operating frequency range | ATA5811 $V_{433_N868} = 0\text{ V}$ | 4, 10 | f_{RF} | 867 | | 870 | MHz | A |
| | | ATA5811 $V_{433_N868} = AVCC$ | 4, 10 | f_{RF} | 433 | | 435 | MHz | A |
| | | ATA5812 $V_{433_N868} = 0\text{ V}$ | 4, 10 | f_{RF} | 313 | | 316 | MHz | A |
| 1.2 | Supply current OFF mode | $V_{VS1} = V_{VS2} = 3\text{ V}$, $V_{VSINT} = 0\text{ V}$ (1 battery) and $V_{VS2} = 6\text{ V}$ (2 battery) OFF mode is not available if $V_{VS2} = V_{VAUX} = 5\text{ V}$ $V_{VSINT} = 0\text{ V}$ (car) | | I_{S_OFF} | | <10 | | nA | A |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to 50 Ω according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to 50 Ω according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the "Electrical Characteristics".

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|----------|---|---|--------------------|---|--------|--------|--------|---------------|-------|
| 1.3 | Supply current Idle mode | V_{VSOUT} disabled, XTO running $V_{VS1} = V_{VS2} = 3\text{V}$ (1 battery) | | I_{S_IDLE} | | 220 | | μA | B |
| | | $V_{VS2} = 6\text{V}$ (2 battery) | | I_{S_IDLE} | | 310 | | μA | B |
| | | $V_{VS2} = V_{VAUX} = 5\text{V}$ (car) | | I_{S_IDLE} | | 310 | | μA | B |
| 1.4 | System start-up time | From OFF mode to Idle mode including reset and XTO start-up (see Figure 9-4 on page 43) XTAL: $C_m = 5\text{ fF}$, $C_0 = 1.8\text{ pF}$, $R_m = 15\Omega$ | | $T_{PWR_ON_IRQ_1}$ | | 0.3 | | ms | C |
| 1.5 | RX start-up time | From Idle mode to receiving mode $N_{\text{Bit-check}} = 3$ Baud rate = 20 kBaud, BR_Range_3 (see Figure 11-1 on page 51 , Figure 11-2 on page 52 and Figure 11-3 on page 53) | | $T_{\text{Startup_PLL}} +$ $T_{\text{Startup_Sig_Proc}}$ $+ T_{\text{Bit-chek}}$ | | 1.39 | | ms | A |
| 1.6 | TX start-up time | From Idle mode to TX mode (see Figure 11-11 on page 60) | | T_{Startup} | | 0.4 | | ms | A |
| 2 | Receiver/RX Mode | | | | | | | | |
| 2.1 | Supply current RX mode | $f_{RF} = 433.92\text{ MHz}$ and $f_{RF} = 315\text{ MHz}$ | 17, 18 | I_{S_RX} | | 10.5 | | mA | A |
| | | $f_{RF} = 868\text{ MHz}$ | 17, 18 | I_{S_RX} | | 10.3 | | mA | A |
| 2.2 | Supply current RX polling mode | $T_{\text{Sleep}} = 49.45\text{ ms}$ $X_{\text{SLEEP}} = 8$, Sleep = 5 Baud rate = 20 kBaud FSK, V_{VSOUT} disabled | 17, 18 | I_P | | 444 | | μA | B |
| 2.3 | Input sensitivity FSK $f_{RF} = 433.92\text{ MHz}$ | FSK deviation $f_{DEV} = \pm 16\text{ kHz}$ limits according to Table 11-3 on page 58 , $BER = 10^{-3}$ $T_{amb} = 25^{\circ}\text{C}$ | | | | | | | |
| | | Baud rate 20 kBaud | (4) | P_{REF_FSK} | -104.0 | -106.0 | -107.5 | dBm | B |
| | | Baud rate 2.4 kBaud | (4) | P_{REF_FSK} | -107.5 | -109.5 | -111.0 | dBm | B |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to 50 Ω according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to 50 Ω according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|--|--|--------------------|---------------------|----------|------------------|----------|------|-------|
| 2.4 | Input sensitivity ASK $f_{RF} = 433.92\text{ MHz}$ | ASK 100%, level of carrier limits according to Table 11-3 on page 58 , $\text{BER} = 10^{-3}$ $T_{amb} = 25^{\circ}\text{C}$ | | | | | | | |
| | | Baud rate 10 kBaud | (4) | P_{REF_ASK} | -110.5 | -112.5 | -114.0 | dBm | B |
| | | Baud rate 2.4 kBaud | (4) | P_{REF_ASK} | -114.5 | -116.5 | -118.0 | dBm | B |
| 2.5 | Sensitivity change at $f_{RF} = 315.0\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ compared to $f_{RF} = 433.92\text{ MHz}$ | $f_{RF} = 433.92\text{ MHz}$ to $f_{RF} = 315.00\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ to $f_{RF} = 868.00\text{ MHz}$ $P = P_{REF_ASK} + \Delta P_{REF1} + \Delta P_{REF2}$ $P = P_{REF_FSK} + \Delta P_{REF1} + \Delta P_{REF2}$ | (4) | ΔP_{REF1} | | -1.0 +2.7 | | dB | B |
| 2.6 | Maximum frequency offset in FSK mode | Maximum frequency difference of f_{RF} between receiver and transmitter in FSK mode (f_{RF} is the center frequency of the FSK signal with $f_{DEV} = \pm 16\text{ kHz}$) | (4) | Δf_{OFFSET} | -58 | | +58 | kHz | B |
| 2.7 | Sensitivity change versus temperature, supply voltage and frequency offset | FSK $f_{DEV} = \pm 16\text{ kHz}$ $\Delta f_{OFFSET} \leq 58\text{ kHz}$ ASK 100% $\Delta f_{OFFSET} \leq 58\text{ kHz}$ $P = P_{REF_ASK} + \Delta P_{REF1} + \Delta P_{REF2}$ $P = P_{REF_FSK} + \Delta P_{REF1} + \Delta P_{REF2}$ | (4) | ΔP_{REF2} | +4.5 | | -1.5 | | B |
| 2.8 | Supported FSK frequency deviation | With up to 2 dB loss of sensitivity. Note that the tolerable frequency offset is for $f_{DEV} = \pm 22\text{ kHz}$, 6 kHz lower than for $f_{DEV} = \pm 16\text{ kHz}$ hence $\Delta f_{OFFSET} \leq \pm 52\text{ kHz}$ | (4) | f_{DEV} | ± 14 | ± 16 | ± 22 | kHz | B |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\ \Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\ \Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|---|--|--------------------|---------------|------|-------------|------|----------|-------|
| 2.9 | System noise figure | $f_{RF} = 315\text{ MHz}$ | (4) | NF | | 6.0 | | dB | B |
| | | $f_{RF} = 433.92\text{ MHz}$ | (4) | NF | | 7.0 | | dB | B |
| | | $f_{RF} = 868.3\text{ MHz}$ | (4) | NF | | 9.7 | | dB | B |
| 2.10 | Intermediate frequency | $f_{RF} = 868.3\text{ MHz}$ | | f_{IF} | | 226 | | kHz | A |
| | | $f_{RF} = 433.92\text{ MHz}$ | | f_{IF} | | 223 | | kHz | A |
| | | $f_{RF} = 315\text{ MHz}$ | | f_{IF} | | 227 | | kHz | A |
| 2.11 | System bandwidth | This value is for information only! Note that for crystal and system frequency offset calculations, Δf_{OFFSET} must be used. | (4) | SBW | | 185 | | kHz | A |
| 2.12 | System outband 2nd-order input intercept point with respect to f_{IF} | $\Delta f_{meas1} = 1,800\text{ MHz}$ $\Delta f_{meas2} = 2,026\text{ MHz}$ $f_{IF} = \Delta f_{meas2} - \Delta f_{meas1}$ | (4) | IIP2 | | +50 | | dBm | C |
| 2.13 | System outband 3rd-order input intercept point | $\Delta f_{meas1} = 1.8\text{ MHz}$ $\Delta f_{meas2} = 3.6\text{ MHz}$ $f_{RF} = 315\text{ MHz}$ | (4) | IIP3 | | -22 | | dBm | C |
| | | $f_{RF} = 433.92\text{ MHz}$ | (4) | IIP3 | | -21 | | dBm | C |
| | | $f_{RF} = 868.3\text{ MHz}$ | (4) | IIP3 | | -17 | | dBm | C |
| 2.14 | System outband input 1 dB compression point | $\Delta f_{meas1} = 10\text{ MHz}$ $f_{RF} = 315\text{ MHz}$ | (4) | I1dBCP | | -31 | | dBm | C |
| | | $f_{RF} = 433.92\text{ MHz}$ | (4) | I1dBCP | | -30 | | dBm | C |
| | | $f_{RF} = 868.3\text{ MHz}$ | (4) | I1dBCP | | -27 | | dBm | C |
| 2.15 | LNA input impedance | $f_{RF} = 315\text{ MHz}$ | 4 | Z_{in_LNA} | | (44 - j233) | | Ω | C |
| | | $f_{RF} = 433.92\text{ MHz}$ | 4 | Z_{in_LNA} | | (32 - j169) | | Ω | C |
| | | $f_{RF} = 868.3\text{ MHz}$ | 4 | Z_{in_LNA} | | (21 - j78) | | Ω | C |
| 2.16 | Maximum peak RF input level, ASK and FSK | $\text{BER} < 10^{-3}$, ASK: 100% | (4) | P_{IN_max} | -10 | +10 | | dBm | C |
| | | FSK: $f_{DEV} = \pm 16\text{ kHz}$ | (4) | P_{IN_max} | -10 | +10 | | dBm | C |
| 2.17 | LO spurious at LNA_IN | $f < 1\text{ GHz}$ | (4) | | | | -57 | dBm | C |
| | | $f > 1\text{ GHz}$ | (4) | | | | -47 | dBm | C |
| | | $f_{RF} = 315\text{ MHz}$ | (4) | | | -100 | | dBm | C |
| | | $f_{RF} = 433.92\text{ MHz}$ | (4) | | | -97 | | dBm | C |
| | | $f_{RF} = 868.3\text{ MHz}$ | (4) | | | -84 | | dBm | C |
| 2.18 | Image rejection | Within the complete image band | (4) | | 20 | 30 | | dB | A |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to 50 Ω according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to 50 Ω according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|-----------------------------------|---|--------------------|------------------------------|---------|------------------------|------------|-------------------|-------|
| 2.19 | Useful signal to interferer ratio | Peak level of useful signal to peak level of interferer for $\text{BER} < 10^{-3}$ with any modulation scheme of interferer | | | | | | | |
| | | FSK BR_Ranges 0, 1, 2 | (4) | $\text{SNR}_{\text{FSK0-2}}$ | | 2 | 3 | dB | B |
| | | FSK BR_Range_3 | (4) | SNR_{FSK3} | | 4 | 6 | dB | B |
| | | ASK ($P_{\text{RF}} < P_{\text{RFIN_High}}$) | (4) | SNR_{ASK} | | 10 | 12 | dB | B |
| 2.20 | RSSI output | Dynamic range | (4), 36 | D_{RSSI} | | 70 | | dB | A |
| | | Lower level of range $f_{\text{RF}} = 315\text{ MHz}$ $f_{\text{RF}} = 433.92\text{ MHz}$ $f_{\text{RF}} = 868.3\text{ MHz}$ | (4), 36 | $P_{\text{RFIN_Low}}$ | | -116 -115 -112.3 | | dBm dBm dBm | A |
| | | Upper level of range $f_{\text{RF}} = 315\text{ MHz}$ $f_{\text{RF}} = 433.92\text{ MHz}$ $f_{\text{RF}} = 868.3\text{ MHz}$ | (4), 36 | $P_{\text{RFIN_High}}$ | | -46 -45 -42.3 | | dBm dBm dBm | A |
| | | Gain | (4), 36 | | 5.5 | 8.0 | 10.5 | mV/dB | A |
| | | Output voltage range | (4), 36 | OV_{RSSI} | 400 | | 1100 | mV | A |
| | | | | | | | | | |
| 2.21 | Output resistance RSSI pin | RX mode TX mode | 36 | R_{RSSI} | 8 32 | 10 40 | 12.5 50 | k Ω | C |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\ \Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\ \Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|--|---|--------------------|--------------------|------|----------------------------|------|------|-------|
| 2.22 | Blocking | Sensitivity (BER = 10^{-3}) is reduced by 6 dB if a continuous wave blocking signal at $\pm\Delta f$ is ΔP_{Block} higher than the useful signal level (baud rate = 20 kBaud, FSK, $f_{DEV} \pm 16\text{kHz}$, Manchester code) | | | | | | | |
| | | $f_{RF} = 315\text{ MHz}$ $\Delta f \pm 0.75\text{ MHz}$ $\Delta f \pm 1.0\text{ MHz}$ $\Delta f \pm 1.5\text{ MHz}$ $\Delta f \pm 5\text{ MHz}$ $\Delta f \pm 10\text{ MHz}$ | (4) | ΔP_{Block} | | 56 60 63 69 71 | | dBc | C |
| | | $f_{RF} = 433.92\text{ MHz}$ $\Delta f \pm 0.75\text{ MHz}$ $\Delta f \pm 1.0\text{ MHz}$ $\Delta f \pm 1.5\text{ MHz}$ $\Delta f \pm 5\text{ MHz}$ $\Delta f \pm 10\text{ MHz}$ | (4) | ΔP_{Block} | | 55 59 62 68 70 | | dBc | C |
| | | $f_{RF} = 868.3\text{ MHz}$ $\Delta f \pm 0.75\text{ MHz}$ $\Delta f \pm 1.0\text{ MHz}$ $\Delta f \pm 1.5\text{ MHz}$ $\Delta f \pm 5\text{ MHz}$ $\Delta f \pm 10\text{ MHz}$ | (4) | ΔP_{Block} | | 50 53 57 67 69 | | dBc | C |
| 2.23 | CDEM | C_6 in Figure 2-1 on page 6 , Figure 3-1 on page 7 and Figure 4-1 on page 8 | 37 | | -5% | 15 | +5% | nF | D |
| 3 | Power Amplifier/TX Mode | | | | | | | | |
| 3.1 | Supply current TX mode power amplifier OFF | $f_{RF} = 868.3\text{ MHz}$ | | $I_{S_TX_PAOFF}$ | | 6.50 | | mA | A |
| | | $f_{RF} = 433.92\text{ MHz}$ and $f_{RF} = 315\text{ MHz}$ | | $I_{S_TX_PAOFF}$ | | 6.95 | | mA | A |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\ \Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\ \Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|--|---|--------------------|--------------------|------|------|------|------|-------|
| 3.2 | Output power 1 | $V_{VS1} = V_{VS2} = 3\text{V}$ $T_{amb} = 25^{\circ}\text{C}$ $V_{PWR_H} = 0\text{V}$ $f_{RF} = 315\text{ MHz}$ $R_{R_PWR} = 56\text{ k}\Omega$ $R_{Lopt} = 2.5\text{ k}\Omega$ $f_{RF} = 433.92\text{ MHz}$ $R_{R_PWR} = 56\text{ k}\Omega$ $R_{Lopt} = 2.3\text{ k}\Omega$ $f_{RF} = 868.3\text{ MHz}$ $R_{R_PWR} = 30\text{ k}\Omega$ $R_{Lopt} = 1.3\text{ k}\Omega$ RF_OUT matched to $R_{Lopt} //$ $j/(2 \times \pi \times f_{RF} \times 1.0\text{ pF})$ | (10) | P_{REF1} | -2.5 | 0 | +2.5 | dBm | B |
| 3.3 | Supply current TX mode power amplifier ON 1 | PA on/0 dBm | 17, 18 | $I_{S_TX_PAON1}$ | | 8.5 | | mA | B |
| | | $f_{RF} = 315\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON1}$ | | 8.6 | | mA | B |
| | | $f_{RF} = 433.92\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON1}$ | | 9.6 | | mA | B |
| 3.4 | Output power 2 | $V_{VS1} = V_{VS2} = 3\text{V}$ $T_{amb} = 25^{\circ}\text{C}$ $V_{PWR_H} = 0\text{V}$ $f_{RF} = 315\text{ MHz}$ $R_{R_PWR} = 30\text{ k}\Omega$ $R_{Lopt} = 1.0\text{ k}\Omega$ $f_{RF} = 433.92\text{ MHz}$ $R_{R_PWR} = 27\text{ k}\Omega$ $R_{Lopt} = 1.1\text{ k}\Omega$ $f_{RF} = 868.3\text{ MHz}$ $R_{R_PWR} = 16\text{ k}\Omega$ $R_{Lopt} = 0.5\text{ k}\Omega$ RF_OUT matched to $R_{Lopt} //$ $j/(2 \times \pi \times f_{RF} \times 1.0\text{ pF})$ | (10) | P_{REF2} | 3.5 | 5.0 | 6.5 | dBm | B |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\text{ }\Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\text{ }\Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|--|---|--------------------|--------------------|------|------|------|------|-------|
| 3.5 | Supply current TX mode power amplifier ON 2 | PA on/5 dBm $f_{RF} = 315\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON2}$ | | 10.3 | | mA | B |
| | | $f_{RF} = 433.92\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON2}$ | | 10.5 | | mA | B |
| | | $f_{RF} = 868.3\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON2}$ | | 11.2 | | mA | B |
| 3.6 | Output power 3 | $V_{VS1} = V_{VS2} = 3\text{V}$ $T_{amb} = 25^{\circ}\text{C}$ $V_{PWR_H} = AVCC$ $f_{RF} = 315\text{ MHz}$ $R_{R_PWR} = 30\text{ k}\Omega$ $R_{Lopt} = 0.38\text{ k}\Omega$ $f_{RF} = 433.92\text{ MHz}$ $R_{R_PWR} = 27\text{ k}\Omega$ $R_{Lopt} = 0.36\text{ k}\Omega$ $f_{RF} = 868.3\text{ MHz}$ $R_{R_PWR} = 20\text{ k}\Omega$ $R_{Lopt} = 0.22\text{ k}\Omega$ RF_OUT matched to $R_{Lopt} // j/(2 \times \pi \times f_{RF} \times 1.0\text{ pF})$ | (10) | P_{REF3} | 8.5 | 10 | 11.5 | dBm | B |
| 3.7 | Supply current TX mode power amplifier ON 3 | PA on/10dBm $f_{RF} = 315\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON3}$ | | 15.7 | | mA | B |
| | | $f_{RF} = 433.92\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON3}$ | | 15.8 | | mA | B |
| | | $f_{RF} = 868.3\text{ MHz}$ | 17, 18 | $I_{S_TX_PAON3}$ | | 17.3 | | mA | B |
| 3.8 | Output power variation for full temperature and supply voltage range | $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$ $P_{out} = P_{REFX} + \Delta P_{REFX}$ $X = 1, 2$ or 3 $V_{VS1} = V_{VS2} = 3.0\text{V}$ | (10) | ΔP_{REF} | | -0.8 | -1.5 | dB | B |
| | | $V_{VS1} = V_{VS2} = 2.4\text{V}$ | (10) | ΔP_{REF} | | | -3.5 | dB | B |
| | | $V_{VS1} = V_{VS2} = 2.7\text{V}$ | (10) | ΔP_{REF} | | | -2.5 | dB | C |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\text{ }\Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\text{ }\Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|--------------|---|--|--------------------|-----------------------|-------------|--------------|-------------|---------------|-------|
| 3.9 | Impedance RF_OUT in RX mode | $f_{RF} = 315\text{ MHz}$ | 10 | $Z_{RF_OUT_RX}$ | | (36 – j502) | | Ω | C |
| | | $f_{RF} = 433.92\text{ MHz}$ | 10 | $Z_{RF_OUT_RX}$ | | (19 – j366) | | Ω | C |
| | | $f_{RF} = 868.3\text{ MHz}$ | 10 | $Z_{RF_OUT_RX}$ | | (2.8 – j141) | | Ω | C |
| 3.10 | Noise floor power amplifier | at $\pm 10\text{ MHz}$ /at 5 dBm $f_{RF} = 868.3\text{ MHz}$ | (10) | L_{TX10M} | | –125 | | dBc/Hz | C |
| | | at $f_{RF} = 433.92\text{ MHz}$ | (10) | L_{TX10M} | | –126 | | dBc/Hz | C |
| | | $f_{RF} = 315\text{ MHz}$ | (10) | L_{TX10M} | | –127 | | dBc/Hz | C |
| 3.11 | ASK modulation rate | This correspond to 10 kBaud Manchester coding and 20 kBaud NRZ coding | | f_{Data_ASK} | | | 10 | kHz | C |
| 4 XTO | | | | | | | | | |
| 4.1 | Pulling XTO due to XTO, C_{L1} and C_{L2} tolerances | Pulling at nominal temperature and supply voltage $f_{XTAL} = \text{resonant frequency of the XTAL}$ $C_0 \geq 1.5\text{ pF}$ $R_m \leq 120\Omega$ $C_m \leq 7.0\text{ fF}$ $C_m \leq 14\text{ fF}$ | 24, 25 | Δf_{XTO1} | –50 –100 | f_{XTAL} | +50 +100 | ppm | A |
| 4.2 | Transconductance XTO at start | At start-up, after start-up the amplitude is regulated to V_{PPXTAL} | 24, 25 | $g_{m, XTO}$ | | 19 | | ms | B |
| 4.3 | XTO start-up time | $C_0 \leq 2.2\text{ pF}$ $C_m = 4.0\text{ fF}$ to 7.0 fF $R_m \leq 120\Omega$ | 24, 25 | $T_{PWR_ON_IRQ_1}$ | | 300 | 800 | μs | A |
| 4.4 | Maximum C_0 of XTAL | Required for stable operation with internal load capacitors | 24, 25 | C_{0max} | | | 3.8 | pF | D |
| 4.5 | Internal capacitors | C_{L1} and C_{L2} | 24, 25 | C_{L1}, C_{L2} | 14.8 | 18 pF | 21.2 | pF | B |
| 4.6 | Pulling of radio frequency f_{RF} due to XTO, C_{L1} and C_{L2} versus temperature and supply changes | $1.5\text{ pF} \leq C_0 \leq 2.2\text{ pF}$ $C_m = 4.0\text{ fF}$ to 7.0 fF $R_m \leq 120\Omega$ PLL adjusted with FREQ at nominal temperature and supply voltage | 4, 10 | Δf_{XTO2} | –2 | | +2 | ppm | C |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to 50Ω according to Figure 5-1 on page 10 with component values according to Table 5-2 on page 10 and RF_OUT matched to 50Ω according to Figure 5-10 on page 19 with component values according to Table 5-7 on page 20.

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|--|--|--------------------|---------------------|-------------------------------|----------------------------------|------|------------|-------|
| 4.7 | Amplitude XTAL after start-up | $C_m = 5\text{ fF}$, $C_0 = 1.8\text{ pF}$ $R_m = 15\Omega$ | | | | | | | |
| | | V(XTAL1, XTAL2) peak-to-peak value | 24, 25 | V_{PPXTAL} | | 700 | | mVpp | C |
| | | V(XTAL1) peak-to-peak value | 24, 25 | V_{PPXTAL} | | 350 | | mVpp | C |
| 4.8 | Maximum series resistance R_m of XTAL at start-up | $C_0 \leq 2.2\text{ pF}$, start-up may take longer under these conditions | 24, 25 | Z_{XTAL12_START} | -1,500 | -2,000 | | Ω | B |
| 4.9 | Maximum series resistance R_m of XTAL after start-up | $C_0 \leq 2.2\text{ pF}$ $C_m = 4.0\text{ fF}$ to 7.0 fF $R_m \leq 120\Omega$ | 24, 25 | R_{m_max} | | 15 | 120 | Ω | B |
| 4.10 | Nominal XTAL load resonant frequency | FREQ = 3,928 $f_{RF} = 868.3\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 315\text{ MHz}$ | 24, 25 | f_{XTAL} | | 13.41191 13.25311 12.73193 | | MHz MHz | D |
| 4.11 | External CLK frequency | FREQ = 3,928 | 30 | f_{CLK} | $f_{CLK} = \frac{f_{XTO}}{3}$ | | | MHz | D |
| | | $f_{RF} = 868.3\text{ MHz}$ CLK division ratio = 3 CLK has nominal 50% duty cycle | 30 | f_{CLK} | | 4.471 | | MHz | D |
| | | $f_{RF} = 433.92\text{ MHz}$ CLK division ratio = 3 CLK has nominal 50% duty cycle | 30 | f_{CLK} | | 4.418 | | MHz | D |
| | | $f_{RF} = 315\text{ MHz}$ CLK division ratio = 3 CLK has nominal 50% duty cycle | 30 | f_{CLK} | | 4.244 | | MHz | D |
| 4.12 | DC voltage after start-up | $V_{DC}(XTAL1, XTAL2)$ XTO running (Idle mode, RX mode and TX mode) | 24, 25 | V_{DCXTO} | -150 | -30 | | mV | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to 50Ω according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to 50Ω according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|-----------------------------|--|--------------------|------------------------|------|---|------|--------|-------|
| 5 | Synthesizer | | | | | | | | |
| 5.1 | Spurious TX mode | At $\pm f_{CLK}$, CLK enabled $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | SP_{TX} | | -72 -68 -70 | | dBC | A |
| | | at $\pm f_{XTO}$ $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | SP_{TX} | | -70 -66 -60 | | dBC | A |
| 5.2 | Spurious RX mode | At $\pm f_{CLK}$, CLK enabled $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | SP_{RX} | | < -75 < -75 < -75 | | dBC | A |
| | | at $\pm f_{XTO}$ $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | SP_{RX} | | -75 -75 -68 | | dBC | A |
| 5.3 | In loop phase noise TX mode | Measured at 20 kHz distance to carrier $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | L_{TX20k} | | -85 -80 -75 | | dBC/Hz | A |
| 5.4 | Phase noise at 1M RX mode | $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | L_{RX1M} | | -121 -120 -113 | | dBC/Hz | A |
| 5.5 | Phase noise at 1M TX mode | $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | L_{TX1M} | | -113 -111 -107 | | dBC/Hz | A |
| 5.6 | Phase noise at 10M RX mode | Noise floor PLL | | L_{RX10M} | | -135 | | dBC/Hz | B |
| 5.7 | Loop bandwidth PLL TX mode | Frequency where the absolute value loop gain is equal to 1 | | f_{Loop_PLL} | | 70 | | kHz | B |
| 5.8 | Frequency deviation TX mode | $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | | f_{DEV_TX} | | ± 15.54 ± 16.17 ± 16.37 | | kHz | D |
| 5.9 | Frequency resolution | $f_{RF} = 315\text{ MHz}$ $f_{RF} = 433.92\text{ MHz}$ $f_{RF} = 868.3\text{ MHz}$ | 4, 10 | Δf_{Step_PLL} | | 777.1 808.9 818.6 | | Hz | D |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to 50 Ω according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to 50 Ω according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

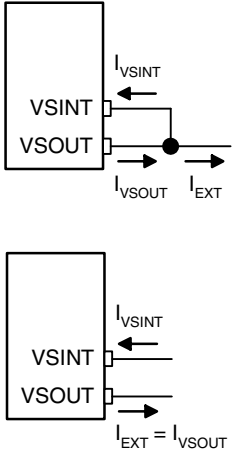
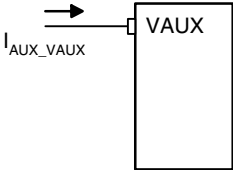
| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|---|---|------------------------------------|------------------------|--------------|---------------|------|------|-------|
| 5.10 | FSK modulation rate | This correspond to 20 kBaud Manchester coding and 40 kBaud NRZ coding | | f _{Data_FSK} | | | 20 | kHz | B |
| 6 | RX/TX Switch | | | | | | | | |
| 6.1 | Impedance RX mode | RX mode, pin 38 with short connection to GND, f _{RF} = 0Hz (DC) | 39 | Z _{Switch_RX} | | 23000 | | Ω | A |
| | | f _{RF} = 315 MHz | 39 | Z _{Switch_RX} | | (11.3 – j214) | | Ω | C |
| | | f _{RF} = 433.92 MHz | 39 | Z _{Switch_RX} | | (10.3 – j153) | | Ω | C |
| | | f _{RF} = 868.3 MHz | 39 | Z _{Switch_RX} | | (8.9 – j73) | | Ω | C |
| 6.2 | Impedance TX mode | TX mode, pin 38 with short connection to GND, f _{RF} = 0Hz (DC) | 39 | Z _{Switch_TX} | | 5 | | Ω | A |
| | | f _{RF} = 315 MHz | 39 | Z _{Switch_TX} | | (4.8 + j3.2) | Ω | C | |
| | | f _{RF} = 433.92 MHz | | | (4.5 + j4.3) | C | | | |
| | | f _{RF} = 868.3 MHz | | | | (5 + j9) | | C | |
| 7 | Microcontroller Interface | | | | | | | | |
| 7.1 | Voltage range for microcontroller interface | I _{VSINT} < 10 μA if CLK is disabled and all interface pins are in stable condition and unloaded | 27, 28, 29, 30, 31, 32, 33, 34, 35 | | 2.4 | | 5.25 | V | A |
| 7.2 | CLK output rise and fall time | f _{CLK} < 4.5 MHz | 30 | t _{rise} | | 20 | 30 | ns | B |
| | | t _{fall} | | | 20 | 30 | ns | | |
| | | C _L = 10 pF | | | | | | | |
| | | C _L = Load capacitance on pin CLK | | | | | | | |
| | | 2.4 V ≤ V _{VSINT} ≤ 5.25V | | | | | | | |
| | | 20% to 80% V _{VSINT} | | | | | | | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\text{ }\Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\text{ }\Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|--|--|--|--------------------|-------------|------|---|------|------|-------|
| 7.4 | Current consumption of the microcontroller interface | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled V_{VSOUT} disabled C_L = Load capacitance on pin CLK (All interface pins, except pin CLK, are in stable condition and unloaded) | 27 | I_{VSINT} | | $I_{VSINT} = \frac{(C_{CLK} + C_L) \times V_{VSINT} \times f_{XTO}}{3}$ $< 10\ \mu\text{A}$ $< 10\ \mu\text{A}$ | | | |
| 7.5 | Internal equivalent capacitance | Used for current calculation | 30, 27 | CCLK | | 8 | | pF | B |
| 8 Power Supply General Definitions and AUX Mode | | | | | | | | | |
| 8.1 | Current consumption of an external device connected to pin VSOUT |  | | I_{EXT} | | $I_{EXT} = I_{VSOUT} - I_{VSINT}$ $I_{EXT} = I_{VSOUT}$ | | | |
| 8.2 | AUX mode | | | | |  | | | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\ \Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\ \Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

14. Electrical Characteristics: General (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = V_{VAUX} = 4.75\text{V}$ to 5.25V (car application). Typical values are given at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$, $f_{RF} = 433.92\text{ MHz}$ (1-battery application) unless otherwise specified. Details about current consumption, timing and digital pin properties can be found in the specific sections of the “Electrical Characteristics”.

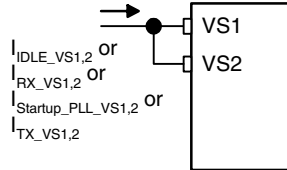
| No. | Parameters | Test Conditions | Pin ⁽¹⁾ | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|---------------------------------|---|--------------------|-----------------|--|------|------------|--------------------------------|-------|
| 8.3 | Power supply output voltage | AUX mode $V_{VAUX} \geq 4\text{ V}$ $I_{VSOUT} \leq 13.5\text{ mA}$ (3.25V regulator mode, V_REG2 , see Figure 7-1 on page 27) | 22 | V_{VSOUT} | 2.7 | | 3.5 | V | A |
| 8.4 | Current in AUX mode on pin VAUX | $I_{VSOUT} = 0$ $V_{VAUX} = 6\text{V}$ $V_{VAUX} = 4\text{V}$ to 7V | 19 | I_{AUX_VAUX} | | 380 | 500 500 | μA μA | B |
| 8.5 | Supply current AUX mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled | 19, 22, 27 | I_{S_AUX} | $I_{S_AUX} = I_{AUX_VAUX} + I_{VSINT} + I_{EXT}$ $I_{S_AUX} = I_{AUX_VAUX} + I_{EXT}$ | | | | |
| 8.6 | Supported voltage range VAUX | | 19 | V_{VAUX} | 4 | 6 | 7 | V | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. Pin numbers in brackets mean they were measured with RF_IN matched to $50\ \Omega$ according to [Figure 5-1 on page 10](#) with component values according to [Table 5-2 on page 10](#) and RF_OUT matched to $50\ \Omega$ according to [Figure 5-10 on page 19](#) with component values according to [Table 5-7 on page 20](#).

15. Electrical Characteristic: 1-Battery Application

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 2-1 on page 6](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----|--|---|--------|--|------|------|------|------|-------|
| 9 | 1-Battery Application | | |  | | | | | |
| 9.1 | Supported voltage range (every mode except high power TX mode) | 1-battery application $PWR_H = \text{GND}$ | 17, 18 | V_{VS1}, V_{VS2} | 2.4 | | 3.6 | V | A |
| 9.2 | Supported voltage range (high power TX mode) | 1-battery application $PWR_H = \text{AVCC}$ | 17, 18 | V_{VS1}, V_{VS2} | 2.7 | | 3.6 | V | A |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. The voltage of VAUX may rise up to 2V. The current I_{VAUX} may not exceed $100\ \mu\text{A}$.

15. Electrical Characteristic: 1-Battery Application (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 2-1 on page 6](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|--|--|----------------------|----------------------------|--|---------------------------|---------------------------|---|---------------------|
| 9.3 | Power supply output voltage | 1-battery application $V_{VS1} = V_{VS2} \geq 2.6\text{V}$ VAUX open ⁽¹⁾ $I_{VSOUT} \leq 13.5\text{ mA}$ (no voltage regulator to stabilize V_{VSOUT}) $V_{VS1} = V_{VS2} \geq 2.425\text{V}$ VAUX open ⁽¹⁾ $I_{VSOUT} \leq 1.5\text{ mA}$ (no voltage regulator to stabilize V_{VSOUT}) | 22 | V_{VSOUT} | 2.4 | | V_{VS1} | V | B |
| 9.4 | Supply voltage for microcontroller interface | | 27 | V_{VSINT} | 2.4 | | 5.25 | V | A |
| 9.5 | Threshold hysteresis | $V_{Thres_2} - V_{Thres_1}$ | 22 | ΔV_{Thres} | 60 | 80 | 100 | mV | B |
| 9.6 | Reset threshold voltage at pin VSOUT (N_RESET) | | 22 | V_{Thres_1} | 2.18 | 2.3 | 2.42 | V | A |
| 9.7 | Reset threshold voltage at pin VSOUT (Low_Batt) | | 22 | V_{Thres_2} | 2.26 | 2.38 | 2.5 | V | A |
| 9.8 | Supply current OFF mode | $V_{VS1} = V_{VS2} \leq 3.6\text{V}$ $V_{VSINT} = 0\text{V}$ | 17, 18, 22, 27 | I_{S_OFF} | | 2 | 350 | nA | A |
| 9.9 | Current in Idle mode on pin VS1 and VS2 | $V_{VS1} = V_{VS2} \leq 3\text{V}$ $I_{VSOUT} = 0$ CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled V_{VSOUT} disabled | 17, 18 | $I_{IDLE_VS1, 2}$ | | 312 260 225 | 430 370 320 | μA μA μA | A B B |
| 9.10 | Supply current Idle mode | | 17, 18, 22, 27 | I_{S_IDLE} | $I_{S_IDLE} = I_{IDLE_VS1, 2} + I_{VSINT} + I_{EXT}$ | | | | |
| 9.11 | Current in RX mode on pin VS1 and VS2 | $V_{VS1} = V_{VS2} \leq 3\text{V}$ $I_{VSOUT} = 0$ | 17, 18 | $I_{RX_VS1, 2}$ | | 10.5 | 14 | mA | A |
| 9.12 | Supply current RX mode | CLK enabled V_{VSOUT} enabled | 17, 18, 22, 27 | I_{S_RX} | $I_{S_RX} = I_{RX_VS1, 2} + I_{VSINT} + I_{EXT}$ | | | | |
| 9.13 | Current during $T_{Startup_PLL}$ on pin VS1 and VS2 | $V_{VS1} = V_{VS2} \leq 3\text{V}$ $I_{VSOUT} = 0$ | 17, 18 | $I_{Startup_PLL_VS1, 2}$ | | 8.8 | 11.5 | mA | C |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. The voltage of VAUX may rise up to 2V. The current I_{VAUX} may not exceed 100 μA .

15. Electrical Characteristic: 1-Battery Application (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 2-1 on page 6](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

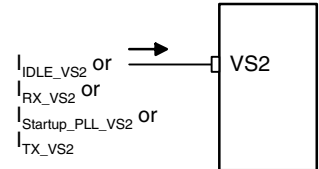
| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|---|--|----------------------|--------------------|---|--|--|------|-------|
| 9.14 | Current in RX polling mode on pin VS1 and VS2 | $I_P = \frac{I_{IDLE_VS1,2} \times T_{SLEEP} + I_{Startup_PLL_VS1,2} \times T_{Startup_PLL} + I_{RX_VS1,2} \times (T_{Startup_Sig_Proc} + T_{Bitcheck})}{T_{Sleep} + T_{Startup_PLL} + T_{Startup_Sig_Proc} + T_{Bitcheck}}$ | | | | | | | |
| 9.15 | Supply current RX polling mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled V_{VSOUT} disabled | 17, 18, 22, 27 | I_{S_Poll} | $I_{S_Poll} = I_P + I_{VSINT} + I_{EXT}$ $I_{S_Poll} = I_P + I_{EXT}$ $I_{S_Poll} = I_P$ | | | | |
| 9.16 | Current in TX mode on pin VS1 and VS2 | $V_{VS1} = V_{VS2} \leq 3\text{V}$ $I_{VSOUT} = 0$ Pout = 5 dBm/10 dBm 315 MHz/5 dBm 315 MHz/10 dBm 433.92 MHz/5 dBm 433.92 MHz/10 dBm 868.3 MHz/5 dBm 868.3 MHz/10 dBm | 17, 18 | $I_{TX_VS1_VS2}$ | | 10.3 15.7 10.5 15.8 11.2 17.3 | 13.4 20.5 13.5 20.5 14.5 22.5 | mA | B |
| 9.17 | Supply current TX mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled | 17, 18, 22, 27 | I_{S_TX} | $I_{S_TX} = I_{TX_VS1,2} + I_{VSINT} + I_{EXT}$ $I_{S_TX} = I_{TX_VS1,2} + I_{EXT}$ | | | | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. The voltage of VAUX may rise up to 2V. The current I_{VAUX} may not exceed 100 μA .

16. Electrical Characteristics: 2-Battery Application

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS2} = 4.4\text{V}$ to 6.6V typical values at $V_{VS2} = 6\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 4-1 on page 8](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-------|---|---|------------|--------------------|---|-------------------|-------------------|---|-------------|
| 10 | 2-Battery Application |  | | | | | | | |
| 10.1 | Supported voltage range | 2-battery application | 17 | V_{VS2} | 4.4 | | 6.6 | V | A |
| 10.2 | Power supply output voltage | 2 battery application $V_{VS2} \geq 4.4\text{V}$ VAUX open ⁽¹⁾ $I_{VSOUT} \leq 13.5\text{ mA}$ (3.3V regulator mode, V_REG1, see Figure 7-1 on page 27) | 22 | V_{VSOUT} | 3.0 | | 3.5 | V | A |
| 10.3 | Supply voltage for microcontroller interface | | 27 | V_{VSINT} | 2.4 | | 5.25 | V | A |
| 10.4 | Threshold hysteresis | $V_{Thres_2} - V_{Thres_1}$ | 22 | ΔV_{Thres} | 60 | 80 | 100 | mV | B |
| 10.5 | Reset threshold voltage at pin VSOUT (N_RESET) | | 22 | V_{Thres_1} | 2.18 | 2.3 | 2.42 | V | A |
| 10.6 | Reset threshold voltage at pin VSOUT (Low_Batt) | | 22 | V_{Thres_2} | 2.26 | 2.38 | 2.5 | V | A |
| 10.7 | Supply current OFF mode | $V_{VS2} \leq 6.6\text{V}$ $V_{VSINT} = 0\text{V}$ | 17, 22, 27 | I_{S_OFF} | | 10 | 350 | nA | A |
| 10.8 | Current in Idle mode on pin VS2 | $V_{VS2} \leq 6\text{V}$ $I_{VSOUT} = 0$ CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled V_{VSOUT} disabled | 17 | I_{IDLE_VS2} | | 410 348 309 | 560 490 430 | μA μA μA | A B B |
| 10.9 | Supply current Idle mode | | 17, 22, 27 | I_{S_IDLE} | $I_{S_IDLE} = I_{IDLE_VS2} + I_{VSINT} + I_{EXT}$ | | | | |
| 10.10 | Current in RX mode on pin VS2 | $I_{VSOUT} = 0$ | 17 | I_{RX_VS2} | | 10.8 | 14.5 | mA | B |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. The voltage of VAUX may rise up to 2 V. The current I_{VAUX} may not exceed $100\text{ }\mu\text{A}$.

16. Electrical Characteristics: 2-Battery Application (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS2} = 4.4\text{V}$ to 6.6V typical values at $V_{VS2} = 6\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 4-1 on page 8](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

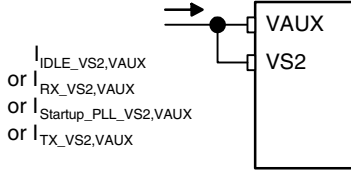
| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-------|--|--|---------------|-------------------------|---|--|--|------|-------|
| 10.11 | Supply current RX mode | CLK enabled V_{VSOUT} enabled | 17, 22, 27 | I_{S_RX} | $I_{S_RX} = I_{RX_VS2} + I_{VSINT} + I_{EXT}$ | | | | |
| 10.12 | Current during $T_{Startup_PLL}$ on pin VS2 | $I_{VSOUT} = 0$ | 17 | $I_{Startup_PLL_VS2}$ | | 9.1 | 12 | mA | C |
| 10.13 | Current in RX polling mode on on pin VS2 | $I_P = \frac{I_{IDLE_VS2} \times T_{SLEEP} + I_{Startup_PLL_VS2} \times T_{Startup_PLL} + I_{RX_VS2} \times (T_{Startup_Sig_Proc} + T_{Bitcheck})}{T_{Sleep} + T_{Startup_PLL} + T_{Startup_Sig_Proc} + T_{Bitcheck}}$ | | | | | | | |
| 10.14 | Supply current RX polling mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled V_{VSOUT} disabled | 17, 22, 27 | I_{S_Poll} | $I_{S_Poll} = I_P + I_{VSINT} + I_{EXT}$ $I_{S_Poll} = I_P + I_{EXT}$ $I_{S_Poll} = I_P$ | | | | |
| 10.15 | Current in TX mode on pin VS2 | $I_{VSOUT} = 0$ $P_{out} = 5\text{ dBm}/10\text{ dBm}$ 315 MHz/5 dBm 315 MHz/10 dBm 433.92 MHz/5 dBm 433.92 MHz/10 dBm 868.3 MHz/5 dBm 868.3 MHz/10 dBm | 17, 19 | I_{TX_VS2} | | 10.7 16.2 10.9 16.3 11.6 17.8 | 13.9 21.0 14.0 21.0 15.0 23.0 | mA | B |
| 10.16 | Supply current TX mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled | 17, 22, 27 | I_{S_TX} | $I_{S_TX} = I_{TX_VS2} + I_{VSINT} + I_{EXT}$ $I_{S_TX} = I_{TX_VS2} + I_{EXT}$ | | | | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. The voltage of VAUX may rise up to 2 V. The current I_{VAUX} may not exceed 100 μA .

17. Electrical Characteristics: Car Application

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS2} = 4.75\text{V}$ to 5.25V . Typical values at $V_{VS2} = 5\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 3-1 on page 7](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-------|---|---|----------------|-----------------------|---|------|------|---------------|-------|
| 11 | Car Application |  | | | | | | | |
| 11.1 | Supported voltage range | Car application | 17, 19, 27 | V_{VS2}, V_{AUX} | 4.75 | | 5.25 | V | A |
| 11.2 | Power supply output voltage | Car application $V_{VS2} = V_{VAUX}$ $I_{VSOUT} \leq 13.5\text{ mA}$ (3.25V regulator mode, V_{REG2} , see Figure 7-1 on page 27) | 22 | V_{VSOUT} | 3.0 | | 3.5 | V | A |
| 11.3 | Supply voltage for microcontroller-interface | | 27 | V_{VSINT} | 2.4 | | 5.25 | V | A |
| 11.4 | Threshold hysteresis | $V_{Thres_2} - V_{Thres_1}$ | 22 | ΔV_{Thres} | 60 | 80 | 100 | mV | B |
| 11.5 | Reset threshold voltage at pin VSOUT (N_RESET) | | 22 | V_{Thres_1} | 2.18 | 2.3 | 2.42 | V | A |
| 11.6 | Reset threshold voltage at pin VSOUT (Low_Batt) | | 22 | V_{Thres_2} | 2.26 | 2.38 | 2.5 | V | A |
| 11.7 | Current in Idle mode on pin VS2 and VAUX | $I_{VSOUT} = 0$ CLK enabled V_{VSOUT} enabled | 17, 19 | $I_{IDLE_VS2_VAUX}$ | | 444 | 580 | μA | B |
| | | CLK disabled V_{VSOUT} enabled | | | | 380 | 500 | μA | B |
| | | V_{VSOUT} disabled | | | | 310 | 400 | μA | B |
| 11.8 | Supply current in Idle mode | | 17, 19, 22, 27 | I_{S_IDLE} | $I_{S_IDLE} = I_{IDLE_VS2_VAUX} + I_{VSINT} + I_{EXT}$ | | | | |
| 11.9 | Current in RX mode on pin VS2 and VAUX | $I_{VSOUT} = 0$ | 17, 19 | $I_{RX_VS2_VAUX}$ | | 10.8 | 14.5 | mA | B |
| 11.10 | Supply current in RX mode | CLK enabled V_{VSOUT} enabled | 17, 19, 22, 27 | I_{S_RX} | $I_{S_RX} = I_{RX_VS2_VAUX} + I_{VSINT} + I_{EXT}$ | | | | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

17. Electrical Characteristics: Car Application (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS2} = 4.75\text{V}$ to 5.25V . Typical values at $V_{VS2} = 5\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$. Application according to [Figure 3-1 on page 7](#). $f_{RF} = 315.0\text{ MHz}/433.92\text{ MHz}/868.3\text{ MHz}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-------|---|--|----------------|-------------------------------|--|--|--|------|-------|
| 11.11 | Current during $T_{Startup_PLL}$ on pin VS2 and VAUX | $I_{VSOUT} = 0$ | 17, 19 | $I_{Startup_PLL_VS2_VAUX}$ | | 9.1 | 12 | mA | C |
| 11.12 | Current in RX_Polling_Mode on pin VS2 and VAUX $I_P = \frac{I_{IDLE_VS2,VAUX} \times T_{SLEEP} + I_{Startup_PLL_VS2,VAUX} \times T_{Startup_PLL} + I_{RX_VS2,VAUX} \times (T_{Startup_Sig_Proc} + T_{Bitcheck})}{T_{Sleep} + T_{Startup_PLL} + T_{Startup_Sig_Proc} + T_{Bitcheck}}$ | | | | | | | | |
| 11.13 | Supply current in RX polling mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled V_{VSOUT} disabled | 17, 19, 22, 27 | I_{S_Poll} | $I_{S_Poll} = I_P + I_{VSINT} + I_{EXT}$ $I_{S_Poll} = I_P + I_{EXT}$ $I_{S_Poll} = I_P$ | | | | |
| 11.14 | Current in TX mode on pin VS2 and VAUX | $I_{VSOUT} = 0$ $P_{out} = 5\text{dBm}/10\text{dBm}$ 315 MHz/5dBm 315 MHz/10dBm 433.92 MHz/5dBm 433.92 MHz/10dBm 868.3 MHz/10dBm | 17, 19 | $I_{TX_VS2_VAUX}$ | | 10.7 16.2 10.9 16.3 11.6 17.8 | 13.9 21.0 14.0 21.0 15.0 23.0 | mA | B |
| 11.15 | Supply current in TX mode | CLK enabled V_{VSOUT} enabled CLK disabled V_{VSOUT} enabled | 17, 19, 22, 27 | I_{S_TX} | $I_{S_TX} = I_{TX_VS2_VAUX} + I_{VSINT} + I_{EXT}$ $I_{S_TX} = I_{TX_VS2_VAUX} + I_{EXT}$ | | | | |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

18. Digital Timing Characteristics

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$. $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = 4.75\text{V}$ to 5.25V (car application), typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----------|---|---|-----|--------------------------|---|-------------------------|---|---------------|-------|
| 12 | Basic Clock Cycle of the Digital Circuitry | | | | | | | | |
| 12.1 | Basic clock cycle | | | T_{DCLK} | $16/f_{XTO}$ | | $16/f_{XTO}$ | μs | A |
| 12.2 | Extended basic clock cycle | XLIM = 0 BR_Range_0 BR_Range_1 BR_Range_2 BR_Range_3 XLIM = 1 BR_Range_0 BR_Range_1 BR_Range_2 BR_Range_3 | | T_{XDCLK} | 8 4 2 1 $\times T_{DCLK}$ 16 8 4 2 $\times T_{DCLK}$ | | 8 4 2 1 $\times T_{DCLK}$ 16 8 4 2 $\times T_{DCLK}$ | μs | A |
| 13 | RX Mode/RX Polling Mode | | | | | | | | |
| 13.1 | Sleep time | Sleep and XSleep are defined in control register 4 | | T_{Sleep} | $\text{Sleep} \times$ $X_{Sleep} \times$ $1024 \times$ T_{DCLK} | | $\text{Sleep} \times$ $X_{Sleep} \times$ $1024 \times$ T_{DCLK} | ms | A |
| 13.2 | Start-up PLL RX mode | from Idle mode | | $T_{Startup_PLL}$ | | $798.5 \times T_{DCLK}$ | $798.5 \times T_{DCLK}$ | μs | A |
| 13.3 | Start-up signal processing | BR_Range_0 BR_Range_1 BR_Range_2 BR_Range_3 | | $T_{Startup_Sig_Proc}$ | 882 498 306 210 $\times T_{DCLK}$ | | 882 498 306 210 $\times T_{DCLK}$ | | A |
| 13.4 | Time for Bit-check | Average time during polling. No RF signal applied. $f_{Signal} = 1/(2 \times t_{ee})$ Signal data rate Manchester (Lim_min and Lim_max up to $\pm 50\%$ of t_{ee} , see Figure 11-4 on page 53) Bit-check time for a valid input signal f_{Sig} $N_{Bit-check} = 0$ $N_{Bit-check} = 3$ $N_{Bit-check} = 6$ $N_{Bit-check} = 9$ | | T_{Bit_check} | $3/f_{Sig}$ $6/f_{Sig}$ $9/f_{Sig}$ | $1/f_{Signal}$ | $3.5/f_{Sig}$ $6.5/f_{Sig}$ $9.5/f_{Sig}$ | ms | C |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

18. Digital Timing Characteristics (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$. $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = 4.75\text{V}$ to 5.25V (car application), typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----------|---|--|--------|--------------------|--------------------------|-------------------------|----------------------------|---------------|-------|
| 13.5 | Baud-rate range | BR_Range = BR_Range0 BR_Range1 BR_Range2 BR_Range3 | | BR_Range | 1.0 2.0 4.0 8.0 | | 2.5 5.0 10.0 20.0 | kBaud | A |
| 13.6 | Minimum time period between edges at pin SDO_TMDO in RX transparent mode | XLIM = 0 BR_Range_0 BR_Range_1 BR_Range_2 BR_Range_3 XLIM = 1 BR_Range_0 BR_Range_1 BR_Range_2 BR_Range_3 | 31 | T_{DATA_min} | $10 \times T_{XDCLK}$ | | | μs | A |
| 13.7 | Edge-to-edge time period of the data signal for full sensitivity in RX mode | BR_Range_0 BR_Range_1 BR_Range_2 BR_Range_3 | | T_{DATA} | 200 100 50 25 | | 500 250 125 62.5 | μs | B |
| 14 | TX Mode | | | | | | | | |
| 14.1 | Start-up time | From Idle mode | | $T_{Startup}$ | | $331.5 \times T_{DCLK}$ | $331.5 \times T_{DCLK}$ | μs | A |
| 15 | Configuration of the Transceiver with 4-wire Serial Interface | | | | | | | | |
| 15.1 | CS set-up time to rising edge of SCK | | 33, 35 | T_{CS_setup} | $1.5 \times T_{DCLK}$ | | | μs | A |
| 15.2 | SCK cycle time | | 33 | T_{Cycle} | 2 | | | μs | A |
| 15.3 | SDI_TMDI set-up time to rising edge of SCK | | 32, 33 | T_{Setup} | 250 | | | ns | C |
| 15.4 | SDI_TMDI hold time from rising edge of SCK | | 32, 33 | T_{Hold} | 250 | | | ns | C |
| 15.5 | SDO_TMDO enable time from rising edge of CS | | 31, 35 | T_{Out_enable} | | | 250 | ns | C |
| 15.6 | SDO_TMDO output delay from falling edge of SCK | $C_L = 10\text{ pF}$ | 31, 35 | T_{Out_delay} | | | 250 | ns | C |
| 15.7 | SDO_TMDO disable time from falling edge of CS | | 31, 33 | $T_{Out_disable}$ | | | 250 | ns | C |
| 15.8 | CS disable time period | | 35 | $T_{CS_disable}$ | $1.5 \times T_{DCLK}$ | | | μs | A |
| 15.9 | Time period SCK low to CS high | | 33, 35 | T_{SCK_setup1} | 250 | | | ns | C |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

18. Digital Timing Characteristics (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$. $V_{VS1} = V_{S2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = 4.75\text{V}$ to 5.25V (car application), typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----------|--|--|--------|-----------------------|------|-----------------------------|---------------------------|------|-------|
| 15.10 | Time period SCK low to CS low | | 33, 35 | T_{SCK_setup2} | 250 | | | ns | C |
| 15.11 | Time period CS low to SCK high | | 33, 35 | T_{SCK_hold} | 250 | | | ns | C |
| 16 | Start Time Push Button T_n and PWR_ON Timing of wake-up via PWR_ON or T_n | | | | | | | | |
| 16.1 | PWR_ON high to positive edge on pin IRQ (see Figure 9-4 on page 43) | From OFF mode to Idle mode, applications according to Figure 2-1 on page 6 , Figure 3-1 on page 7 and Figure 4-1 on page 8 XTAL: $C_m = 4..7\text{ fF}$ (typ. 5 fF) $C_0 < 2.2\text{ pF}$ (typ. 1.8 pF) $R_m \leq 120\Omega$ (typ. 15 Ω) 1-battery application $C_1 = C_2 = 68\text{ nF}$ $C_3 = C_4 = 68\text{ nF}$ $C_5 = 10\text{ nF}$ 2-battery application $C_1 = C_4 = 68\text{ nF}$ $C_2 = C_3 = 2.2\text{ }\mu\text{F}$ $C_5 = 10\text{ nF}$ Car application $C_1 = C_3 = C_4 = 68\text{ nF}$ $C_2 = C_{12} = 2.2\text{ }\mu\text{F}$ $C_5 = 10\text{ nF}$ | 29, 40 | $T_{PWR_ON_IRQ_1}$ | | 0.3 0.45 0.45 | 0.8 1.3 1.3 | ms | B |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

18. Digital Timing Characteristics (Continued)

All parameters refer to GND and are valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$. $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1-battery application), $V_{VS2} = 4.4\text{V}$ to 6.6V (2-battery application) and $V_{VS2} = 4.75\text{V}$ to 5.25V (car application), typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|------|--|--|------------------------|-----------------------|---------------------------|-----------------------------|---------------------------|---------------|-------|
| 16.2 | PWR_ON high to positive edge on pin IRQ (see Figure 9-4 on page 43) | Every mode except OFF mode | 29, 40 | $T_{PWR_ON_IRQ_2}$ | | | $2 \times T_{DCLK}$ | μs | A |
| 16.3 | Tn low to positive edge on pin IRQ (see Figure 9-2 on page 41) | From OFF mode to Idle mode, applications according to Figure 2-1 on page 6 , Figure 3-1 on page 7 and Figure 4-1 on page 8 XTAL: $C_m = 4..7\text{ fF}$ (typ 5 fF) $C_0 < 2.2\text{ pF}$ (typ 1.8 pF) $R_m \leq 120\Omega$ (typ 15Ω) 1-battery application $C_1 = C_2 = 68\text{ nF}$ $C_3 = C_4 = 68\text{ nF}$ $C_5 = 10\text{ nF}$ 2-battery application $C_1 = C_4 = 68\text{ nF}$ $C_2 = C_3 = 2.2\text{ }\mu\text{F}$ $C_5 = 10\text{ nF}$ Car application $C_1 = C_3 = C_4 = 68\text{ nF}$ $C_2 = C_{12} = 2.2\text{ }\mu\text{F}$ $C_5 = 10\text{ nF}$ | 29, 41, 42, 43, 44, 45 | T_{Tn_IRQ} | | 0.3 0.45 0.45 | 0.8 1.3 1.3 | ms | B |
| 16.4 | Push button debounce time | Every mode except OFF mode | 29, 41, 42, 43, 44, 45 | $T_{Debounce}$ | 8195 $\times T_{DCLK}$ | | 8195 $\times T_{DCLK}$ | μs | A |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

19. Digital Port Characteristics

All parameter refer to GND and valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1 Battery Application) and $V_{VS2} = 4.4\text{V}$ to 6.6V (2 Battery Application) and $V_{VS2} = 4.75\text{V}$ to 5.25V (Car Application) typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-----------|--|--|--------------------|----------|--------------------------------|------|------------------------|---------------|-------|
| 17 | Digital Ports | | | | | | | | |
| 17.1 | CS input -Low level input voltage | $V_{VSINT} = 2.4\text{V}$ to 5.25V | 35 | V_{ll} | | | $0.2 \times V_{VSINT}$ | V | A |
| | -High level input voltage | $V_{VSINT} = 2.4\text{V}$ to 5.25V | 35 | V_{lh} | $0.8 \times V_{VSINT}$ | | V_{VSINT} | V | A |
| 17.2 | SCK input -Low level input voltage | $V_{VSINT} = 2.4\text{V}$ to 5.25V | 33 | V_{ll} | | | $0.2 \times V_{VSINT}$ | V | A |
| | -High level input voltage | $V_{VSINT} = 2.4\text{V}$ to 5.25V | 33 | V_{lh} | $0.8 \times V_{VSINT}$ | | V_{VSINT} | V | A |
| 17.3 | SDI_TMDI input -Low level input voltage | $V_{VSINT} = 2.4\text{V}$ to 5.25V | 32 | V_{ll} | | | $0.2 \times V_{VSINT}$ | V | A |
| | -High level input voltage | $V_{VSINT} = 2.4\text{V}$ to 5.25V | 32 | V_{lh} | $0.8 \times V_{VSINT}$ | | V_{VSINT} | V | A |
| 17.4 | TEST1 input | TEST1 input must always be directly connected to GND | 20 | | | | | | D |
| 17.5 | TEST2 input | TEST2 input must always be direct connected to GND | 23 | | | | | | D |
| 17.6 | PWR_ON input -Low level input voltage | Internal pull-down with series connection of $40\text{ k}\Omega \pm 20\%$ resistor and diode | 40 | V_{ll} | | | 0.4 | V | A |
| | -High level input voltage ⁽¹⁾ | Internal pull-down with series connection of $40\text{ k}\Omega \pm 20\%$ resistor and diode | 40 | V_{lh} | $0.8 \times V_{VS2}$ | | | V | A |
| 17.7 | Tn input -Low level input voltage | Internal pull-up resistor of $50\text{ k}\Omega \pm 20\%$ | 41, 42, 43, 44, 45 | V_{ll} | | | $0.2 \times V_{VS2}$ | V | A |
| | -High level input voltage ⁽¹⁾ | Internal pull-up resistor of $50\text{ k}\Omega \pm 20\%$ | 41, 42, 43, 44, 45 | V_{lh} | $\times V_{VS2} - 0.5\text{V}$ | | | V | A |
| 17.8 | 433_N868 input -Low level input voltage | | 6 | V_{ll} | | | 0.25 | V | A |
| | -Input current low | | 6 | I_{ll} | | | -5 | μA | A |
| | -High level input voltage | | 6 | V_{lh} | 1.7 | | AVCC | V | A |
| | -Input current high | | 6 | I_{lh} | | | 1 | μA | A |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. If a logic high level is applied to this pin a minimum serial impedance of $100\ \Omega$ must be ensured for proper operation over full temperature range.

19. Digital Port Characteristics (Continued)

All parameter refer to GND and valid for $T_{amb} = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $V_{VS1} = V_{VS2} = 2.4\text{V}$ to 3.6V (1 Battery Application) and $V_{VS2} = 4.4\text{V}$ to 6.6V (2 Battery Application) and $V_{VS2} = 4.75\text{V}$ to 5.25V (Car Application) typical values at $V_{VS1} = V_{VS2} = 3\text{V}$ and $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
|-------|--|---|-----|----------|--------------------------|---------------------------|------|---------------|-------|
| 17.9 | PWR_H input -Low level input voltage | | 9 | V_{ll} | | | 0.25 | V | A |
| | -Input current low | | 9 | I_{ll} | | | -5 | μA | A |
| | -High level input voltage | | 9 | V_{lh} | 1.7 | | AVCC | V | A |
| | -Input current high | | 9 | I_{lh} | | | 1 | μA | A |
| 17.10 | SDO_TMDO output -Saturation voltage low | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{SDO_TMDO} = 250\ \mu\text{A}$ | 31 | V_{ol} | | 0.15 | 0.4 | V | B |
| | Saturation voltage high | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{SDO_TMDO} = -250\ \mu\text{A}$ | 31 | V_{oh} | $V_{VSINT} - 0.4$ | $V_{VSINT} - 0.15$ | | V | B |
| 17.11 | IRQ output -Saturation voltage low | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{IRQ} = 250\ \mu\text{A}$ | 29 | V_{ol} | | 0.15 | 0.4 | V | B |
| | Saturation voltage high | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{IRQ} = -250\ \mu\text{A}$ | 29 | V_{oh} | $V_{VSINT} - 0.4$ | $V_{VSINT} - 0.15$ | | V | B |
| 17.12 | CLK output -Saturation voltage low | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{CLK} = 100\ \mu\text{A}$ internal series resistor of $1\ \text{k}\Omega$ for spurious reduction in PLL | 30 | V_{ol} | | 0.15 | 0.4 | V | B |
| | Saturation voltage high | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{CLK} = -100\ \mu\text{A}$ internal series resistor of $1\ \text{k}\Omega$ for spurious reduction in PLL | 30 | V_{oh} | $V_{VSINT} - 0.4$ | $V_{VSINT} - 0.15$ | | V | B |
| 17.13 | N_RESET output -Saturation voltage low | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{N_RESET} = 250\ \mu\text{A}$ | 28 | V_{ol} | | 0.15 | 0.4 | V | B |
| | -Saturation voltage high | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{N_RESET} = -250\ \mu\text{A}$ | 28 | V_{oh} | $V_{VSINT} - 0.4$ | $V_{VSINT} - 0.15$ | | V | B |
| 17.14 | RX_ACTIVE output -Saturation voltage high | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{RX_ACTIVE} = -1.5\ \text{mA}$ | 46 | V_{oh} | $V_{AVCC} - 0.5\text{V}$ | $V_{AVCC} - 0.15\text{V}$ | | V | B |
| | -Saturation voltage low | $V_{VSINT} = 2.4\text{V}$ to 5.25V $I_{RX_ACTIVE} = 25\ \mu\text{A}$ | 46 | V_{ol} | | 0.25 | 0.4 | V | B |
| 17.15 | DEM_OUT output Saturation voltage low | Open drain output $I_{DEM_OUT} = 250\ \mu\text{A}$ | 34 | V_{ol} | | 0.15 | 0.4 | V | B |

*) Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Note: 1. If a logic high level is applied to this pin a minimum serial impedance of $100\ \Omega$ must be ensured for proper operation over full temperature range.

20. Ordering Information

| Extended Type Number | Package | Remarks |
|----------------------|---------|----------------------|
| ATA5811-PLQW | QFN48 | 7 mm × 7 mm, Pb-free |
| ATA5812-PLQW | QFN48 | 7 mm × 7 mm, Pb-free |

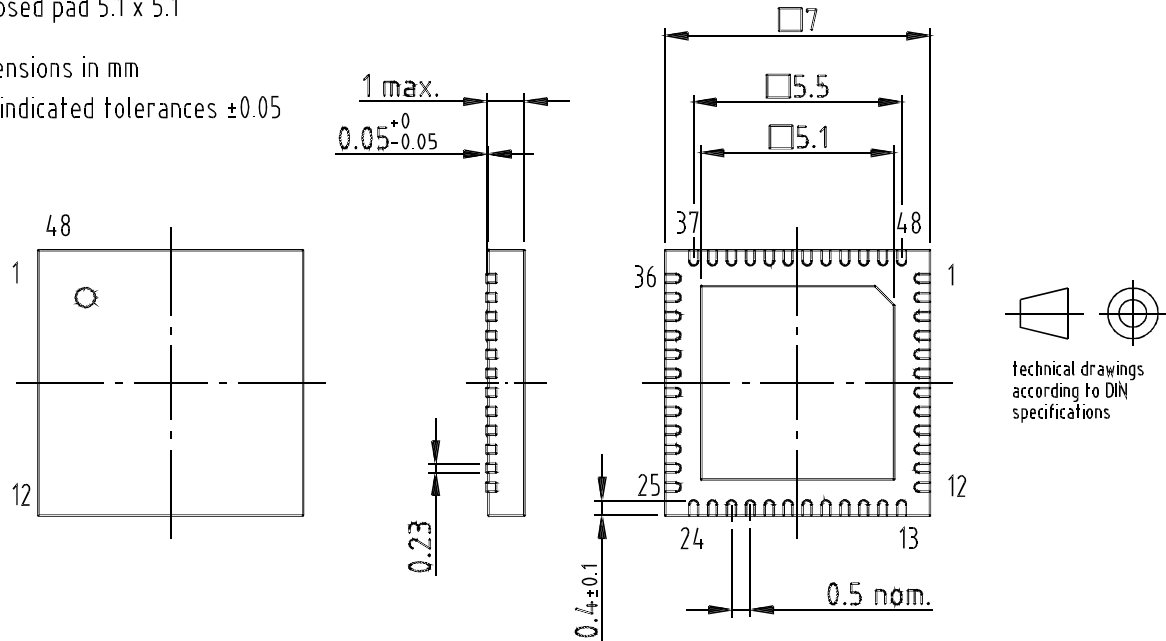
21. Package Information

Package: QFN 48 7x7

Exposed pad 5.1 x 5.1

Dimensions in mm

Not indicated tolerances ± 0.05



Drawing-No.: 6.543-5089.02-4

Issue: 1; 14.01.03

22. Revision History

Please note that the following page numbers referred to in this section refer to the specific revision mentioned, not to this document.

| Revision No. | History |
|-----------------|--|
| 4689D-RKE-09/05 | <ul style="list-style-type: none"> Pb-free Logo on page 1 added Table 1-1 "Pin Description" on pages 4 to 5 changed Ordering Information on page 89 changed |

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